

RL78/G12

RENESAS MCU

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Rev.2.20
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True Low Power Platform (as low as 63 μ A/MHz), 1.8V to 5.5V operation,
2 to 16 Kbyte Flash, 31 DMIPS at 24MHz, for General Purpose Applications

1. OUTLINE

1.1 Features

Ultra-low power consumption technology

- V_{DD} = single power supply voltage of 1.8 to 5.5 V which can operate at a low voltage
- HALT mode
- STOP mode
- SNOOZE mode

RL78 CPU core

- CISC architecture with 3-stage pipeline
- Minimum instruction execution time: Can be changed from high speed (0.04167 μ s: @ 24 MHz operation with high-speed on-chip oscillator) to ultra-low speed (1 μ s: @ 1 MHz operation)
- Address space: 1 MB
- General-purpose registers: (8-bit register x 8) x 4 banks
- On-chip RAM: 256 B to 2 KB

Code flash memory

- Code flash memory: 2 to 16 KB
- Block size: 1 KB
- Prohibition of block erase and rewriting (security function)
- On-chip debug function
- Self-programming (with flash shield window function)

Data flash memory ^{Note}

- Data flash memory: 2 KB
- Back ground operation (BGO): Instructions are executed from the program memory while rewriting the data flash memory.
- Number of rewrites: 1,000,000 times (TYP.)
- Voltage of rewrites: V_{DD} = 1.8 to 5.5 V

High-speed on-chip oscillator

- Select from 24 MHz, 16 MHz, 12 MHz, 8 MHz, 6 MHz, 4 MHz, 3 MHz, 2 MHz, and 1 MHz
- High accuracy: +/- 1.0 % (V_{DD} = 1.8 to 5.5 V, T_A = -20 to +85 $^{\circ}$ C)

Operating ambient temperature

- T_A = -40 to +85 $^{\circ}$ C (A: Consumer applications, D: Industrial applications)
- T_A = -40 to +105 $^{\circ}$ C (G: Industrial applications) ^{Note}

Power management and reset function

- On-chip power-on-reset (POR) circuit
- On-chip voltage detector (LVD) (Select interrupt and reset from 12 levels)

DMA (Direct Memory Access) controller ^{Note}

- 2 channels
- Number of clocks during transfer between 8/16-bit SFR and internal RAM: 2 clocks

Multiplier and divider/multiply-accumulator

- 16 bits x 16 bits = 32 bits (Unsigned or signed)
- 32 bits x 32 bits = 32 bits (Unsigned)
- 16 bits x 16 bits + 32 bits = 32 bits (Unsigned or signed)

Serial interface

- CSI : 1 to 3 channels
- UART : 1 to 3 channels
- Simplified I²C communication : 0 to 3 channels
- I²C communication : 1 channel

Timer

- 16-bit timer : 4 to 8 channels
- 12-bit interval timer : 1 channel
- Watchdog timer : 1 channel (operable with the dedicated low-speed on-chip oscillator)

A/D converter

- 8/10-bit resolution A/D converter (V_{DD} = 1.8 to 5.5 V)
- 8 to 11 channels, internal reference voltage (1.45 V), and temperature sensor ^{Note}

I/O port

- I/O port: 18 to 26
(N-ch open drain I/O [withstand voltage of 6 V]: 2, N-ch open drain I/O [V_{DD} withstand voltage]: 4 to 9)
- Can be set to N-ch open drain, TTL input buffer, and on-chip pull-up resistor
- Different potential interface: Can connect to a 1.8/2.5/3 V device
- On-chip key interrupt function
- On-chip clock output/buzzer output controller

Others

- On-chip BCD (binary-coded decimal) correction circuit

Note Can be selected only in HS (high-speed main) mode.

Remark The functions mounted depend on the product.
See 1.7 Outline of Functions.

O ROM, RAM capacities

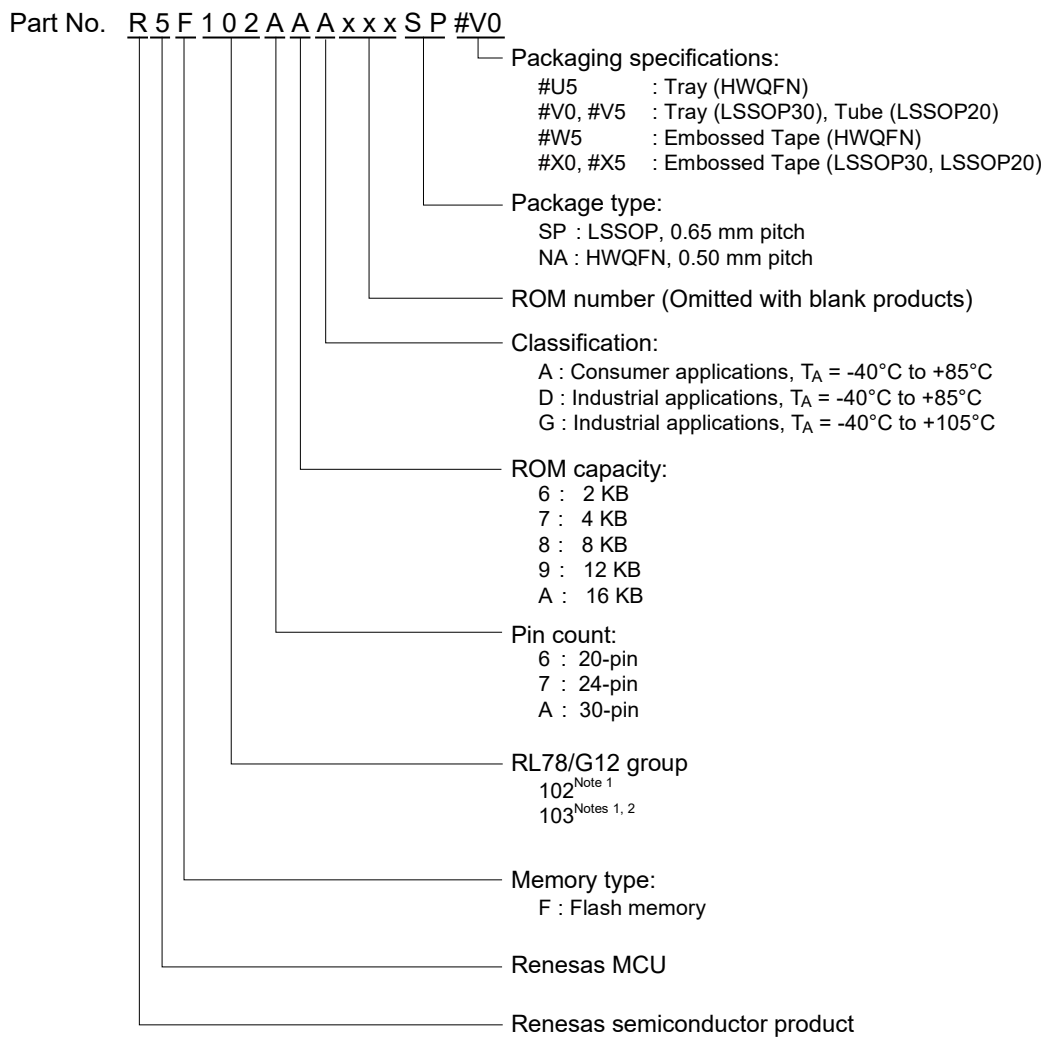
Code flash	Data flash	RAM	20 pins	24 pins	30 pins
16 KB	2 KB	2 KB	–	–	R5F102AA
	–		–	–	R5F103AA
	2 KB	1.5 KB	R5F1026A ^{Note 1}	R5F1027A ^{Note 1}	–
	–		R5F1036A ^{Note 1}	R5F1037A ^{Note 1}	–
12 KB	2KB	1 KB	R5F10269 ^{Note 1}	R5F10279 ^{Note 1}	R5F102A9
	–		R5F10369 ^{Note 1}	R5F10379 ^{Note 1}	R5F103A9
8 KB	2 KB	768 B	R5F10268 ^{Note 1}	R5F10278 ^{Note 1}	R5F102A8
	–		R5F10368 ^{Note 1}	R5F10378 ^{Note 1}	R5F103A8
4 KB	2KB	512 B	R5F10267	R5F10277	R5F102A7
	–		R5F10367	R5F10377	R5F103A7
2 KB	2 KB	256 B	R5F10266 ^{Note 2}	–	–
	–		R5F10366 ^{Note 2}	–	–

- Notes**
- This is 640 bytes when the self-programming function or data flash function is used. (For details, see **CHAPTER 3 CPU ARCHITECTURE** in the RL78/G12 User's Manual.)
 - The self-programming function cannot be used for R5F10266 and R5F10366.

Caution When the flash memory is rewritten via a user program, the code flash area and RAM area are used because each library is used. When using the library, refer to RL78 Family Flash Self Programming Library Type01 User's Manual and RL78 Family Data Flash Library Type04 User's Manual.

1.2 List of Part Numbers

Figure 1-1. Part Number, Memory Size, and Package of RL78/G12



- Notes**
1. For details about the differences between the R5F102 products and the R5F103 products of RL78/G12, see **1.1 Differences between the R5F102 Products and the R5F103 Products**.
 2. Products only for “A: Consumer applications ($T_A = -40$ to $+85^{\circ}\text{C}$)” and “D: Industrial applications ($T_A = -40$ to $+85^{\circ}\text{C}$)”

Table 1-1. List of Ordering Part Numbers

Pin count	Package	Data flash	Fields of Application Note	Part Number
20 pins	20-pin plastic LSSOP (4.4 × 6.5 mm, 0.65 mm pitch)	Mounted	A	R5F1026AASP#V5, R5F10269ASP#V5, R5F10268ASP#V5, R5F10267ASP#V5, R5F10266ASP#V5 R5F1026AASP#X5, R5F10269ASP#X5, R5F10268ASP#X5, R5F10267ASP#X5, R5F10266ASP#X5
			D	R5F1026ADSP#V5, R5F10269DSP#V5, R5F10268DSP#V5, R5F10267DSP#V5, R5F10266DSP#V5 R5F1026ADSP#X5, R5F10269DSP#X5, R5F10268DSP#X5, R5F10267DSP#X5, R5F10266DSP#X5
			G	R5F1026AGSP#V5, R5F10269GSP#V5, R5F10268GSP#V5, R5F10267GSP#V5, R5F10266GSP#V5 R5F1026AGSP#X5, R5F10269GSP#X5, R5F10268GSP#X5, R5F10267GSP#X5, R5F10266GSP#X5
		Not mounted	A	R5F1036AASP#V5, R5F10369ASP#V5, R5F10368ASP#V5, R5F10367ASP#V5, R5F10366ASP#V5 R5F1036AASP#X5, R5F10369ASP#X5, R5F10368ASP#X5, R5F10367ASP#X5, R5F10366ASP#X5
			D	R5F1036ADSP#V5, R5F10369DSP#V5, R5F10368DSP#V5, R5F10367DSP#V5, R5F10366DSP#V5 R5F1036ADSP#X5, R5F10369DSP#X5, R5F10368DSP#X5, R5F10367DSP#X5, R5F10366DSP#X5
			G	R5F1027AANA#U5, R5F10279ANA#U5, R5F10278ANA#U5, R5F10277ANA#U5 R5F1027AANA#W5, R5F10279ANA#W5, R5F10278ANA#W5, R5F10277ANA#W5
24 pins	24-pin plastic HWQFN (4 × 4 mm, 0.5 mm pitch)	Mounted	A	R5F1027AANA#U5, R5F10279ANA#U5, R5F10278ANA#U5, R5F10277ANA#U5 R5F1027AANA#W5, R5F10279ANA#W5, R5F10278ANA#W5, R5F10277ANA#W5
			D	R5F1027ADNA#U5, R5F10279DNA#U5, R5F10278DNA#U5, R5F10277DNA#U5 R5F1027ADNA#W5, R5F10279DNA#W5, R5F10278DNA#W5, R5F10277DNA#W5
			G	R5F1027AGNA#U5, R5F10279GNA#U5, R5F10278GNA#U5, R5F10277GNA#U5 R5F1027AGNA#W5, R5F10279GNA#W5, R5F10278GNA#W5, R5F10277GNA#W5
		Not mounted	A	R5F1037AANA#U5, R5F10379ANA#U5, R5F10378ANA#U5, R5F10377ANA#U5 R5F1037AANA#W5, R5F10379ANA#W5, R5F10378ANA#W5, R5F10377ANA#W5
			D	R5F1037ADNA#U5, R5F10379DNA#U5, R5F10378DNA#U5, R5F10377DNA#U5 R5F1037ADNA#W5, R5F10379DNA#W5, R5F10378DNA#W5, R5F10377DNA#W5
			G	R5F102AAAASP#V0, R5F102A9ASP#V0, R5F102A8ASP#V0, R5F102A7ASP#V0 R5F102AAAASP#X0, R5F102A9ASP#X0, R5F102A8ASP#X0, R5F102A7ASP#X0
30 pins	30-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)	Mounted	A	R5F102AAAASP#V0, R5F102A9ASP#V0, R5F102A8ASP#V0, R5F102A7ASP#V0 R5F102AAAASP#X0, R5F102A9ASP#X0, R5F102A8ASP#X0, R5F102A7ASP#X0
			D	R5F102AADSP#V0, R5F102A9DSP#V0, R5F102A8DSP#V0, R5F102A7DSP#V0 R5F102AADSP#X0, R5F102A9DSP#X0, R5F102A8DSP#X0, R5F102A7DSP#X0
			G	R5F102AAGSP#V0, R5F102A9GSP#V0, R5F102A8GSP#V0, R5F102A7GSP#V0 R5F102AAGSP#X0, R5F102A9GSP#X0, R5F102A8GSP#X0, R5F102A7GSP#X0
		Not mounted	A	R5F103AAAASP#V0, R5F103A9ASP#V0, R5F103A8ASP#V0, R5F103A7ASP#V0 R5F103AAAASP#X0, R5F103A9ASP#X0, R5F103A8ASP#X0, R5F103A7ASP#X0
			D	R5F103AADSP#V0, R5F103A9DSP#V0, R5F103A8DSP#V0, R5F103A7DSP#V0 R5F103AADSP#X0, R5F103A9DSP#X0, R5F103A8DSP#X0, R5F103A7DSP#X0
			G	R5F103AAGSP#V0, R5F103A9GSP#V0, R5F103A8GSP#V0, R5F103A7GSP#V0 R5F103AAGSP#X0, R5F103A9GSP#X0, R5F103A8GSP#X0, R5F103A7GSP#X0

<R>

Note For fields of application, see **Figure 1-1 Part Number, Memory Size, and Package of RL78/G12**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3 Differences between the R5F102 Products and the R5F103 Products

The following are differences between the R5F102 products and the R5F103 products.

- Whether the data flash memory is mounted or not
- High-speed on-chip oscillator oscillation frequency accuracy
- Number of channels in serial interface
- Whether the DMA function is mounted or not
- Whether a part of the safety functions are mounted or not

1.3.1 Data Flash

The data flash memory of 2 KB is mounted on the R5F102 products, but not on the R5F103 products.

Product	Data Flash
<u>R5F102 products</u> R5F1026A, R5F1027A, R5F102AA, R5F10269, R5F10279, R5F102A9, R5F10268, R5F10278, R5F102A8, R5F10267, R5F10277, R5F102A7, R5F10266 <small>Note</small>	2 KB
<u>R5F103 products</u> R5F1036A, R5F1037A, R5F103AA, R5F10369, R5F10379, R5F103A9, R5F10368, R5F10378 R5F103A8, R5F10367, R5F10377, R5F103A7, R5F10366	Not mounted

Note The RAM in the R5F10266 has capacity as small as 256 bytes. Depending on the customer's program specification, the stack area to execute the data flash library may not be kept and data may not be written to or erased from the data flash memory.

Caution When the flash memory is rewritten via a user program, the code flash area and RAM area are used because each library is used. When using the library, refer to RL78 Family Flash Self Programming Library Type01 User's Manual and RL78 Family Data Flash Library Type04 User's Manual.

1.3.2 On-chip oscillator characteristics

(1) High-speed on-chip oscillator oscillation frequency of the R5F102 products

Oscillator	Condition	MIN	MAX	Unit
High-speed on-chip oscillator oscillation frequency accuracy	$T_A = -20$ to $+85^\circ\text{C}$	-1.0	+1.0	%
	$T_A = -40$ to -20°C	-1.5	+1.5	
	$T_A = +85$ to $+105^\circ\text{C}$	-2.0	+2.0	

(2) High-speed on-chip oscillator oscillation frequency of the R5F103 products

Oscillator	Condition	MIN	MAX	Unit
High-speed on-chip oscillator oscillation frequency accuracy	$T_A = -40$ to $+85^\circ\text{C}$	-5.0	+5.0	%

1.3.3 Peripheral Functions

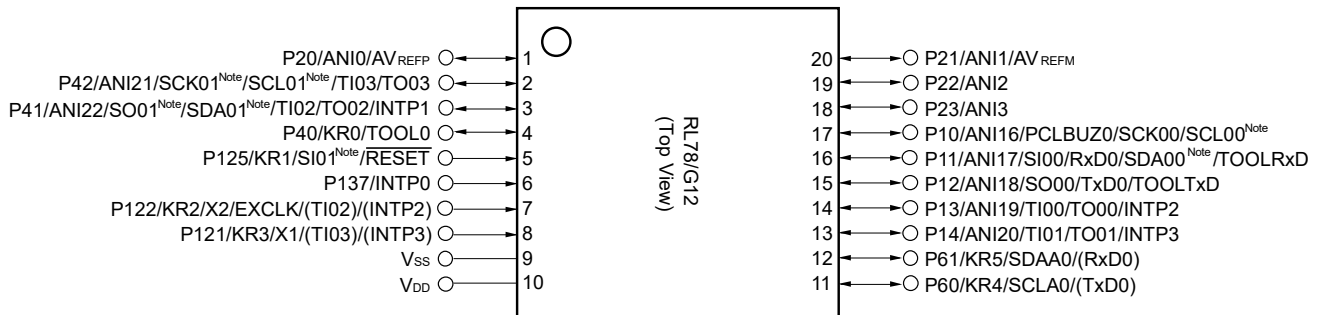
The following are differences in peripheral functions between the R5F102 products and the R5F103 products.

RL78/G12		R5F102 product		R5F103 product	
		20, 24 pin product	30 pin product	20, 24 pin product	30 pin product
Serial interface	UART	1 channel	3 channels	1 channel	
	CSI	2 channels	3 channels	1 channel	
	Simplified I ² C	2 channels	3 channels	None	
DMA function		2 channels		None	
Safety function	CRC operation	Yes		None	
	RAM guard	Yes		None	
	SFR guard	Yes		None	

1.4 Pin Configuration (Top View)

1.4.1 20-pin products

- <R>
- 20-pin plastic LSSOP (4.4 × 6.5 mm, 0.65 mm pitch)



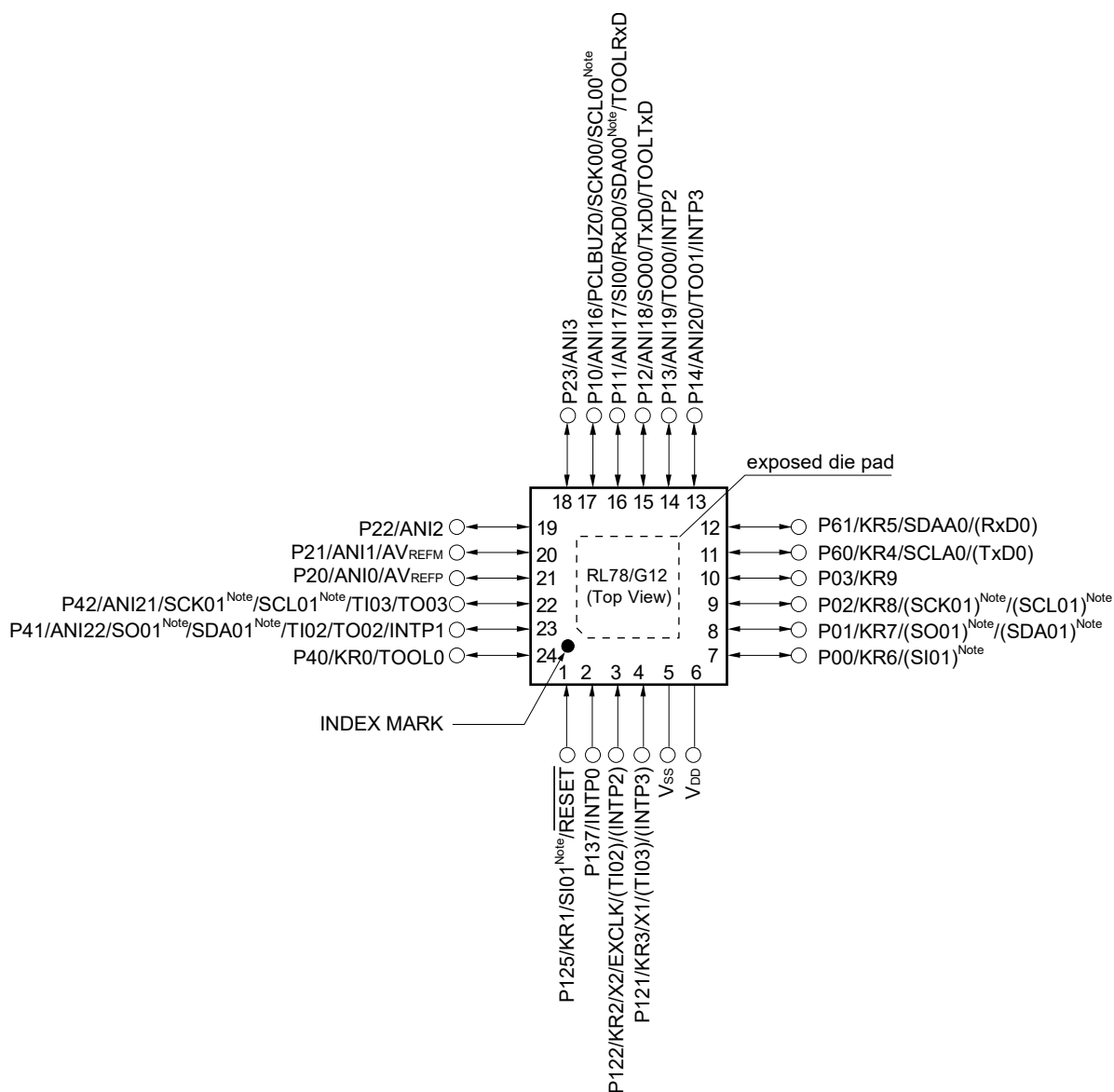
Note Provided only in the R5F102 products.

Remarks 1. For pin identification, see **1.5 Pin Identification**.

- 2.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). See **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G12 User's Manual.

1.4.2 24-pin products

- 24-pin plastic HWQFN (4 × 4 mm, 0.5 mm pitch)



Note Provided only in the R5F102 products.

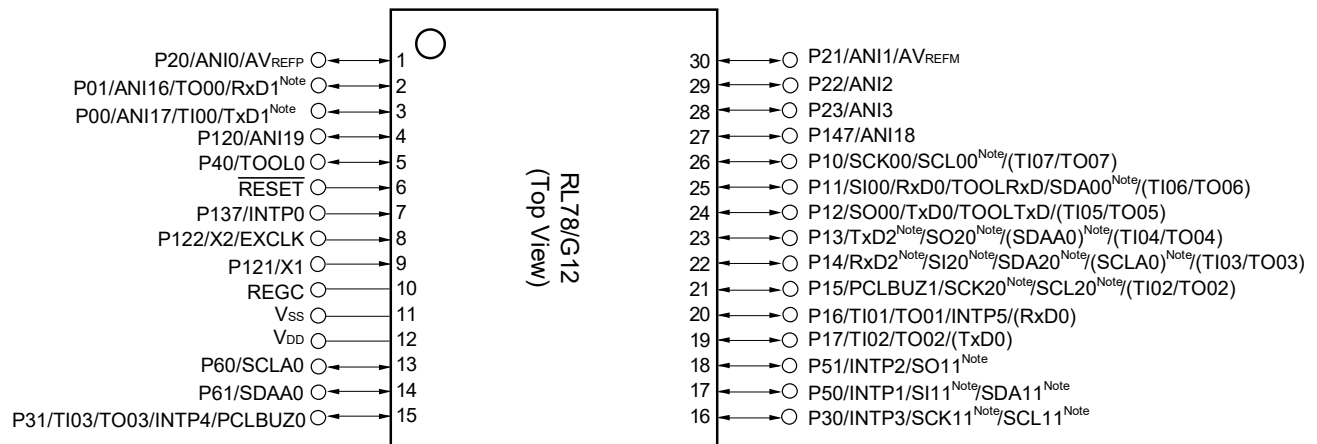
Remarks 1. For pin identification, see 1.5 Pin Identification.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G12 User's Manual.

3. It is recommended to connect an exposed die pad to V_{SS}.

1.4.3 30-pin products

- 30-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)



Note Provided only in the R5F102 products.

Caution Connect the REGC pin to V_{SS} via capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.5 Pin Identification.

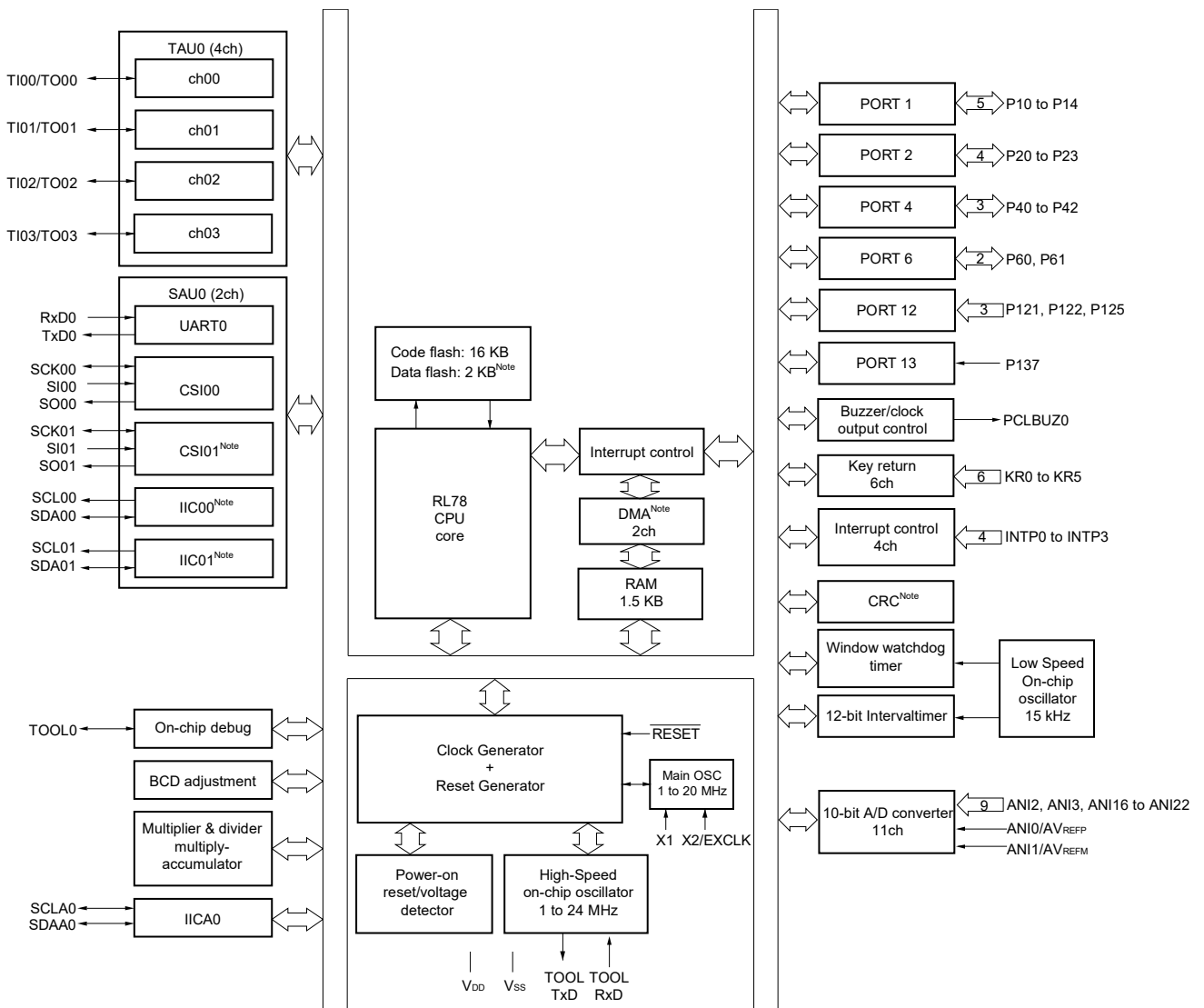
2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). See **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G12 User's Manual.

1.5 Pin Identification

ANI0 to ANI3, ANI16 to ANI22:	Analog input	REGC:	Regulator Capacitance
AVREFM:	Analog Reference Voltage Minus	RESET:	Reset
AVREFP:	Analog reference voltage plus	RxD0 to RxD2:	Receive Data
EXCLK:	External Clock Input (Main System Clock)	SCK00, SCK01, SCK11, SCK20:	Serial Clock Input/Output
INTP0 to INTP5	Interrupt Request From Peripheral	SCL00, SCL01, SCL11, SCL20, SCLA0:	Serial Clock Input/Output
KR0 to KR9:	Key Return	SDA00, SDA01, SDA11, SDA20, SDAA0:	Serial Data Input/Output
P00 to P03:	Port 0	SI00, SI01, SI11, SI20:	Serial Data Input
P10 to P17:	Port 1	SO00, SO01, SO11, SO20:	Serial Data Output
P20 to P23:	Port 2	TI00 to TI07:	Timer Input
P30 to P31:	Port 3	TO00 to TO07:	Timer Output
P40 to P42:	Port 4	TOOL0:	Data Input/Output for Tool
P50, P51:	Port 5	TOOLRxD, TOOLTxD:	Data Input/Output for External Device
P60, P61:	Port 6	TxD0 to TxD2:	Transmit Data
P120 to P122, P125:	Port 12	VDD:	Power supply
P137:	Port 13	VSS:	Ground
P147:	Port 14	X1, X2:	Crystal Oscillator (Main System Clock)
PCLBUZ0, PCLBUZ1:	Programmable Clock Output/ Buzzer Output		

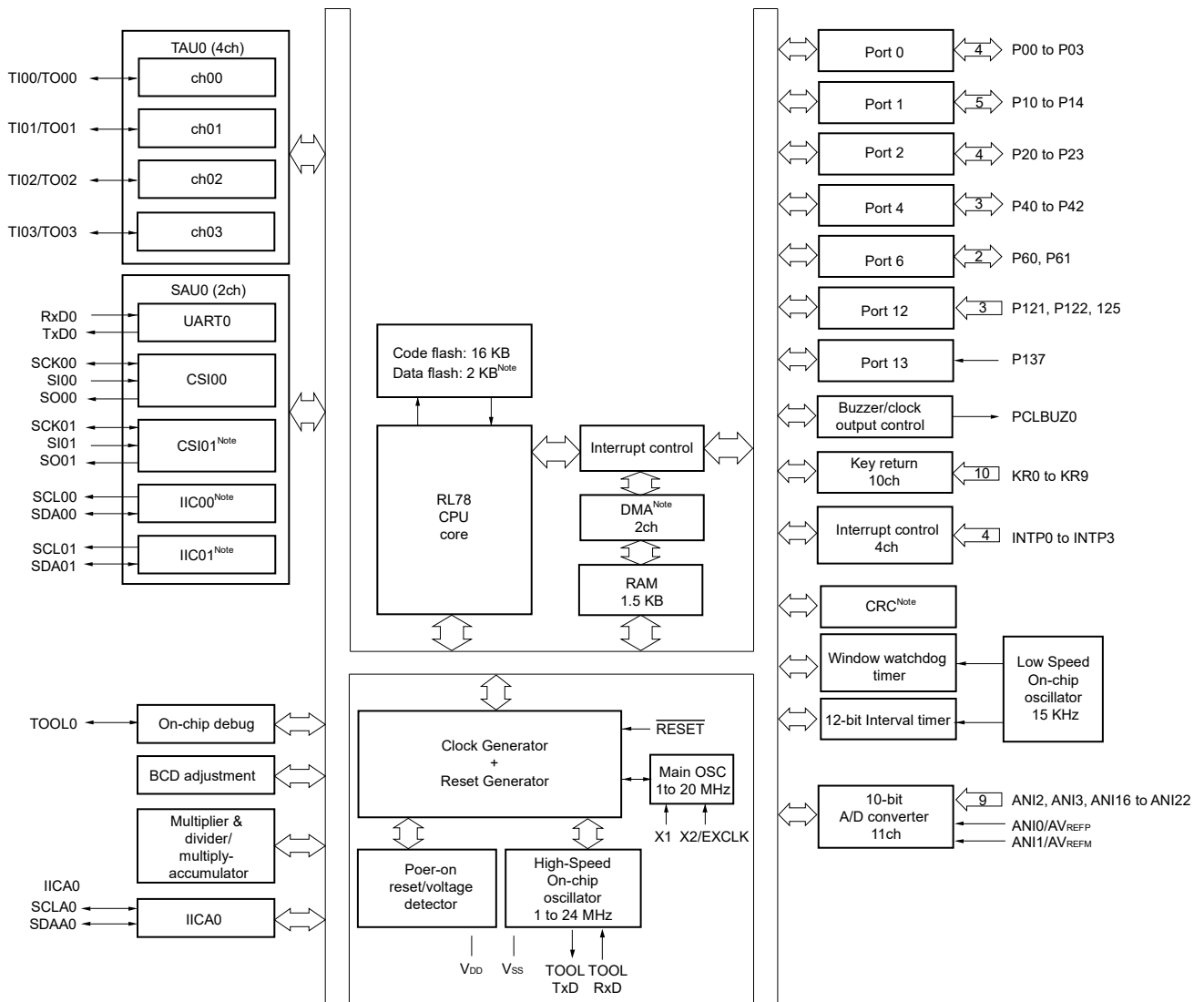
1.6 Block Diagram

1.6.1 20-pin products



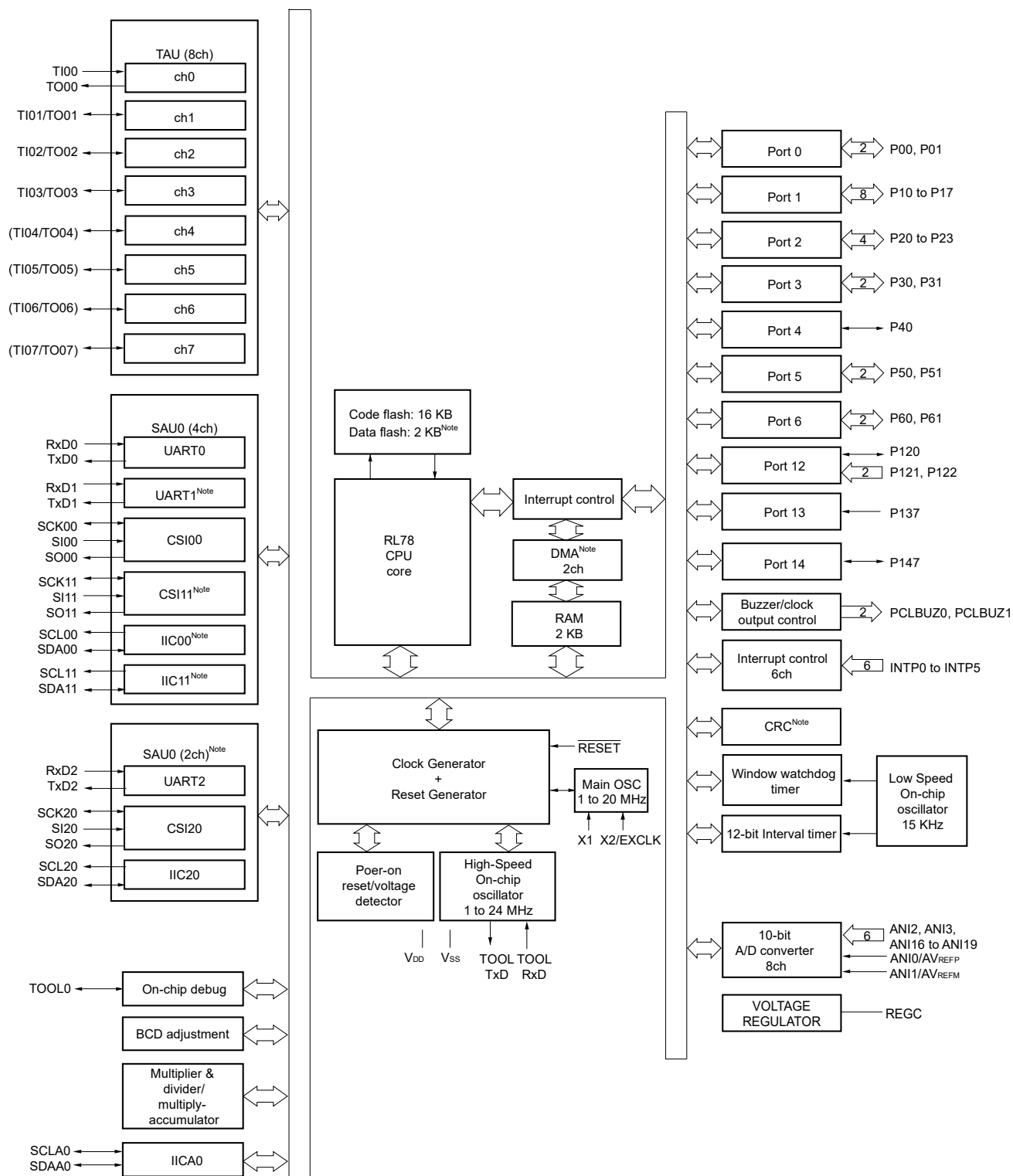
Note Provided only in the R5F102 products.

1.6.2 24-pin products



Note Provided only in the R5F102 products.

1.6.3 30-pin products



Note Provided only in the R5F102 products.

Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). See **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G12 User's Manual.

1.7 Outline of Functions

This outline describes the function at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

(1/2)

Item		20-pin		24-pin		30-pin	
		R5F1026x	R5F1036x	R5F1027x	R5F1037x	R5F102Ax	R5F103Ax
Code flash memory		2 to 16 KB ^{Note 1}		4 to 16 KB			
Data flash memory		2 KB	–	2 KB	–	2 KB	–
RAM		256 B to 1.5 KB		512 B to 1.5 KB		512 B to 2KB	
Address space		1 MB					
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (High-speed main) mode : 1 to 20 MHz ($V_{DD} = 2.7$ to 5.5 V), HS (High-speed main) mode : 1 to 16 MHz ($V_{DD} = 2.4$ to 5.5 V), LS (Low-speed main) mode : 1 to 8 MHz ($V_{DD} = 1.8$ to 5.5 V)					
	High-speed on-chip oscillator clock	HS (High-speed main) mode : 1 to 24 MHz ($V_{DD} = 2.7$ to 5.5 V), HS (High-speed main) mode : 1 to 16 MHz ($V_{DD} = 2.4$ to 5.5 V), LS (Low-speed main) mode : 1 to 8 MHz ($V_{DD} = 1.8$ to 5.5 V)					
Low-speed on-chip oscillator clock		15 kHz (TYP)					
General-purpose register		(8-bit register × 8) × 4 banks					
Minimum instruction execution time		0.04167 μs (High-speed on-chip oscillator clock: $f_{IH} = 24$ MHz operation)					
		0.05 μs (High-speed system clock: $f_{MX} = 20$ MHz operation)					
Instruction set		<ul style="list-style-type: none"> • Data transfer (8/16 bits) • Adder and subtractor/logical operation (8/16 bits) • Multiplication (8 bits × 8 bits) • Rotate, barrel shift, and bit manipulation (set, reset, test, and Boolean operation), etc. 					
I/O port	Total	18		22		26	
	CMOS I/O	12 (N-ch O.D. I/O [V_{DD} withstand voltage]: 4)		16 (N-ch O.D. I/O [V_{DD} withstand voltage]: 5)		21 (N-ch O.D. I/O [V_{DD} withstand voltage]: 9)	
	CMOS input	4		4		3	
	N-ch open-drain I/O (6 V tolerance)	2					
Timer	16-bit timer	4 channels				8 channels	
	Watchdog timer	1 channel					
	12-bit Interval timer	1 channel					
	Timer output	4 channels (PWM outputs: 3 ^{Note 3})				8 channels (PWM outputs: 7 ^{Notes 2, 3})	

- Notes**
1. The self-programming function cannot be used in the R5F10266 and R5F10366.
 2. The maximum number of channels when PIOR0 is set to 1.
 3. The number of PWM outputs varies depending on the setting of channels in use (the number of masters and slaves). (See **6.9.3 Operation as multiple PWM output function** in the RL78/G12 User's Manual.)

Caution When the flash memory is rewritten via a user program, the code flash area and RAM area are used because each library is used. When using the library, refer to RL78 Family Flash Self Programming Library Type01 User's Manual and RL78 Family Data Flash Library Type04 User's Manual.

(2/2)

Item	20-pin		24-pin		30-pin				
	R5F1026x	R5F1036x	R5F1027x	R5F1037x	R5F102Ax	R5F103Ax			
Clock output/buzzer output	1				2				
	2.44 kHz to 10 MHz: (Peripheral hardware clock: $f_{\text{MAIN}} = 20$ MHz operation)								
8/10-bit resolution A/D converter	11 channels				8 channels				
Serial interface	[R5F1026x (20-pin), R5F1027x (24-pin)]								
	<ul style="list-style-type: none"> • CSI: 2 channels/Simplified I²C: 2 channels/UART: 1 channel 								
	[R5F102Ax (30-pin)]								
I ² C bus	<ul style="list-style-type: none"> • CSI: 1 channel/Simplified I²C: 1 channel/UART: 1 channel • CSI: 1 channel/Simplified I²C: 1 channel/UART: 1 channel • CSI: 1 channel/Simplified I²C: 1 channel/UART: 1 channel 								
	[R5F1036x (20-pin), R5F1037x (24-pin)]								
	<ul style="list-style-type: none"> • CSI: 1 channel/Simplified I²C: 0 channel/UART: 1 channel 								
Multiplier and divider/multiply-accumulator	[R5F103Ax (30-pin)]								
	<ul style="list-style-type: none"> • CSI: 1 channel/Simplified I²C: 0 channel/UART: 1 channel 								
	1 channel								
DMA controller	<ul style="list-style-type: none"> • 16 bits × 16 bits = 32 bits (unsigned or signed) • 32 bits × 32 bits = 32 bits (unsigned) • 16 bits × 16 bits + 32 bits = 32 bits (unsigned or signed) 								
	2 channels		–		2 channels		–		
	18		16		18		16		
Vectored interrupt sources	Internal	18		16		26		19	
	External	5				6			
Key interrupt	6		10		–				
Reset	<ul style="list-style-type: none"> • Reset by $\overline{\text{RESET}}$ pin • Internal reset by watchdog timer • Internal reset by power-on-reset • Internal reset by voltage detector • Internal reset by illegal instruction execution ^{Note} • Internal reset by RAM parity error • Internal reset by illegal-memory access 								
Power-on-reset circuit	<ul style="list-style-type: none"> • Power-on-reset: 1.51 V (TYP) • Power-down-reset: 1.50 V (TYP) 								
Voltage detector	<ul style="list-style-type: none"> • Rising edge : 1.88 to 4.06 V (12 stages) • Falling edge : 1.84 to 3.98 V (12 stages) 								
On-chip debug function	Provided								
Power supply voltage	$V_{\text{DD}} = 1.8$ to 5.5 V								
Operating ambient temperature	$T_{\text{A}} = -40$ to $+85^{\circ}\text{C}$ (A: Consumer applications, D: Industrial applications), $T_{\text{A}} = -40$ to $+105^{\circ}\text{C}$ (G: Industrial applications)								

Note The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.

2. ELECTRICAL SPECIFICATIONS (T_A = -40 to +85°C)

This chapter describes the following electrical specifications.

Target products A: Consumer applications T_A = -40 to +85°C

R5F102xxAxx, R5F103xxAxx

D: Industrial applications T_A = -40 to +85°C

R5F102xxDxx, R5F103xxDxx

G: Industrial applications when T_A = -40 to +105°C products is used in the range of T_A = -40 to +85°C

R5F102xxGxx

- Cautions**
- 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.**
 - 2. The pins mounted depend on the product. Refer to 2.1 Port Functions to 2.2.1 Functions for each product in the RL78/G12 User's Manual.**

2.1 Absolute Maximum Ratings

Absolute Maximum Ratings (TA = 25°C)

Parameter	Symbols	Conditions		Ratings	Unit
Supply Voltage	V _{DD}			-0.5 to + 6.5	V
REGC terminal input voltage ^{Note1}	V _{IREGC}	REGC		-0.3 to +2 and -0.3 to V _{DD} + 0.3 ^{Note 2}	V
Input Voltage	V _{I1}	Other than P60, P61		-0.3 to V _{DD} + 0.3 ^{Note 3}	V
	V _{I2}	P60, P61 (N-ch open drain)		-0.3 to 6.5	V
Output Voltage	V _O			-0.3 to V _{DD} + 0.3 ^{Note 3}	V
Analog input voltage	V _{AI}	20-, 24-pin products: ANI0 to ANI3, ANI16 to ANI22 30-pin products: ANI0 to ANI3, ANI16 to ANI19		-0.3 to V _{DD} + 0.3 and -0.3 to AV _{REF(+)} +0.3 ^{Notes 3, 4}	V
Output current, high	I _{OH1}	Per pin	Other than P20 to P23	-40	mA
		Total of all pins	All the terminals other than P20 to P23	-170	mA
			20-, 24-pin products: P40 to P42 30-pin products: P00, P01, P40, P120	-70	mA
			20-, 24-pin products: P00 to P03 ^{Note 5} , P10 to P14 30-pin products: P10 to P17, P30, P31, P50, P51, P147	-100	mA
	I _{OH2}	Per pin	P20 to P23	-0.5	mA
		Total of all pins		-2	mA
Output current, low	I _{OL1}	Per pin	Other than P20 to P23	40	mA
		Total of all pins	All the terminals other than P20 to P23	170	mA
			20-, 24-pin products: P40 to P42 30-pin products: P00, P01, P40, P120	70	mA
			20-, 24-pin products: P00 to P03 ^{Note 5} , P10 to P14, P60, P61 30-pin products: P10 to P17, P30, P31, P50, P51, P60, P61, P147	100	mA
	I _{OL2}	Per pin	P20 to P23	1	mA
		Total of all pins		5	mA
Operating ambient temperature	T _A			-40 to +85	°C
Storage temperature	T _{stg}			-65 to +150	°C

- Notes**
- 30-pin product only.
 - Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μF). This value determines the absolute maximum rating of the REGC pin. Do not use it with voltage applied.
 - Must be 6.5 V or lower.
 - Do not exceed AV_{REF(+)} + 0.3 V in case of A/D conversion target pin.
 - 24-pin products only.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

- Remarks**
- Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
 - AV_{REF(+)} : + side reference voltage of the A/D converter.
 - V_{SS} : Reference voltage

2.2 Oscillator Characteristics

2.2.1 X1 oscillator characteristics

(TA = -40 to +85°C, 1.8 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (fx) ^{Note}	Ceramic resonator / crystal oscillator	2.7 V ≤ VDD ≤ 5.5 V	1.0		20.0	MHz
		1.8 V ≤ VDD < 2.7 V	1.0		8.0	

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator, refer to 5.4 System Clock Oscillator in the RL78/G12 User's Manual.

2.2.2 On-chip oscillator characteristics

(TA = -40 to +85°C, 1.8 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit	
High-speed on-chip oscillator clock frequency ^{Notes 1, 2}	f _H		1		24	MHz	
High-speed on-chip oscillator clock frequency accuracy		R5F102 products	TA = -20 to +85°C	-1.0		+1.0	%
			TA = -40 to -20°C	-1.5		+1.5	%
		R5F103 products	-5.0		+5.0	%	
Low-speed on-chip oscillator clock frequency	f _L			15		kHz	
Low-speed on-chip oscillator clock frequency accuracy			-15		+15	%	

Notes 1. High-speed on-chip oscillator frequency is selected by bits 0 to 3 of option byte (000C2H) and bits 0 to 2 of HOCODIV register.

2. This only indicates the oscillator characteristics. Refer to AC Characteristics for instruction execution time.

2.3 DC Characteristics

2.3.1 Pin characteristics

(TA = -40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

(1/4)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit		
Output current, high ^{Note 1}	I _{OH1}	20-, 24-pin products: Per pin for P00 to P03 ^{Note 4} , P10 to P14, P40 to P42 30-pin products: Per pin for P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147			-10.0 ^{Note 2}	mA		
		20-, 24-pin products: Total of P40 to P42 30-pin products: Total of P00, P01, P40, P120 (When duty ≤ 70% ^{Note 3})	4.0 V ≤ V _{DD} ≤ 5.5 V			-30.0	mA	
			2.7 V ≤ V _{DD} < 4.0 V			-6.0	mA	
			1.8 V ≤ V _{DD} < 2.7 V			-4.5	mA	
		20-, 24-pin products: Total of P00 to P03 ^{Note 4} , P10 to P14 30-pin products: Total of P10 to P17, P30, P31, P50, P51, P147 (When duty ≤ 70% ^{Note 3})	4.0 V ≤ V _{DD} ≤ 5.5 V			-80.0	mA	
			2.7 V ≤ V _{DD} < 4.0 V			-18.0	mA	
			1.8 V ≤ V _{DD} < 2.7 V			-10.0	mA	
		Total of all pins (When duty ≤ 70% ^{Note 3})				-100	mA	
		I _{OH2}	Per pin for P20 to P23				-0.1	mA
			Total of all pins				-0.4	mA

- Notes**
- value of current at which the device operation is guaranteed even if the current flows from the V_{DD} pin to an output pin.
 - However, do not exceed the total current value.
 - The output current value under conditions where the duty factor ≤ 70%.
If duty factor > 70%: The output current value can be calculated with the following expression (where n represents the duty factor as a percentage).
 - Total output current of pins = (I_{OH} × 0.7)/(n × 0.01)
 <Example> Where n = 80% and I_{OH} = -10.0 mA
 Total output current of pins = (-10.0 × 0.7)/(80 × 0.01) ≅ -8.7 mA
 However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.
 - 24-pin products only.

Caution P10 to P12 and P41 for 20-pin products, P01, P10 to P12, and P41 for 24-pin products, and P00, P10 to P15, P17, and P50 for 30-pin products do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(TA = -40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

(2/4)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit	
Output current, low ^{Note 1}	I _{OL1}	20-, 24-pin products: Per pin for P00 to P03 ^{Note 4} , P10 to P14, P40 to P42			20.0 ^{Note 2}	mA	
		30-pin products: Per pin for P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147					
		Per pin for P60, P61			15.0 ^{Note 2}	mA	
	20-, 24-pin products: Total of P40 to P42		4.0 V ≤ V _{DD} ≤ 5.5 V			60.0	mA
			2.7 V ≤ V _{DD} < 4.0 V			9.0	mA
			30-pin products: Total of P00, P01, P40, P120 (When duty ≤ 70% ^{Note 3})	1.8 V ≤ V _{DD} < 2.7 V			1.8
	20-, 24-pin products: Total of P00 to P03 ^{Note 4} , P10 to P14, P60, P61		4.0 V ≤ V _{DD} ≤ 5.5 V			80.0	mA
			2.7 V ≤ V _{DD} < 4.0 V			27.0	mA
			30-pin products: Total of P10 to P17, P30, P31, P50, P51, P60, P61, P147 (When duty ≤ 70% ^{Note 3})	1.8 V ≤ V _{DD} < 2.7 V			5.4
			Total of all pins (When duty ≤ 70% ^{Note 3})			140	mA
I _{OL2}		Per pin for P20 to P23			0.4	mA	
		Total of all pins			1.6	mA	

- Notes**
- Value of current at which the device operation is guaranteed even if the current flows from an output pin to the V_{SS} pin.
 - However, do not exceed the total current value.
 - The output current value under conditions where the duty factor ≤ 70%.
If duty factor > 70%: The output current value can be calculated with the following expression (where n represents the duty factor as a percentage).
 - Total output current of pins = (I_{OL} × 0.7)/(n × 0.01)
 <Example> Where n = 80% and I_{OL} = 10.0 mA
 Total output current of pins = (10.0 × 0.7)/(80 × 0.01) ≅ 8.7 mA
 However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.
 - 24-pin products only.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(TA = -40 to +85°C, 1.8 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

(3/4)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input voltage, high	VIH1	Normal input buffer 20-, 24-pin products: P00 to P03 ^{Note 2} , P10 to P14, P40 to P42 30-pin products: P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147	0.8VDD		VDD	V
			VIH2	TTL input buffer	4.0 V ≤ VDD ≤ 5.5 V	2.2
	VIH2	20-, 24-pin products: P10, P11 30-pin products: P01, P10, P11, P13 to P17	3.3 V ≤ VDD < 4.0 V	2.0	VDD	V
			1.8 V ≤ VDD < 3.3 V	1.5	VDD	V
			VIH3	P20 to P23	0.7VDD	VDD
	VIH4	P60, P61	0.7VDD	6.0	V	
VIH5	P121, P122, P125 ^{Note 1} , P137, EXCLK, RESET	0.8VDD	VDD	V		
Input voltage, low	VIL1	Normal input buffer 20-, 24-pin products: P00 to P03 ^{Note 2} , P10 to P14, P40 to P42 30-pin products: P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147	0		0.2VDD	V
			VIL2	TTL input buffer	4.0 V ≤ VDD ≤ 5.5 V	0
	VIL2	20-, 24-pin products: P10, P11 30-pin products: P01, P10, P11, P13 to P17	3.3 V ≤ VDD < 4.0 V	0	0.5	V
			1.8 V ≤ VDD < 3.3 V	0	0.32	V
			VIL3	P20 to P23	0	0.3VDD
	VIL4	P60, P61	0	0.3VDD	V	
VIL5	P121, P122, P125 ^{Note 1} , P137, EXCLK, RESET	0	0.2VDD	V		
Output voltage, high	VOH1	20-, 24-pin products: P00 to P03 ^{Note 2} , P10 to P14, P40 to P42 30-pin products: P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147	4.0 V ≤ VDD ≤ 5.5 V, IOH1 = -10.0 mA	VDD-1.5		V
			4.0 V ≤ VDD ≤ 5.5 V, IOH1 = -3.0 mA	VDD-0.7		V
			2.7 V ≤ VDD ≤ 5.5 V, IOH1 = -2.0 mA	VDD-0.6		V
			1.8 V ≤ VDD ≤ 5.5 V, IOH1 = -1.5 mA	VDD-0.5		V
	VOH2	P20 to P23	IOH2 = -100 μA	VDD-0.5		V

Notes 1. 20, 24-pin products only.

2. 24-pin products only.

Caution The maximum value of VIH of pins P10 to P12 and P41 for 20-pin products, P01, P10 to P12, and P41 for 24-pin products, and P00, P10 to P15, P17, and P50 for 30-pin products is VDD even in N-ch open-drain mode.

High level is not output in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(TA = -40 to +85°C, 1.8 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

(4/4)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit	
Output voltage, low	VOL1	20-, 24-pin products: P00 to P03 ^{Note} , P10 to P14, P40 to P42 30-pin products: P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147	4.0 V ≤ VDD ≤ 5.5 V, IOL1 = 20.0 mA			1.3	V	
			4.0 V ≤ VDD ≤ 5.5 V, IOL1 = 8.5 mA			0.7	V	
			2.7 V ≤ VDD ≤ 5.5 V, IOL1 = 3.0 mA			0.6	V	
			2.7 V ≤ VDD ≤ 5.5 V, IOL1 = 1.5 mA			0.4	V	
			1.8 V ≤ VDD ≤ 5.5 V, IOL1 = 0.6 mA			0.4	V	
	VOL2	P20 to P23	IOL2 = 400 μA			0.4	V	
	VOL3	P60, P61	4.0 V ≤ VDD ≤ 5.5 V, IOL1 = 15.0 mA			2.0	V	
			4.0 V ≤ VDD ≤ 5.5 V, IOL1 = 5.0 mA			0.4	V	
			2.7 V ≤ VDD ≤ 5.5 V, IOL1 = 3.0 mA			0.4	V	
			1.8 V ≤ VDD ≤ 5.5 V, IOL1 = 2.0 mA			0.4	V	
Input leakage current, high	ILIH1	Other than P121, P122	Vi = VDD			1	μA	
	ILIH2	P121, P122 (X1, X2/EXCLK)	Vi = VDD	Input port or external clock input			1	μA
				When resonator connected			10	μA
Input leakage current, low	ILIL1	Other than P121, P122	Vi = VSS			-1	μA	
	ILIL2	P121, P122 (X1, X2/EXCLK)	Vi = VSS	Input port or external clock input			-1	μA
				When resonator connected			-10	μA
On-chip pull-up resistance	Ru	20-, 24-pin products: P00 to P03 ^{Note} , P10 to P14, P40 to P42, P125, RESET 30-pin products: P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147	Vi = VSS, input port	10	20	100	kΩ	

Note 24-pin products only.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2.3.2 Supply current characteristics

(1) 20-, 24-pin products

(TA = -40 to +85°C, 1.8 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

(1/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit		
Supply current ^{Note 1}	IDD1	Operating mode	HS(High-speed main) mode ^{Note 4}	f _{IH} = 24 MHz ^{Note 3}	Basic operation	V _{DD} = 5.0 V		1.5		mA	
						V _{DD} = 3.0 V		1.5			
					Normal operation	V _{DD} = 5.0 V		3.3	5.0	mA	
						V _{DD} = 3.0 V		3.3	5.0		
				f _{IH} = 16 MHz ^{Note 3}	V _{DD} = 5.0 V		2.5	3.7	mA		
					V _{DD} = 3.0 V		2.5	3.7			
					LS(Low-speed main) mode ^{Note 4}	f _{IH} = 8 MHz ^{Note 3}	V _{DD} = 3.0 V		1.2	1.8	mA
						V _{DD} = 2.0 V		1.2	1.8		
			HS(High-speed main) mode ^{Note 4}	f _{MX} = 20 MHz ^{Note 2} , V _{DD} = 5.0 V	Square wave input			2.8	4.4	mA	
						Resonator connection			3.0		4.6
					Square wave input			2.8	4.4	mA	
						Resonator connection			3.0		4.6
				f _{MX} = 20 MHz ^{Note 2} , V _{DD} = 3.0 V	Square wave input			1.8	2.6	mA	
						Resonator connection			1.8		2.6
					Square wave input			1.8	2.6	mA	
						Resonator connection			1.8		2.6
f _{MX} = 10 MHz ^{Note 2} , V _{DD} = 5.0 V	Square wave input			1.1	1.7	mA					
		Resonator connection			1.1		1.7				
	Square wave input			1.1	1.7	mA					
		Resonator connection			1.1		1.7				
f _{MX} = 10 MHz ^{Note 2} , V _{DD} = 3.0 V	Square wave input			1.1	1.7	mA					
		Resonator connection			1.1		1.7				
	Square wave input			1.1	1.7	mA					
		Resonator connection			1.1		1.7				
LS(Low-speed main) mode ^{Note 4}	f _{MX} = 8 MHz ^{Note 2} , V _{DD} = 3.0 V	Square wave input			1.1	1.7	mA				
			Resonator connection			1.1		1.7			
	f _{MX} = 8 MHz ^{Note 2} , V _{DD} = 2.0 V	Square wave input			1.1	1.7	mA				
			Resonator connection			1.1		1.7			

- Notes**
- Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - When high-speed on-chip oscillator clock is stopped.
 - When high-speed system clock is stopped
 - Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.
 HS (High speed main) mode: V_{DD} = 2.7 V to 5.5 V @1 MHz to 24 MHz
 V_{DD} = 2.4 V to 5.5 V @1 MHz to 16 MHz
 LS (Low speed main) mode: V_{DD} = 1.8 V to 5.5 V @1 MHz to 8 MHz

- Remarks**
- f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - f_{IH}: high-speed on-chip oscillator clock frequency
 - Temperature condition of the TYP. value is TA = 25°C.

(1) 20-, 24-pin products

(TA = -40 to +85°C, 1.8 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

(2/2)

Parameter	Symbol	Conditions			MIN.	TYP.	MAX.	Unit		
Supply current ^{Note 1}	IDD2 ^{Note 2}	HALT mode	HS (High-speed main) mode ^{Note 6}	f _{IH} = 24 MHz ^{Note 4}	V _{DD} = 5.0 V		440	1210	μA	
					V _{DD} = 3.0 V		440	1210		
				f _{IH} = 16 MHz ^{Note 4}	V _{DD} = 5.0 V		400	950	μA	
					V _{DD} = 3.0 V		400	950		
				LS (Low-speed main) mode ^{Note 6}	f _{IH} = 8 MHz ^{Note 4}	V _{DD} = 3.0 V		270	542	μA
						V _{DD} = 2.0 V		270	542	
			HS (High-speed main) mode ^{Note 6}	f _{MX} = 20 MHz ^{Note 3} , V _{DD} = 5.0 V	Square wave input		280	1000	μA	
					Resonator connection		450	1170		
				f _{MX} = 20 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		280	1000	μA	
					Resonator connection		450	1170		
				f _{MX} = 10 MHz ^{Note 3} , V _{DD} = 5.0 V	Square wave input		190	590	μA	
					Resonator connection		260	660		
				f _{MX} = 10 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		190	590	μA	
					Resonator connection		260	660		
LS (Low-speed main) mode ^{Note 6}	f _{MX} = 8 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		110	360	μA				
		Resonator connection		150	416					
	f _{MX} = 8 MHz ^{Note 3} , V _{DD} = 2.0 V	Square wave input		110	360	μA				
		Resonator connection		150	416					
IDD3 ^{Note 5}	STOP mode	T _A = -40°C				0.19	0.50	μA		
		T _A = +25°C				0.24	0.50			
		T _A = +50°C				0.32	0.80			
		T _A = +70°C				0.48	1.20			
		T _A = +85°C				0.74	2.20			

- Notes 1.** Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
2. During HALT instruction execution by flash memory.
 3. When high-speed on-chip oscillator clock is stopped.
 4. When high-speed system clock is stopped.
 5. Not including the current flowing into the 12-bit interval timer and watchdog timer.
 6. Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.
 HS (High speed main) mode: V_{DD} = 2.7 V to 5.5 V @1 MHz to 24 MHz
 V_{DD} = 2.4 V to 5.5 V @1 MHz to 16 MHz
 LS (Low speed main) mode: V_{DD} = 1.8 V to 5.5 V @1 MHz to 8 MHz

- Remarks 1.** f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
2. f_{IH}: high-speed on-chip oscillator clock frequency
 3. Except temperature condition of the TYP. value is T_A = 25°C, other than STOP mode

(2) 30-pin products

(TA = -40 to +85°C, 1.8 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

(1/2)

Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit	
Supply current ^{Note 1}	IDD1	Operating mode	HS (High-speed main) mode ^{Note 4}	f _{IH} = 24 MHz ^{Note 3}	Basic operation	V _{DD} = 5.0 V		1.5		mA	
						V _{DD} = 3.0 V		1.5			
					Normal operation	V _{DD} = 5.0 V		3.7	5.5	mA	
						V _{DD} = 3.0 V		3.7	5.5		
				f _{IH} = 16 MHz ^{Note 3}	V _{DD} = 5.0 V		2.7	4.0	mA		
					V _{DD} = 3.0 V		2.7	4.0			
					LS (Low-speed main) mode ^{Note 4}	f _{IH} = 8 MHz ^{Note 3}	V _{DD} = 3.0 V		1.2	1.8	mA
						V _{DD} = 2.0 V		1.2	1.8		
			HS (High-speed main) mode ^{Note 4}	f _{MX} = 20 MHz ^{Note 2} , V _{DD} = 5.0 V	Square wave input		3.0	4.6	mA		
					Resonator connection		3.2	4.8			
					f _{MX} = 20 MHz ^{Note 2} , V _{DD} = 3.0 V	Square wave input		3.0	4.6	mA	
						Resonator connection		3.2	4.8		
				f _{MX} = 10 MHz ^{Note 2} , V _{DD} = 5.0 V	Square wave input		1.9	2.7	mA		
					Resonator connection		1.9	2.7			
				f _{MX} = 10 MHz ^{Note 2} , V _{DD} = 3.0 V	Square wave input		1.9	2.7	mA		
					Resonator connection		1.9	2.7			
LS (Low-speed main) mode ^{Note 4}	f _{MX} = 8 MHz ^{Note 2} , V _{DD} = 3.0 V	Square wave input		1.1	1.7	mA					
		Resonator connection		1.1	1.7						
	f _{MX} = 8 MHz ^{Note 2} , V _{DD} = 2.0 V	Square wave input		1.1	1.7	mA					
		Resonator connection		1.1	1.7						

Notes 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

2. When high-speed on-chip oscillator clock is stopped.

3. When high-speed system clock is stopped

4. Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.

HS (High speed main) mode: V_{DD} = 2.7 V to 5.5 V @1 MHz to 24 MHz

V_{DD} = 2.4 V to 5.5 V @1 MHz to 16 MHz

LS (Low speed main) mode: V_{DD} = 1.8 V to 5.5 V @1 MHz to 8 MHz

Remarks 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

2. f_{IH}: high-speed on-chip oscillator clock frequency

3. Temperature condition of the TYP. value is TA = 25°C.

(2) 30-pin products

(TA = -40 to +85°C, 1.8 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

(2/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit	
Supply current ^{Note 1}	IDD2 ^{Note 2}	HALT mode	HS (High-speed main) mode ^{Note 6}	f _{IH} = 24 MHz ^{Note 4}	V _{DD} = 5.0 V		440	1280	μA	
					V _{DD} = 3.0 V		440	1280		
				f _{IH} = 16 MHz ^{Note 4}	V _{DD} = 5.0 V		400	1000	μA	
					V _{DD} = 3.0 V		400	1000		
				LS (Low-speed main) mode ^{Note 6}	f _{IH} = 8 MHz ^{Note 4}	V _{DD} = 3.0 V		260	530	μA
						V _{DD} = 2.0 V		260	530	
			HS (High-speed main) mode ^{Note 6}	f _{MX} = 20 MHz ^{Note 3} , V _{DD} = 5.0 V	Square wave input		280	1000	μA	
					Resonator connection		450	1170		
				f _{MX} = 20 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		280	1000	μA	
					Resonator connection		450	1170		
				f _{MX} = 10 MHz ^{Note 3} , V _{DD} = 5.0 V	Square wave input		190	600	μA	
					Resonator connection		260	670		
			f _{MX} = 10 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		190	600	μA		
				Resonator connection		260	670			
			LS (Low-speed main) mode ^{Note 6}	f _{MX} = 8 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		95	330	μA	
					Resonator connection		145	380		
f _{MX} = 8 MHz ^{Note 3} , V _{DD} = 2.0 V	Square wave input			95	330	μA				
	Resonator connection			145	380					
IDD3 ^{Note 5}	STOP mode	T _A = -40°C					0.18	0.50	μA	
		T _A = +25°C					0.23	0.50		
		T _A = +50°C					0.30	1.10		
		T _A = +70°C					0.46	1.90		
		T _A = +85°C					0.75	3.30		

Notes 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

2. During HALT instruction execution by flash memory.
3. When high-speed on-chip oscillator clock is stopped.
4. When high-speed system clock is stopped.
5. Not including the current flowing into the 12-bit interval timer and watchdog timer.
6. Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.

HS (High speed main) mode: V_{DD} = 2.7 V to 5.5 V @1 MHz to 24 MHz

V_{DD} = 2.4 V to 5.5 V @1 MHz to 16 MHz

LS (Low speed main) mode: V_{DD} = 1.8 V to 5.5 V @1 MHz to 8 MHz

Remarks 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

2. f_{IH}: high-speed on-chip oscillator clock frequency
3. Except STOP mode, temperature condition of the TYP. value is T_A = 25°C.

(3) Peripheral functions (Common to all products)**(TA = -40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)**

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Low-speed onchip oscillator operating current	I _{FIL} ^{Note 1}				0.20		μA
12-bit interval timer operating current	I _{TMKA} ^{Notes 1, 2, 3}				0.02		μA
Watchdog timer operating current	I _{WDT} ^{Notes 1, 2, 4}	f _{IL} = 15 kHz			0.22		μA
A/D converter operating current	I _{ADC} ^{Notes 1, 5}	When conversion at maximum speed	Normal mode, AV _{REFP} = V _{DD} = 5.0 V		1.30	1.70	mA
			Low voltage mode, AV _{REFP} = V _{DD} = 3.0 V		0.50	0.70	mA
A/D converter reference voltage operating current	I _{ADREF} ^{Note 1}				75.0		μA
Temperature sensor operating current	I _{TMPS} ^{Note 1}				75.0		μA
LVD operating current	I _{LVD} ^{Notes 1, 6}				0.08		μA
Self-programming operating current	I _{FSP} ^{Notes 1, 8}				2.00	12.20	mA
BGO operating current	I _{BGO} ^{Notes 1, 7}				2.00	12.20	mA
SNOOZE operating current	I _{SNOZ} ^{Note 1}	ADC operation	The mode is performed ^{Note 9}		0.50	0.60	mA
			The A/D conversion operations are performed, Low voltage mode, AV _{REFP} = V _{DD} = 3.0 V		1.20	1.44	mA
		CSI/UART operation		0.70	0.84	mA	

- Notes**
1. Current flowing to the V_{DD}.
 2. When high speed on-chip oscillator and high-speed system clock are stopped.
 3. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator). The current value of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3}, and I_{FIL} and I_{TMKA} when the 12-bit interval timer operates.
 4. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The current value of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{WDT} when the watchdog timer operates.
 5. Current flowing only to the A/D converter. The current value of the RL78 microcontrollers is the sum of I_{DD1} or I_{DD2} and I_{ADC} when the A/D converter operates in an operation mode or the HALT mode.
 6. Current flowing only to the LVD circuit. The current value of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{LVD} when the LVD circuit operates.
 7. Current flowing only during data flash rewrite.
 8. Current flowing only during self programming.
 9. For shift time to the SNOOZE mode, see **17.3.3 SNOOZE mode** in the RL78/G12 User's Manual.

- Remarks**
1. f_{IL}: Low-speed on-chip oscillator clock frequency
 2. Temperature condition of the TYP. value is TA = 25°C

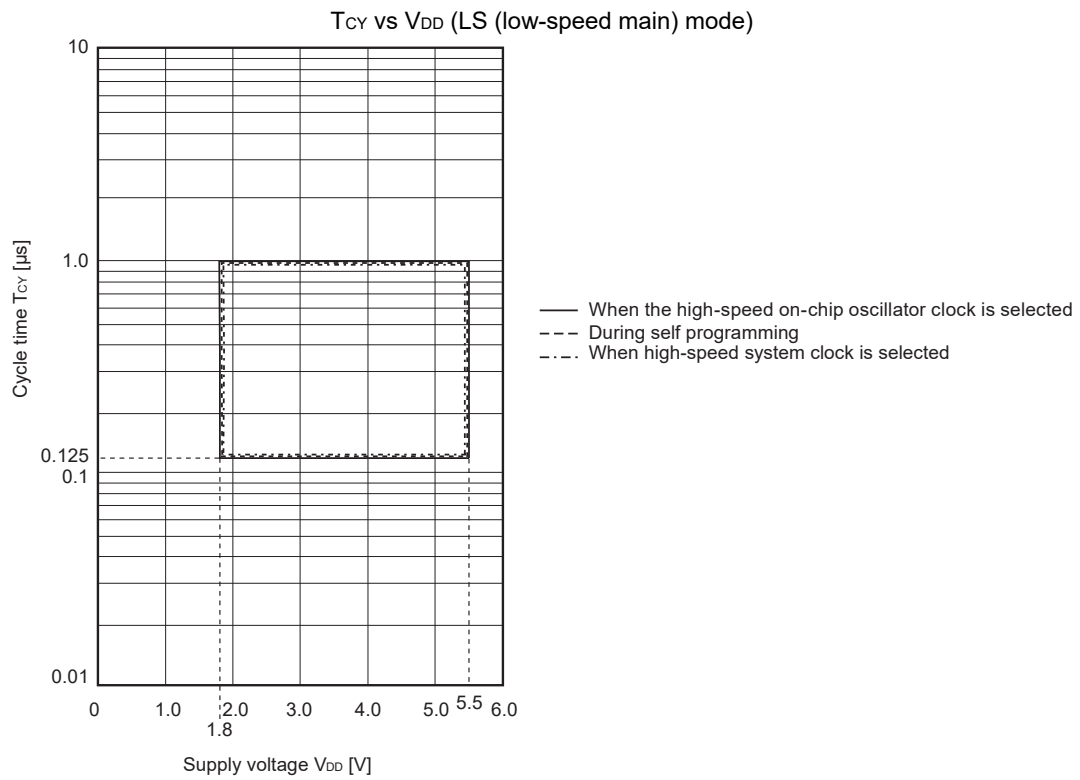
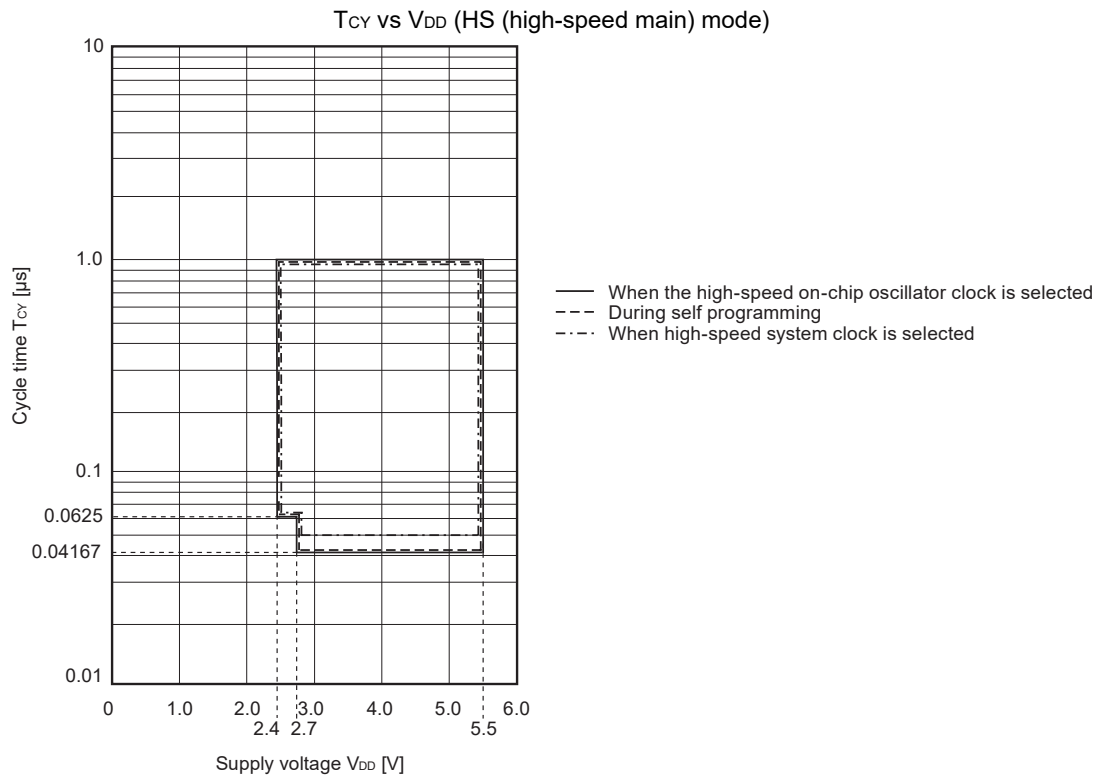
2.4 AC Characteristics

(TA = -40 to +85°C, 1.8 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

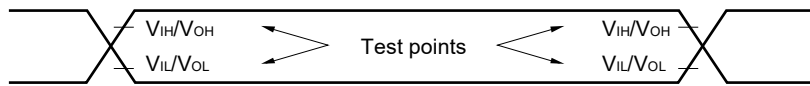
Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	TCY	Main system clock (fMAIN) operation	HS (High-speed main) mode	2.7 V ≤ VDD ≤ 5.5 V	0.04167		1	μs
				2.4 V ≤ VDD < 2.7 V	0.0625		1	μs
			LS (Low-speed main) mode	1.8 V ≤ VDD ≤ 5.5 V	0.125		1	μs
		During self programming	HS (High-speed main) mode	2.7 V ≤ VDD ≤ 5.5 V	0.04167		1	μs
				2.4 V ≤ VDD < 2.7 V	0.0625		1	μs
			LS (Low-speed main) mode	1.8 V ≤ VDD ≤ 5.5 V	0.125		1	μs
External main system clock frequency	fEX	2.7 V ≤ VDD ≤ 5.5 V			1.0		20.0	MHz
		2.4 V ≤ VDD < 2.7 V			1.0		16.0	MHz
		1.8 V ≤ VDD < 2.4 V			1.0		8.0	MHz
External main system clock input high-level width, low-level width	tEXH, tEXL	2.7 V ≤ VDD ≤ 5.5 V			24			ns
		2.4 V ≤ VDD < 2.7 V			30			ns
		1.8 V ≤ VDD < 2.4 V			60			ns
TI00 to TI07 input high-level width, low-level width	tTIH, tTIL				1/fMCK + 10			ns
TO00 to TO07 output frequency	fTO	4.0 V ≤ VDD ≤ 5.5 V					12	MHz
		2.7 V ≤ VDD < 4.0 V					8	MHz
		1.8 V ≤ VDD < 2.7 V					4	MHz
PCLBUZ0, or PCLBUZ1 output frequency	fPCL	4.0 V ≤ VDD ≤ 5.5 V					16	MHz
		2.7 V ≤ VDD < 4.0 V					8	MHz
		1.8 V ≤ VDD < 2.7 V					4	MHz
INTP0 to INTP5 input high-level width, low-level width	tINTH, tINTL				1			μs
KR0 to KR9 input available width	tKR				250			ns
RESET low-level width	tRSL				10			μs

Remark fMCK: Timer array unit operation clock frequency
 (Operation clock to be set by the timer clock select register 0 (TPS0) and the CKS0n bit of timer mode register 0n (TMR0n). n: Channel number (n = 0 to 7))

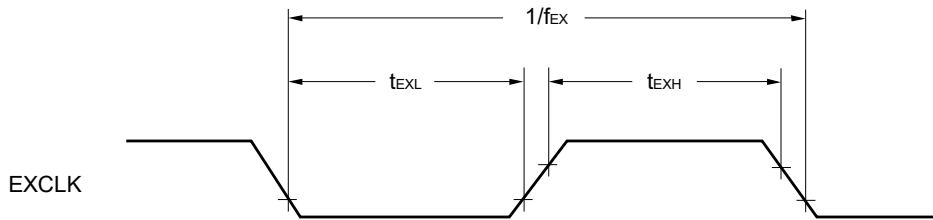
Minimum Instruction Execution Time during Main System Clock Operation



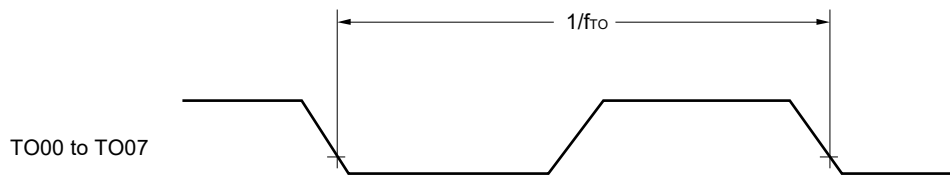
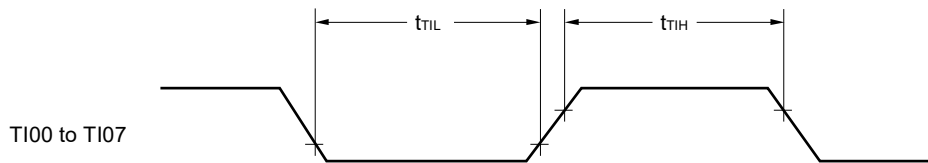
AC Timing Test Point



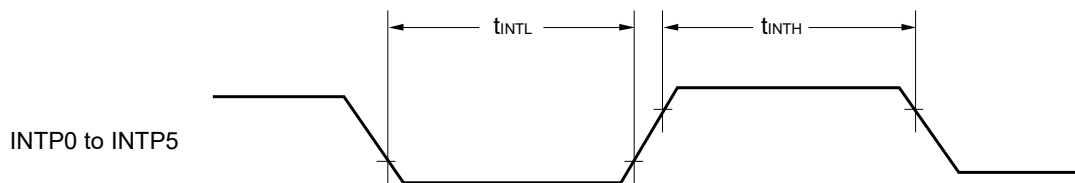
External Main System Clock Timing



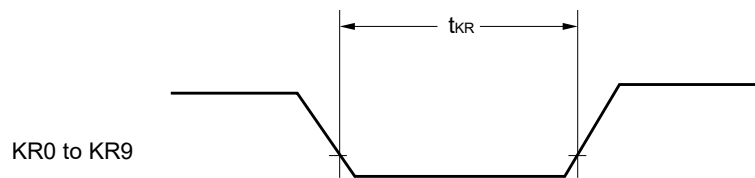
TI/TO Timing



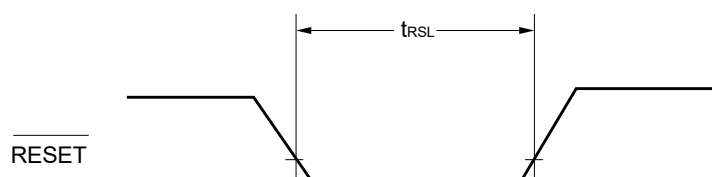
Interrupt Request Input Timing



Key Interrupt Input Timing

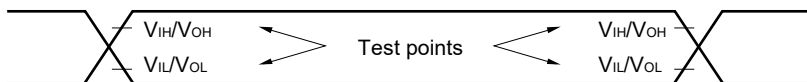


RESET Input Timing



2.5 Peripheral Functions Characteristics

AC Timing Test Point



2.5.1 Serial array unit

(1) During communication at same potential (UART mode)

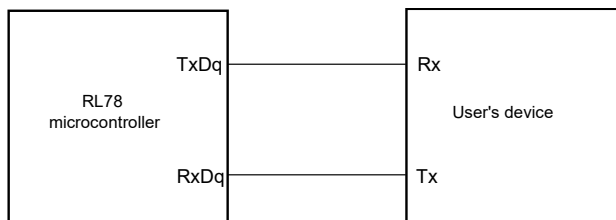
(TA = -40 to +85°C, 1.8 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	
Transfer rate Note 1				$f_{MCK}/6$		$f_{MCK}/6$	bps
		Theoretical value of the maximum transfer rate $f_{CLK} = f_{MCK}$ Note 2		4.0		1.3	Mbps

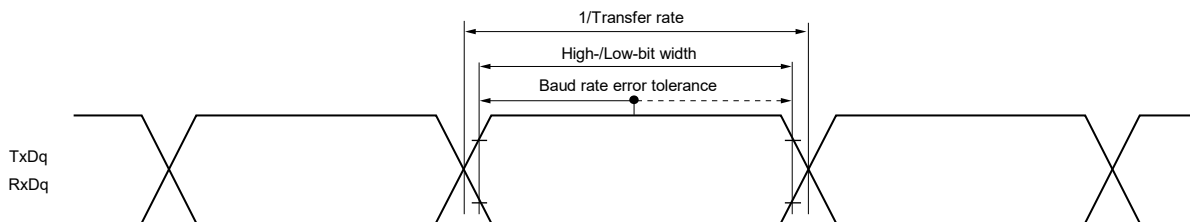
- Notes**
- Transfer rate in the SNOOZE mode is 4800 bps only.
 - The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:
 HS (high-speed main) mode: 24 MHz (2.7 V ≤ VDD ≤ 5.5 V)
 16 MHz (2.4 V ≤ VDD ≤ 5.5 V)
 LS (low-speed main) mode: 8 MHz (1.8 V ≤ VDD ≤ 5.5 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



- Remarks**
- q: UART number (q = 0 to 2), g: PIM, POM number (g = 0, 1)
 - f_{MCK} : Serial array unit operation clock frequency
 (Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn).
 m: Unit number, n: Channel number (mn = 00 to 03, 10, 11))

(2) During communication at same potential (CSI mode) (master mode, SCK00... internal clock output, corresponding CSI00 only)

(TA = -40 to +85°C, 2.7 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	
SCK00 cycle time	t _{KCY1}	t _{KCY1} ≥ 2/f _{CLK}	83.3		250		ns
SCK00 high-/low-level width	t _{KH1} , t _{KL1}	4.0 V ≤ V _{DD} ≤ 5.5 V	t _{KCY1} /2-7		t _{KCY1} /2-50		ns
		2.7 V ≤ V _{DD} ≤ 5.5 V	t _{KCY1} /2-10		t _{KCY1} /2-50		ns
SI00 setup time (to SCK00↑) ^{Note 1}	t _{SIK1}	4.0 V ≤ V _{DD} ≤ 5.5 V	23		110		ns
		2.7 V ≤ V _{DD} ≤ 5.5 V	33		110		ns
SI00 hold time (from SCK00↑) ^{Note 2}	t _{KSI1}		10		10		ns
Delay time from SCK00↓ to SO00 output ^{Note 3}	t _{KSO1}	C = 20 pF ^{Note 4}		10		10	ns

- Notes**
1. When DAP00 = 0 and CKP00 = 0, or DAP00 = 1 and CKP00 = 1. The SI00 setup time becomes “to SCK00↓” when DAP00 = 0 and CKP00 = 1, or DAP00 = 1 and CKP00 = 0.
 2. When DAP00 = 0 and CKP00 = 0, or DAP00 = 1 and CKP00 = 1. The SI00 hold time becomes “from SCK00↓” when DAP00 = 0 and CKP00 = 1, or DAP00 = 1 and CKP00 = 0.
 3. When DAP00 = 0 and CKP00 = 0, or DAP00 = 1 and CKP00 = 1. The delay time to SO00 output becomes “from SCK00↑” when DAP00 = 0 and CKP00 = 1, or DAP00 = 1 and CKP00 = 0.
 4. C is the load capacitance of the SCK00 and SO00 output lines.

Caution Select the normal input buffer for the SI00 pin and the normal output mode for the SO00 and SCK00 pins by using port input mode register 1 (PIM1) and port output mode register 1 (POM1).

- Remarks**
1. This specification is valid only when CSI00's peripheral I/O redirect function is not used.
 2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register 0 (SPS0) and the CKS00 bit of serial mode register 00 (SMR00).)

(3) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output)**(TA = -40 to +85°C, 1.8 V ≤ VDD ≤ 5.5 V, VSS = 0 V)**

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t _{KCY1}	t _{KCY1} ≥ 4/f _{CLK}	2.7 V ≤ V _{DD} ≤ 5.5 V	167		500		ns
			2.4 V ≤ V _{DD} ≤ 5.5 V	250		500		ns
			1.8 V ≤ V _{DD} ≤ 5.5 V	–		500		ns
SCKp high-/low-level width	t _{KH1} ,	t _{KL1}	4.0 V ≤ V _{DD} ≤ 5.5 V	t _{KCY1} /2–12		t _{KCY1} /2–50		ns
			2.7 V ≤ V _{DD} ≤ 5.5 V	t _{KCY1} /2–18		t _{KCY1} /2–50		ns
	2.4 V ≤ V _{DD} ≤ 5.5 V	t _{KCY1} /2–38		t _{KCY1} /2–50		ns		
	1.8 V ≤ V _{DD} ≤ 5.5 V	–		t _{KCY1} /2–50		ns		
Slp setup time (to SCKp↑) Note 1	t _{SIK1}	4.0 V ≤ V _{DD} ≤ 5.5 V	44		110		ns	
		2.7 V ≤ V _{DD} ≤ 5.5 V	44		110		ns	
		2.4 V ≤ V _{DD} ≤ 5.5 V	75		110		ns	
		1.8 V ≤ V _{DD} ≤ 5.5 V	–		110		ns	
Slp hold time (from SCKp↑) Note 2	t _{KSH1}		19		19		ns	
Delay time from SCKp↓ to SOp output Note 3	t _{KSO1}	C = 30 pF Note 4		25		25	ns	

- Notes**
1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the Slp pin and the normal output mode for the SOp and SCKp pins by using port input mode register 1 (PIM1) and port output mode registers 0, 1, 4 (POM0, POM1, POM4).

- Remarks**
1. p: CSI number (p = 00, 01, 11, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0, 1, 3: “1, 3” is only for the R5F102 products)
 2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0, 1, 3: “1, 3” is only for the R5F102 products.))

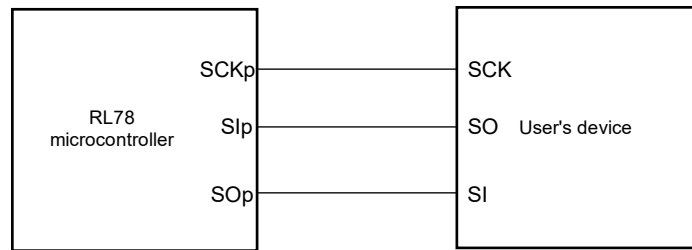
(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input)**(TA = -40 to +85°C, 1.8 V ≤ VDD ≤ 5.5 V, VSS = 0 V)**

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time ^{Note 5}	t _{KCY2}	4.0 V ≤ V _{DD} ≤ 5.5 V	20 MHz < f _{MCK}	8/f _{MCK}		–		ns
			f _{MCK} ≤ 20 MHz	6/f _{MCK}		6/f _{MCK}		ns
		2.7 V ≤ V _{DD} ≤ 5.5 V	16 MHz < f _{MCK}	8/f _{MCK}		–		ns
			f _{MCK} ≤ 16 MHz	6/f _{MCK}		6/f _{MCK}		ns
		2.4 V ≤ V _{DD} ≤ 5.5 V		6/f _{MCK} and 500		6/f _{MCK} and 500		ns
1.8 V ≤ V _{DD} ≤ 5.5 V		–		6/f _{MCK} and 750		ns		
SCKp high-/low-level width	t _{KH2} , t _{KL2}	4.0 V ≤ V _{DD} ≤ 5.5 V		t _{KCY2} /2–7		t _{KCY2} /2–7		ns
		2.7 V ≤ V _{DD} ≤ 5.5 V		t _{KCY2} /2–8		t _{KCY2} /2–8		ns
		2.4 V ≤ V _{DD} ≤ 5.5 V		t _{KCY2} /2–18		t _{KCY2} /2–18		ns
		1.8 V ≤ V _{DD} ≤ 5.5 V		–		t _{KCY2} /2–18		ns
Slp setup time (to SCKp↑) ^{Note 1}	t _{SIK2}	2.7 V ≤ V _{DD} ≤ 5.5 V		1/f _{MCK} + 20		1/f _{MCK} + 30		ns
		2.4 V ≤ V _{DD} ≤ 5.5 V		1/f _{MCK} + 30		1/f _{MCK} + 30		ns
		1.8 V ≤ V _{DD} ≤ 5.5 V		–		1/f _{MCK} + 30		ns
Slp hold time (from SCKp↑) ^{Note 2}	t _{KSIZ}			1/f _{MCK} + 31		1/f _{MCK} + 31		ns
Delay time from SCKp↓ to SOP output ^{Note 3}	t _{KSO2}	C = 30 pF ^{Note 4}	2.7 V ≤ V _{DD} ≤ 5.5 V		2/f _{MCK} + 44		2/f _{MCK} + 110	ns
			2.4 V ≤ V _{DD} ≤ 5.5 V		2/f _{MCK} + 75		2/f _{MCK} + 110	ns
			1.8 V ≤ V _{DD} ≤ 5.5 V		–		2/f _{MCK} + 110	ns

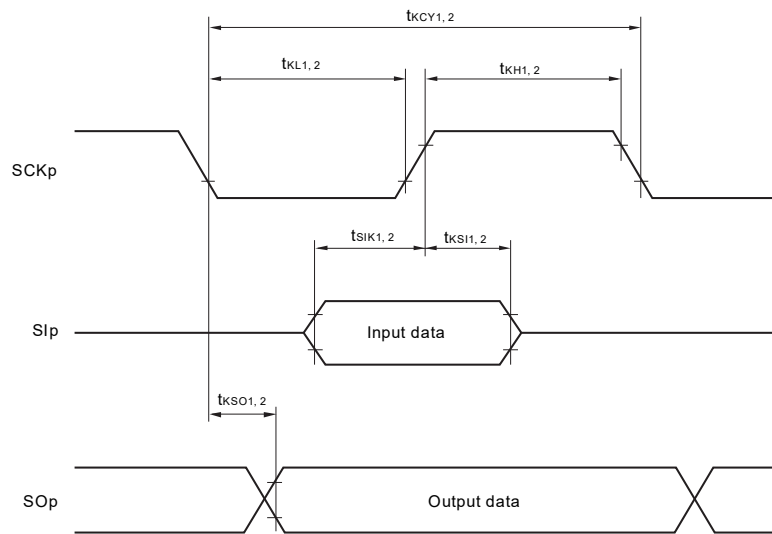
- Notes**
- When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOP output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - C is the load capacitance of the SOP output lines.
 - Transfer rate in the SNOOZE mode: MAX. 1 Mbps.

Caution Select the normal input buffer for the Slp and SCKp pins and the normal output mode for the SOP pin by using port input mode register 1 (PIM1) and port output mode registers 0, 1, 4 (POM0, POM1, POM4).

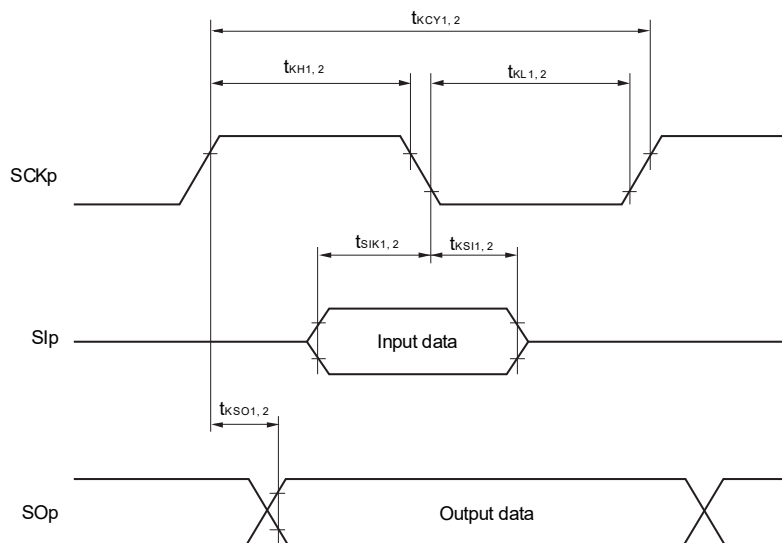
CSI mode connection diagram (during communication at same potential)



**CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)**



**CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)**



(Remarks are listed on the next page.)

- Remarks 1.** p: CSI number (p = 00, 01, 11, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0, 1, 3: "1, 3" is only for the R5F102 products.)
- 2.** f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0, 1, 3: "1, 3" is only for the R5F102 products.))

(5) During communication at same potential (simplified I²C mode)

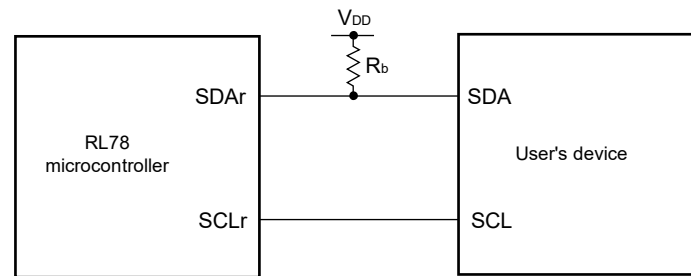
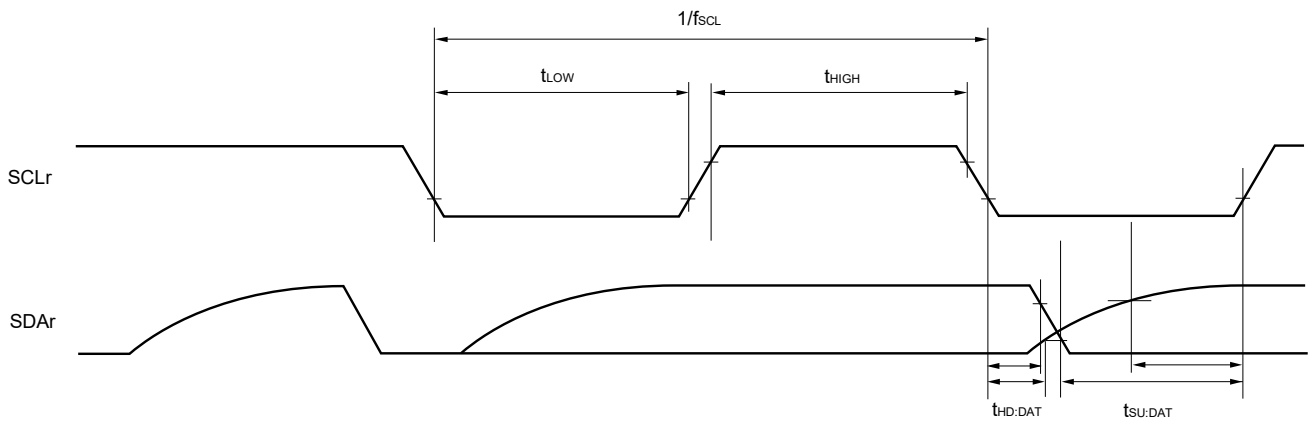
(TA = -40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode LS (low-speed main) Mode		Unit
			MIN.	MAX.	
SCLr clock frequency	f _{SCL}	1.8 V ≤ V _{DD} ≤ 5.5 V, C _b = 100 pF, R _b = 3 kΩ		400 ^{Note 1}	kHz
		1.8 V ≤ V _{DD} < 2.7 V, C _b = 100 pF, R _b = 5 kΩ		300 ^{Note 1}	kHz
Hold time when SCLr = "L"	t _{LOW}	1.8 V ≤ V _{DD} ≤ 5.5 V, C _b = 100 pF, R _b = 3 kΩ	1150		ns
		1.8 V ≤ V _{DD} < 2.7 V, C _b = 100 pF, R _b = 5 kΩ	1550		ns
Hold time when SCLr = "H"	t _{HIGH}	1.8 V ≤ V _{DD} ≤ 5.5 V, C _b = 100 pF, R _b = 3 kΩ	1150		ns
		1.8 V ≤ V _{DD} < 2.7 V, C _b = 100 pF, R _b = 5 kΩ	1550		ns
Data setup time (reception)	t _{SU:DAT}	1.8 V ≤ V _{DD} ≤ 5.5 V, C _b = 100 pF, R _b = 3 kΩ	1/f _{MCK} + 145 ^{Note 2}		ns
		1.8 V ≤ V _{DD} < 2.7 V, C _b = 100 pF, R _b = 5 kΩ	1/f _{MCK} + 230 ^{Note 2}		ns
Data hold time (transmission)	t _{HD:DAT}	1.8 V ≤ V _{DD} ≤ 5.5 V, C _b = 100 pF, R _b = 3 kΩ	0	355	ns
		1.8 V ≤ V _{DD} < 2.7 V, C _b = 100 pF, R _b = 5 kΩ	0	405	ns

- Notes 1.** The value must be equal to or less than f_{MCK}/4.
- 2.** Set t_{SU:DAT} so that it will not exceed the hold time when SCLr = "L" or SCLr = "H".

Caution Select the N-ch open drain output (V_{DD} tolerance) mode for SDAr by using port output mode register h (POMh).

(Remarks are listed on the next page.)

Simplified I²C mode connection diagram (during communication at same potential)Simplified I²C mode serial transfer timing (during communication at same potential)

- Remarks**
1. R_b [Ω]: Communication line (SDAr) pull-up resistance
 C_b [F]: Communication line (SCLr, SDAr) load capacitance
 2. r: IIC number (r = 00, 01, 11, 20), h: = POM number (h = 0, 1, 4, 5)
 3. f_{MCK} : Serial array unit operation clock frequency
 (Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (0, 1, 3))
 4. Simplified I²C mode is supported only by the R5F102 products.

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)**(TA = -40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)**

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		Unit		
			MIN.	MAX.	MIN.	MAX.			
Transfer rate <i>Note4</i>		Reception	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V		f _{MCK} /6 Note1		f _{MCK} /6 Note1	bps	
			Theoretical value of the maximum transfer rate f _{MCK} = f _{CLK} Note3		4.0		1.3	Mbps	
			2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V		f _{MCK} /6 Note1		f _{MCK} /6 Note1	bps	
				Theoretical value of the maximum transfer rate f _{MCK} = f _{CLK} Note3		4.0		1.3	Mbps
		1.8 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V		f _{MCK} /6 Notes1, 2		f _{MCK} /6 Notes1, 2	bps		
				Theoretical value of the maximum transfer rate f _{MCK} = f _{CLK} Note3		4.0		1.3	Mbps
		Transmission	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V		Note4		Note4	bps	
			Theoretical value of the maximum transfer rate C _b = 50 pF, R _b = 1.4 kΩ, V _b = 2.7 V		2.8 Note5		2.8 Note5	Mbps	
			2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V		Note6		Note6	bps	
			Theoretical value of the maximum transfer rate C _b = 50 pF, R _b = 2.7 kΩ, V _b = 2.3 V		1.2 Note7		1.2 Note7	Mbps	
			1.8 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V		Notes 2, 8		Notes 2, 8	bps	
					Theoretical value of the maximum transfer rate C _b = 50 pF, R _b = 5.5 kΩ, V _b = 1.6 V		0.43 Note9		0.43 Note9

- Notes**
- Transfer rate in the SNOOZE mode is 4800 bps only.
 - Use it with V_{DD} ≥ V_b.
 - The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:
 HS (high-speed main) mode: 24 MHz (2.7 V ≤ V_{DD} ≤ 5.5 V)
 16 MHz (2.4 V ≤ V_{DD} ≤ 5.5 V)
 LS (low-speed main) mode: 8 MHz (1.8 V ≤ V_{DD} ≤ 5.5 V)
 - The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.
 Expression for calculating the transfer rate when 4.0 V ≤ V_{DD} ≤ 5.5 V and 2.7 V ≤ V_b ≤ 4.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\} \times 3} \quad [\text{bps}]$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \quad [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

5. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to **Note 4** above to calculate the maximum transfer rate under conditions of the customer.

6. The smaller maximum transfer rate derived by using $f_{MCK}/6$ or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when $2.7\text{ V} \leq V_{DD} < 4.0\text{ V}$ and $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\} \times 3} \quad [\text{bps}]$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

7. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to **Note 6** above to calculate the maximum transfer rate under conditions of the customer.

8. The smaller maximum transfer rate derived by using $f_{MCK}/6$ or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when $1.8\text{ V} \leq V_{DD} < 3.3\text{ V}$, $1.6\text{ V} \leq V_b \leq 2.0\text{ V}$

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\} \times 3} \quad [\text{bps}]$$

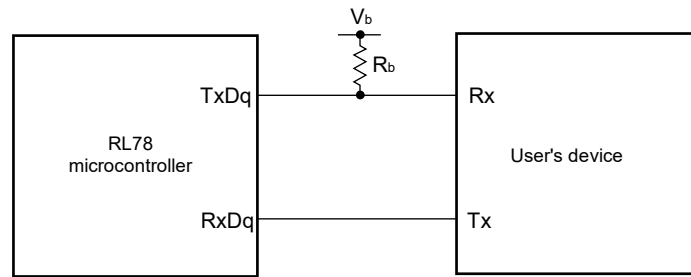
$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

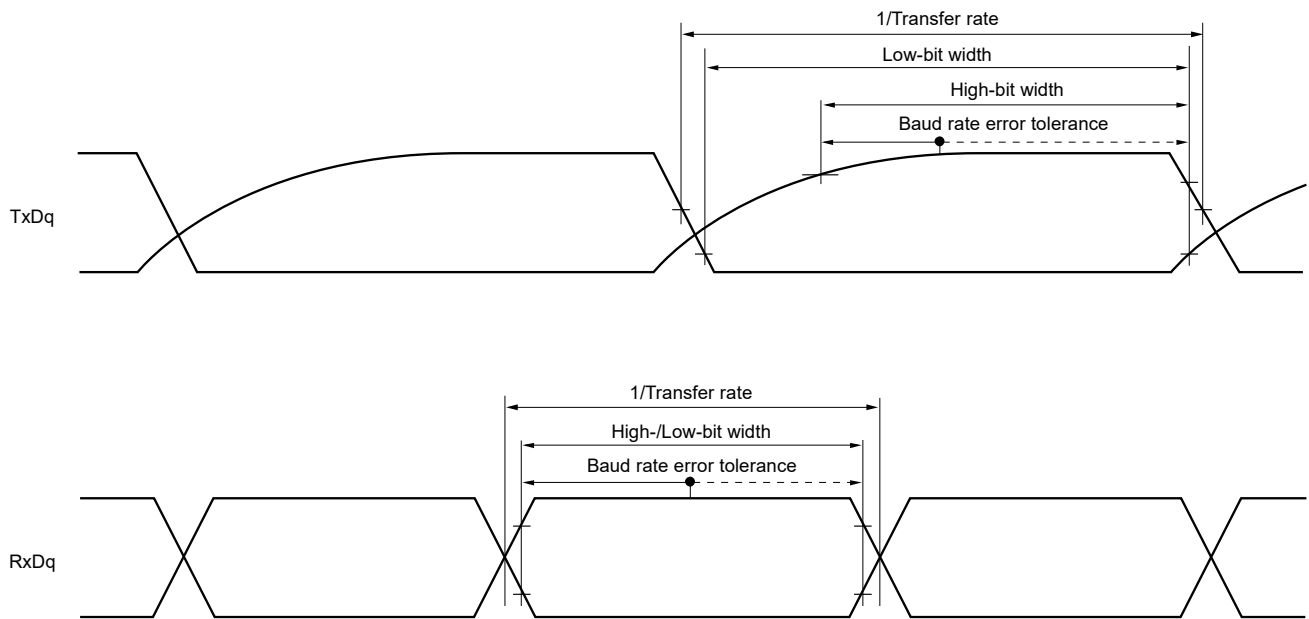
9. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to **Note 8** above to calculate the maximum transfer rate under conditions of the customer.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.

UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)



- Remarks**
1. $R_b[\Omega]$: Communication line (TxDq) pull-up resistance, $C_b[F]$: Communication line (TxDq) load capacitance, $V_b[V]$: Communication line voltage
 2. q: UART number (q = 0 to 2), g: PIM and POM number (g = 0, 1)
 3. f_{MCK} : Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn).
m: Unit number, n: Channel number (mn = 00 to 03, 10, 11))
 4. UART0 of the 20- and 24-pin products supports communication at different potential only when the peripheral I/O redirection function is not used.

(7) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCK00... internal clock output, corresponding CSI00 only)

(TA = -40 to +85°C, 2.7 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	
SCK00 cycle time	t _{KCY1}	t _{KCY1} ≥ 2/fCLK	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 20 pF, R _b = 1.4 kΩ	200		1150		ns
			2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 20 pF, R _b = 2.7 kΩ	300		1150		ns
SCK00 high-level width	t _{KH1}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 20 pF, R _b = 1.4 kΩ		t _{KCY1} /2 – 50		t _{KCY1} /2 – 50		ns
			2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 20 pF, R _b = 2.7 kΩ		t _{KCY1} /2 – 120		t _{KCY1} /2 – 120	
SCK00 low-level width	t _{KL1}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 20 pF, R _b = 1.4 kΩ		t _{KCY1} /2 – 7		t _{KCY1} /2 – 50		ns
			2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 20 pF, R _b = 2.7 kΩ		t _{KCY1} /2 – 10		t _{KCY1} /2 – 50	
SI00 setup time (to SCK00↑) ^{Note 1}	t _{SIK1}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 20 pF, R _b = 1.4 kΩ		58		479		ns
			2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 20 pF, R _b = 2.7 kΩ		121		479	
SI00 hold time (from SCK00↑) ^{Note 1}	t _{KS11}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 20 pF, R _b = 1.4 kΩ		10		10		ns
			2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 20 pF, R _b = 2.7 kΩ		10		10	
Delay time from SCK00↓ to SO00 output ^{Note 1}	t _{KSO1}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 20 pF, R _b = 1.4 kΩ			60		60	ns
			2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 20 pF, R _b = 2.7 kΩ			130		130
SI00 setup time (to SCK00↓) ^{Note 2}	t _{SIK1}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 20 pF, R _b = 1.4 kΩ		23		110		ns
			2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 20 pF, R _b = 2.7 kΩ		33		110	
SI00 hold time (from SCK00↓) ^{Note 2}	t _{KS11}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 20 pF, R _b = 1.4 kΩ		10		10		ns
			2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 20 pF, R _b = 2.7 kΩ		10		10	
Delay time from SCK00↑ to SO00 output ^{Note 2}	t _{KSO1}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 20 pF, R _b = 1.4 kΩ			10		10	ns
			2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 20 pF, R _b = 2.7 kΩ			10		10

(Notes, Caution, and Remarks are listed on the next page.)

- Notes**
1. When DAP00 = 0 and CKP00 = 0, or DAP00 = 1 and CKP00 = 1
 2. When DAP00 = 0 and CKP00 = 1, or DAP00 = 1 and CKP00 = 0.

Caution Select the TTL input buffer for the SI00 pin and the N-ch open drain output (V_{DD} tolerance) mode for the SO00 pin and SCK00 pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

- Remarks**
1. R_b [Ω]: Communication line (SCK00, SO00) pull-up resistance, C_b [F]: Communication line (SCK00, SO00) load capacitance, V_b [V]: Communication line voltage
 2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register 0 (SPS0) and the CKS00 bit of serial mode register 00 (SMR00).)

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (1/3)**(TA = -40 to +85°C, 1.8 V ≤ V_{DD} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)**

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t _{KCY1}	t _{KCY1} ≥ 4/f _{CLK}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ	300		1150		ns
			2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ	500		1150		ns
			1.8 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note} , C _b = 30 pF, R _b = 5.5 kΩ	1150		1150		ns
SCKp high-level width	t _{KH1}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ	t _{KCY1} /2 - 75		t _{KCY1} /2 - 75		ns	
		2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ	t _{KCY1} /2 - 170		t _{KCY1} /2 - 170		ns	
		1.8 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note} , C _b = 30 pF, R _b = 5.5 kΩ	t _{KCY1} /2 - 458		t _{KCY1} /2 - 458		ns	
SCKp low-level width	t _{KL1}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ	t _{KCY1} /2 - 12		t _{KCY1} /2 - 50		ns	
		2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ	t _{KCY1} /2 - 18		t _{KCY1} /2 - 50		ns	
		1.8 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note} , C _b = 30 pF, R _b = 5.5 kΩ	t _{KCY1} /2 - 50		t _{KCY1} /2 - 50		ns	

Note Use it with V_{DD} ≥ V_b.

Cautions 1. Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

2. CSI01 and CSI11 cannot communicate at different potential.

Remarks 1. R_b [Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b [F]: Communication line (SCKp, SOp) load capacitance, V_b [V]: Communication line voltage

2. p: CSI number (p = 00, 20)

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (2/3)**(TA = -40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)**

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	
Slp setup time (to SCKp↑) ^{Note 1}	t _{SIK1}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ	81		479		ns
		2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ	177		479		ns
		1.8 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 2} , C _b = 30 pF, R _b = 5.5 kΩ	479		479		ns
Slp hold time (from SCKp↑) ^{Note 1}	t _{SI1}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ	19		19		ns
		2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ	19		19		ns
		1.8 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 2} , C _b = 30 pF, R _b = 5.5 kΩ	19		19		ns
Delay time from SCKp↓ to SO _p output ^{Note 1}	t _{KSO1}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ		100		100	ns
		2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ		195		195	ns
		1.8 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 2} , C _b = 30 pF, R _b = 5.5 kΩ		483		483	ns

Notes 1. When DAP_{mn} = 0 and CKP_{mn} = 0, or DAP_{mn} = 1 and CKP_{mn} = 1.2. Use it with V_{DD} ≥ V_b.

(Cautions and Remarks are listed on the next page.)

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (3/3)

(TA = -40 to +85°C, 1.8 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

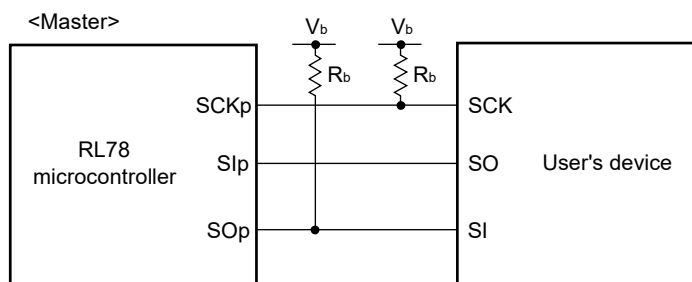
Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	
Slp setup time (to SCKp↓) ^{Note 1}	t _{SIK1}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ	44		110		ns
		2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ	44		110		ns
		1.8 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 2} , C _b = 30 pF, R _b = 5.5 kΩ	110		110		ns
Slp hold time (from SCKp↓) ^{Note 1}	t _{KS1}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ	19		19		ns
		2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ	19		19		ns
		1.8 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 2} , C _b = 30 pF, R _b = 5.5 kΩ	19		19		ns
Delay time from SCKp↑ to SOp output ^{Note 1}	t _{KSO1}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ		25		25	ns
		2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ		25		25	ns
		1.8 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 2} , C _b = 30 pF, R _b = 5.5 kΩ		25		25	ns

- Notes**
- When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - Use it with V_{DD} ≥ V_b.

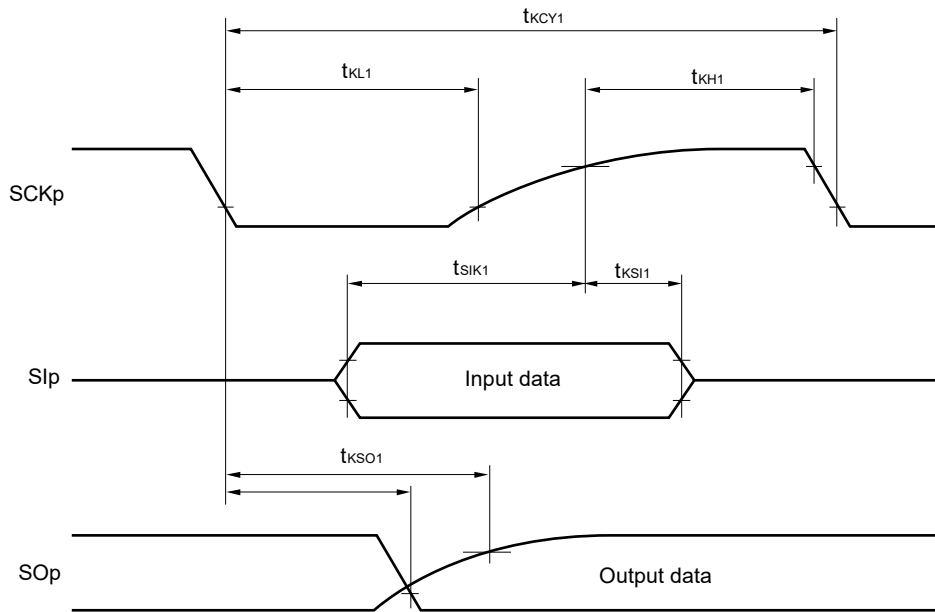
- Cautions**
- Select the TTL input buffer for the Slp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.
 - CSI01 and CSI11 cannot communicate at different potential.

- Remarks**
- R_b [Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b [F]: Communication line (SCKp, SOp) load capacitance, V_b [V]: Communication line voltage
 - p: CSI number (p = 00, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0)

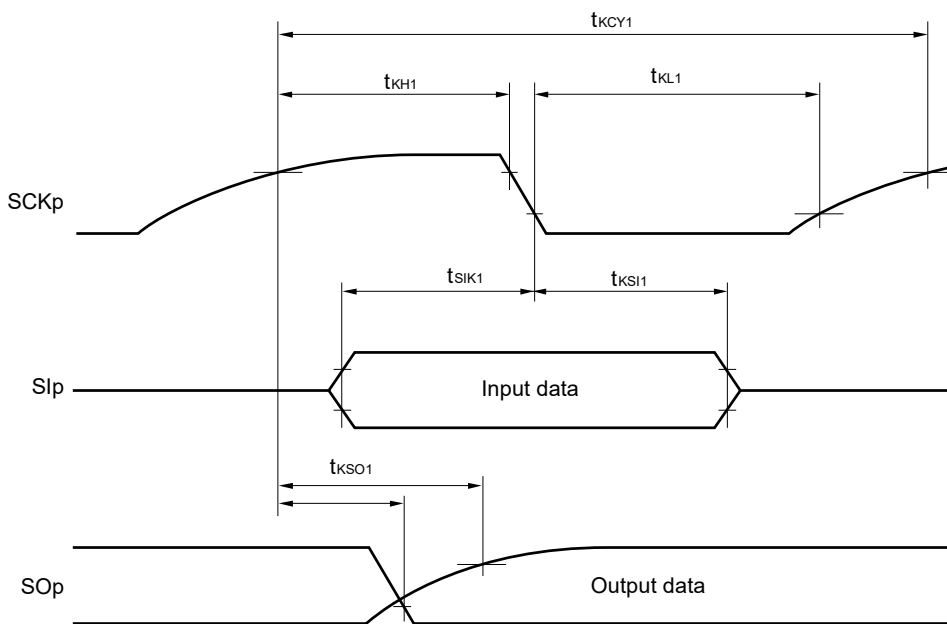
CSI mode connection diagram (during communication at different potential)



CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1)



CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



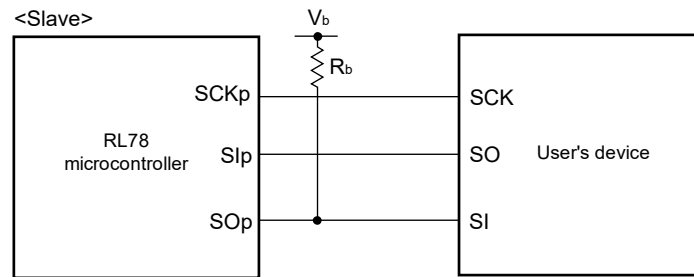
(9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)
(TA = -40 to +85°C, 1.8 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	
SCKp cycle time ^{Note 1}	tkCY2	4.0 V ≤ VDD ≤ 5.5 V, 2.7 V ≤ Vb ≤ 4.0 V	20 MHz < fMCK ≤ 24 MHz	12/fMCK		–	ns
			8 MHz < fMCK ≤ 20 MHz	10/fMCK		–	ns
			4 MHz < fMCK ≤ 8 MHz	8/fMCK		16/fMCK	ns
			fMCK ≤ 4 MHz	6/fMCK		10/fMCK	ns
		2.7 V ≤ VDD < 4.0 V, 2.3 V ≤ Vb ≤ 2.7 V	20 MHz < fMCK ≤ 24 MHz	16/fMCK		–	ns
			16 MHz < fMCK ≤ 20 MHz	14/fMCK		–	ns
			8 MHz < fMCK ≤ 16 MHz	12/fMCK		–	ns
			4 MHz < fMCK ≤ 8 MHz	8/fMCK		16/fMCK	ns
		1.8 V ≤ VDD < 3.3 V, 1.6 V ≤ Vb ≤ 2.0 V ^{Note 2}	fMCK ≤ 4 MHz	6/fMCK		10/fMCK	ns
			20 MHz < fMCK ≤ 24 MHz	36/fMCK		–	ns
			16 MHz < fMCK ≤ 20 MHz	32/fMCK		–	ns
			8 MHz < fMCK ≤ 16 MHz	26/fMCK		–	ns
	4 MHz < fMCK ≤ 8 MHz	16/fMCK		16/fMCK	ns		
	fMCK ≤ 4 MHz	10/fMCK		10/fMCK	ns		
	SCKp high-/low-level width	tkH2, tkL2	4.0 V ≤ VDD ≤ 5.5 V, 2.7 V ≤ Vb ≤ 4.0 V	tkCY2/2 – 12		tkCY2/2 – 50	ns
			2.7 V ≤ VDD < 4.0 V, 2.3 V ≤ Vb ≤ 2.7 V	tkCY2/2 – 18		tkCY2/2 – 50	ns
1.8 V ≤ VDD < 3.3 V, 1.6 V ≤ Vb ≤ 2.0 V ^{Note 2}			tkCY2/2 – 50		tkCY2/2 – 50	ns	
Slp setup time (to SCKp↑) ^{Note 3}	tsIK2	4.0 V ≤ VDD ≤ 5.5 V, 2.7 V ≤ VDD ≤ 4.0 V	1/fMCK + 20		1/fMCK + 30	ns	
		2.7 V ≤ VDD < 4.0 V, 2.3 V ≤ Vb ≤ 2.7 V	1/fMCK + 20		1/fMCK + 30	ns	
		1.8 V ≤ VDD < 3.3 V, 1.6 V ≤ VDD ≤ 2.0 V ^{Note 2}	1/fMCK + 30		1/fMCK + 30	ns	
Slp hold time (from SCKp↑) ^{Note 4}	tkSI2		1/fMCK + 31		1/fMCK + 31	ns	
Delay time from SCKp↓ to SOP output ^{Note 5}	tkSO2	4.0 V ≤ VDD ≤ 5.5 V, 2.7 V ≤ Vb ≤ 4.0 V, Cb = 30 pF, Rb = 1.4 kΩ		2/fMCK + 120		2/fMCK + 573	ns
		2.7 V ≤ VDD < 4.0 V, 2.3 V ≤ Vb ≤ 2.7 V, Cb = 30 pF, Rb = 2.7 kΩ		2/fMCK + 214		2/fMCK + 573	ns
		1.8 V ≤ VDD < 3.3 V, 1.6 V ≤ Vb ≤ 2.0 V ^{Note 2} , Cb = 30 pF, Rb = 5.5 kΩ		2/fMCK + 573		2/fMCK + 573	ns

- Notes**
- Transfer rate in the SNOOZE mode: MAX. 1 Mbps
 - Use it with VDD ≥ Vb.
 - When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOP output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

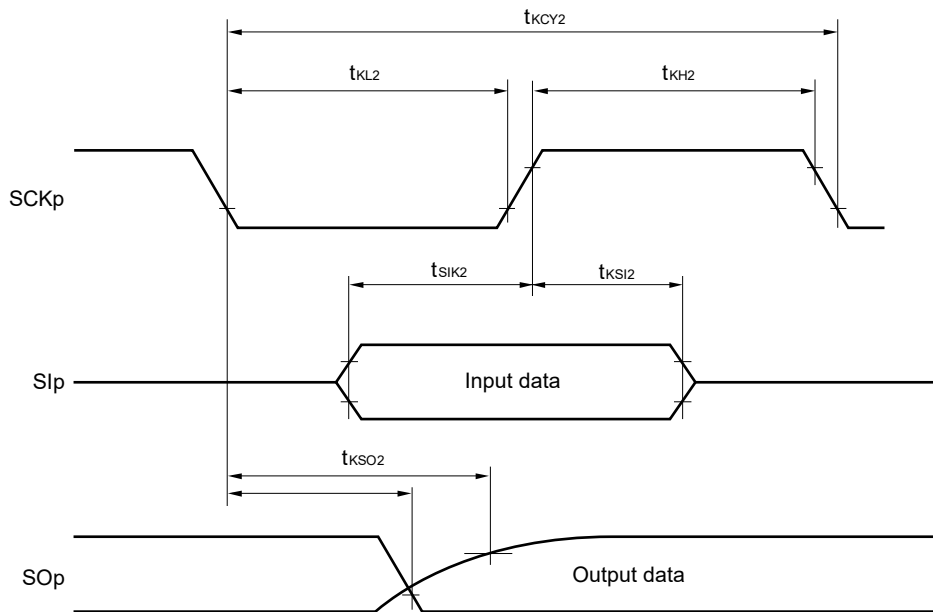
- Cautions**
- Select the TTL input buffer for the Slp and SCKp pins and the N-ch open drain output (VDD tolerance) mode for the SOP pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). For VIH and VIL, see the DC characteristics with TTL input buffer selected.
 - CSI01 and CSI11 cannot communicate at different potential.

CSI mode connection diagram (during communication at different potential)

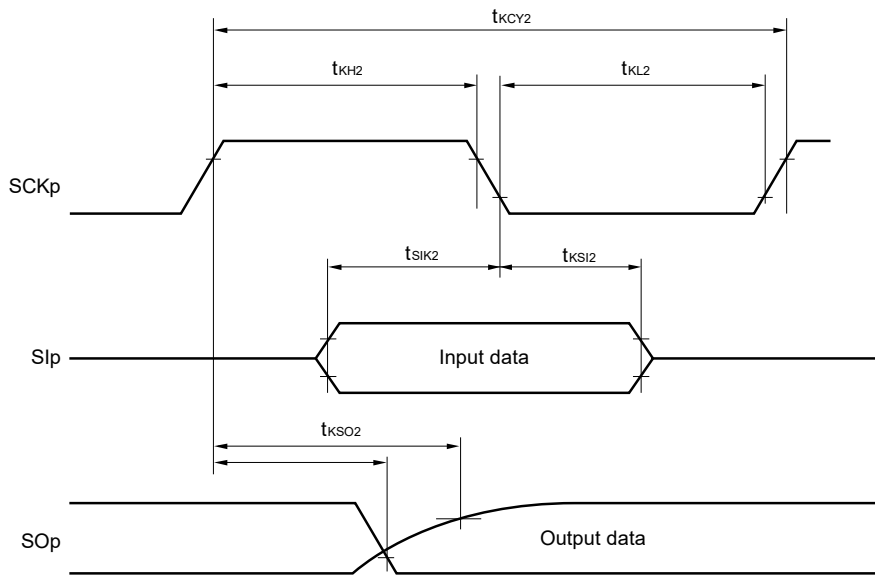


- Remarks**
1. R_b [Ω]: Communication line (SO_p) pull-up resistance, C_b [F]: Communication line (SO_p) load capacitance, V_b [V]: Communication line voltage
 2. p: CSI number (p = 00, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0)
 3. f_{MCK} : Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPS_m) and the CKS_{mn} bit of serial mode register mn (SMR_{mn}). m: Unit number, n: Channel number (mn = 00, 10))

**CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAP_{mn} = 0 and CKP_{mn} = 0, or DAP_{mn} = 1 and CKP_{mn} = 1.)**



**CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)**



Remark p: CSI number (p = 00, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0)

(10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode)**(TA = -40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)**

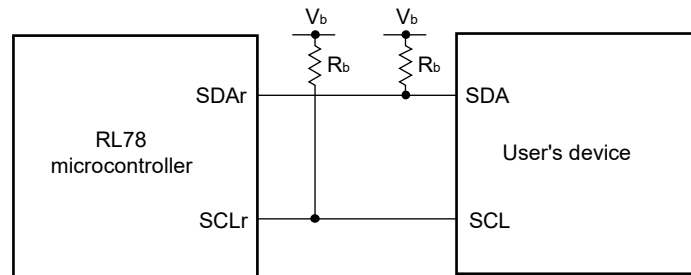
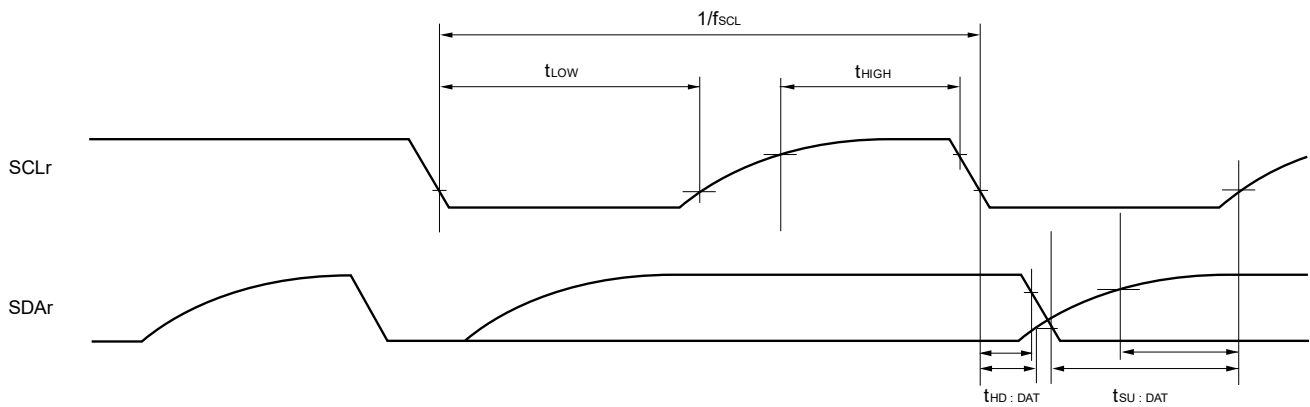
Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	f _{SCL}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 100 pF, R _b = 2.8 kΩ		400 ^{Note1}		300 ^{Note1}	kHz
		2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 100 pF, R _b = 2.7 kΩ		400 ^{Note1}		300 ^{Note1}	kHz
		1.8 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V, ^{Note2} C _b = 100 pF, R _b = 5.5 kΩ		300 ^{Note1}		300 ^{Note1}	kHz
Hold time when SCLr = "L"	t _{LOW}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 100 pF, R _b = 2.8 kΩ	1150		1550		ns
		2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 100 pF, R _b = 2.7 kΩ	1150		1550		ns
		1.8 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V, ^{Note2} C _b = 100 pF, R _b = 5.5 kΩ	1550		1550		ns
Hold time when SCLr = "H"	t _{HIGH}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 100 pF, R _b = 2.8 kΩ	675		610		ns
		2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 100 pF, R _b = 2.7 kΩ	600		610		ns
		1.8 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V, ^{Note2} C _b = 100 pF, R _b = 5.5 kΩ	610		610		ns
Data setup time (reception)	t _{SU:DAT}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 100 pF, R _b = 2.8 kΩ	1/f _{MCK} + 190 ^{Note3}		1/f _{MCK} + 190 ^{Note3}		ns
		2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 100 pF, R _b = 2.7 kΩ	1/f _{MCK} + 190 ^{Note3}		1/f _{MCK} + 190 ^{Note3}		ns
		1.8 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V, ^{Note2} C _b = 100 pF, R _b = 5.5 kΩ	1/f _{MCK} + 190 ^{Note3}		1/f _{MCK} + 190 ^{Note3}		ns
Data hold time (transmission)	t _{HD:DAT}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 100 pF, R _b = 2.8 kΩ	0	355	0	355	ns
		2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 100 pF, R _b = 2.7 kΩ	0	355	0	355	ns
		1.8 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V, ^{Note2} C _b = 100 pF, R _b = 5.5 kΩ	0	405	0	405	ns

- Notes**
1. The value must be equal to or less than f_{MCK}/4.
 2. Use it with V_{DD} ≥ V_b.
 3. Set t_{SU:DAT} so that it will not exceed the hold time when SCLr = "L" or SCLr = "H".

Cautions

1. Select the TTL input buffer and the N-ch open drain output (V_{DD} tolerance) mode for the SDAr pin and the N-ch open drain output (V_{DD} tolerance) mode for the SCLr pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.
2. IIC01 and IIC11 cannot communicate at different potential.

(Remarks are listed on the next page.)

Simplified I²C mode connection diagram (during communication at different potential)Simplified I²C mode serial transfer timing (during communication at different potential)

- Remarks 1.** R_b [Ω]: Communication line (SDAr, SCLr) pull-up resistance, C_b [F]: Communication line (SDAr, SCLr) load capacitance, V_b [V]: Communication line voltage
- 2.** r: IIC Number (r = 00, 20)
- 3.** f_{MCK} : Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn).
m: Unit number (m = 0,1), n: Channel number (n = 0))
- 4.** Simplified I²C mode is supported only by the R5F102 products.

2.5.2 Serial interface IICA

(TA = -40 to +85°C, 1.8 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) mode LS (low-speed main) mode				Unit
			Standard Mode		Fast Mode		
			MIN.	MAX.	MIN.	MAX.	
			SCLA0 clock frequency	fSCL	Fast mode: fCLK ≥ 3.5 MHz Normal mode: fCLK ≥ 1 MHz		
Setup time of restart condition	tSU:STA		4.7		0.6		μs
Hold time ^{Note 1}	tHD:STA		4.0		0.6		μs
Hold time when SCLA0 = "L"	tLOW		4.7		1.3		μs
Hold time when SCLA0 = "H"	tHIGH		4.0		0.6		μs
Data setup time (reception)	tSU:DAT		250		100		ns
Data hold time (transmission) ^{Note 2}	tHD:DAT		0	3.45	0	0.9	μs
Setup time of stop condition	tSU:STO		4.0		0.6		μs
Bus-free time	tBUF		4.7		1.3		μs

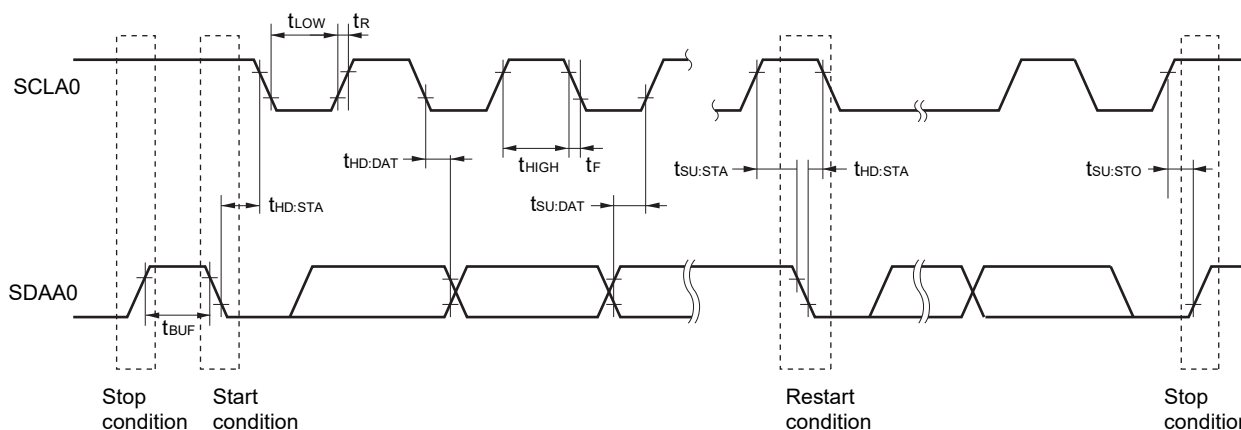
- Notes**
- The first clock pulse is generated after this period when the start/restart condition is detected.
 - The maximum value (MAX.) of tHD:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution Only in the 30-pin products, the values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Normal mode: Cb = 400 pF, Rb = 2.7 kΩ
Fast mode: Cb = 320 pF, Rb = 1.1 kΩ

IICA serial transfer timing



2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Input channel	Reference Voltage		
	Reference voltage (+) = AV _{REFP} Reference voltage (-) = AV _{REFM}	Reference voltage (+) = V _{DD} Reference voltage (-) = V _{SS}	Reference voltage (+) = V _{BGR} Reference voltage (-) = AV _{REFM}
ANI0 to ANI3	Refer to 2.6.1 (1).	Refer to 2.6.1 (3).	Refer to 2.6.1 (4).
ANI16 to ANI22			
Internal reference voltage Temperature sensor output voltage	Refer to 2.6.1 (1).		-

(1) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), target pin: ANI2, ANI3, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +85°C, 1.8 V ≤ AV_{REFP} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, Reference voltage (+) = AV_{REFP}, Reference voltage (-) = AV_{REFM} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit		
Resolution	RES		8		10	bit		
Overall error ^{Note 1}	AINL	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}		1.2	±3.5	LSB		
				1.2	±7.0 ^{Note 4}	LSB		
Conversion time	t _{CONV}	10-bit resolution Target pin: ANI2, ANI3	3.6 V ≤ V _{DD} ≤ 5.5 V	2.125		39	μs	
			2.7 V ≤ V _{DD} ≤ 5.5 V	3.1875		39	μs	
			1.8 V ≤ V _{DD} ≤ 5.5 V	17		39	μs	
					57		95	μs
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V ≤ V _{DD} ≤ 5.5 V	2.375		39	μs	
			2.7 V ≤ V _{DD} ≤ 5.5 V	3.5625		39	μs	
2.4 V ≤ V _{DD} ≤ 5.5 V	17			39	μs			
Zero-scale error ^{Notes 1, 2}	EZS	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}			±0.25	%FSR		
					±0.50 ^{Note 4}	%FSR		
Full-scale error ^{Notes 1, 2}	EFS	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}			±0.25	%FSR		
					±0.50 ^{Note 4}	%FSR		
Integral linearity error ^{Note 1}	ILE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}			±2.5	LSB		
					±5.0 ^{Note 4}	LSB		
Differential linearity error ^{Note 1}	DLE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}			±1.5	LSB		
					±2.0 ^{Note 4}	LSB		
Analog input voltage	V _{AIN}	ANI2, ANI3	0		AV _{REFP}	V		
		Internal reference voltage (2.4 V ≤ V _{DD} ≤ 5.5 V, HS (high-speed main) mode)			V _{BGR} ^{Note 5}	V		
		Temperature sensor output voltage (2.4 V ≤ V _{DD} ≤ 5.5 V, HS (high-speed main) mode)			V _{TMPS25} ^{Note 5}	V		

(Notes are listed on the next page.)

- Notes**
- Excludes quantization error ($\pm 1/2$ LSB).
 - This value is indicated as a ratio (%FSR) to the full-scale value.
 - When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.
 Overall error: Add ± 1.0 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.
 Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when $AV_{REFP} = V_{DD}$.
 Integral linearity error/ Differential linearity error: Add ± 0.5 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.
 - Values when the conversion time is set to 57 μ s (min.) and 95 μ s (max.).
 - Refer to **2.6.2 Temperature sensor/internal reference voltage characteristics**.

(2) When reference voltage (+) = $AV_{REFP}/ANI0$ (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = $AV_{REFM}/ANI1$ (ADREFM = 1), target pin: ANI16 to ANI22

(TA = -40 to +85°C, 1.8 V $\leq AV_{REFP} \leq V_{DD} \leq 5.5$ V, VSS = 0 V, Reference voltage (+) = AV_{REFP} , Reference voltage (-) = $AV_{REFM} = 0$ V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}			1.2	± 5.0	LSB
					1.2	± 8.5 ^{Note 4}	LSB
Conversion time	t_{CONV}	10-bit resolution Target ANI pin: ANI16 to ANI22	3.6 V $\leq V_{DD} \leq 5.5$ V	2.125		39	μ s
			2.7 V $\leq V_{DD} \leq 5.5$ V	3.1875		39	μ s
			1.8 V $\leq V_{DD} \leq 5.5$ V	17		39	μ s
				57		95	μ s
Zero-scale error ^{Notes 1, 2}	EZS	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}				± 0.35	%FSR
						± 0.60 ^{Note 4}	%FSR
Full-scale error ^{Notes 1, 2}	EFS	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}				± 0.35	%FSR
						± 0.60 ^{Note 4}	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}				± 3.5	LSB
						± 6.0 ^{Note 4}	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}				± 2.0	LSB
						± 2.5 ^{Note 4}	LSB
Analog input voltage	V_{AIN}	ANI16 to ANI22		0		AV_{REFP} and V_{DD}	V

- Notes**
- Excludes quantization error ($\pm 1/2$ LSB).
 - This value is indicated as a ratio (%FSR) to the full-scale value.
 - When $AV_{REFP} \leq V_{DD}$, the MAX. values are as follows.
 Overall error: Add ± 4.0 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.
 Zero-scale error/Full-scale error: Add $\pm 0.20\%$ FSR to the MAX. value when $AV_{REFP} = V_{DD}$.
 Integral linearity error/ Differential linearity error: Add ± 2.0 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.
 - When the conversion time is set to 57 μ s (min.) and 95 μ s (max.).

(3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = V_{SS} (ADREFM = 0), target pin: ANI0 to ANI3, ANI16 to ANI22, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, Reference voltage (+) = V_{DD}, Reference voltage (-) = V_{SS})

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit	
Resolution	R _{ES}		8		10	bit	
Overall error ^{Note 1}	AINL	10-bit resolution		1.2	±7.0	LSB	
				1.2	±10.5 ^{Note 3}	LSB	
Conversion time	t _{CONV}	10-bit resolution Target pin: ANI0 to ANI3, ANI16 to ANI22	3.6 V ≤ V _{DD} ≤ 5.5 V	2.125		39	μs
			2.7 V ≤ V _{DD} ≤ 5.5 V	3.1875		39	μs
			1.8 V ≤ V _{DD} ≤ 5.5 V	17		39	μs
				57		95	μs
Conversion time	t _{CONV}	10-bit resolution Target pin: internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V ≤ V _{DD} ≤ 5.5 V	2.375		39	μs
			2.7 V ≤ V _{DD} ≤ 5.5 V	3.5625		39	μs
			2.4 V ≤ V _{DD} ≤ 5.5 V	17		39	μs
Zero-scale error ^{Notes 1, 2}	E _{ZS}	10-bit resolution			±0.60	%FSR	
					±0.85 ^{Note 3}	%FSR	
Full-scale error ^{Notes 1, 2}	E _{FS}	10-bit resolution			±0.60	%FSR	
					±0.85 ^{Note 3}	%FSR	
Integral linearity error ^{Note 1}	I _{LE}	10-bit resolution			±4.0	LSB	
					±6.5 ^{Note 3}	LSB	
Differential linearity error ^{Note 1}	D _{LE}	10-bit resolution			±2.0	LSB	
					±2.5 ^{Note 3}	LSB	
Analog input voltage	V _{AIN}	ANI0 to ANI3, ANI16 to ANI22	0		V _{DD}	V	
		Internal reference voltage (2.4 V ≤ V _{DD} ≤ 5.5 V, HS (high-speed main) mode)	V _{BGR} ^{Note 4}			V	
		Temperature sensor output voltage (2.4 V ≤ V _{DD} ≤ 5.5 V, HS (high-speed main) mode)	V _{TMPS25} ^{Note 4}			V	

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. When the conversion time is set to 57 μs (min.) and 95 μs (max.).

4. Refer to **2.6.2 Temperature sensor/internal reference voltage characteristics**.

(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM (ADREFM = 1), target pin: ANI0, ANI2, ANI3, and ANI16 to ANI22

(TA = -40 to +85°C, 2.4 V ≤ VDD ≤ 5.5 V, VSS = 0 V, Reference voltage (+) = VBGR^{Note 3}, Reference voltage (-) = AVREFM^{Note 4} = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES		8			bit
Conversion time	tCONV	8-bit resolution	17		39	μs
Zero-scale error ^{Notes 1, 2}	EZS	8-bit resolution			±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	8-bit resolution			±2.0	LSB
Differential linearity error ^{Note 1}	DLE	8-bit resolution			±1.0	LSB
Analog input voltage	VAIN		0		VBGR ^{Note 3}	V

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. Refer to **2.6.2 Temperature sensor/internal reference voltage characteristics**.

4. When reference voltage (-) = VSS, the MAX. values are as follows.

Zero-scale error: Add ±0.35%FSR to the MAX. value when reference voltage (-) = AVREFM.

Integral linearity error: Add ±0.5 LSB to the MAX. value when reference voltage (-) = AVREFM.

Differential linearity error: Add ±0.2 LSB to the MAX. value when reference voltage (-) = AVREFM.

2.6.2 Temperature sensor/internal reference voltage characteristics

(TA = -40 to +85°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, HS (high-speed main) mode)

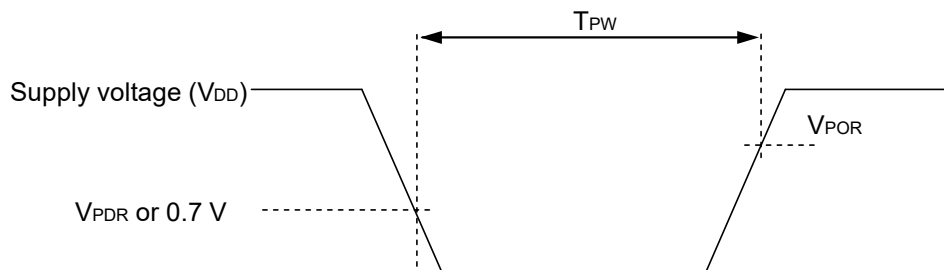
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V _{TMPS25}	Setting ADS register = 80H, TA = +25°C		1.05		V
Internal reference voltage	V _{BGR}	Setting ADS register = 81H	1.38	1.45	1.50	V
Temperature coefficient	F _{VTMPS}	Temperature sensor output voltage that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	t _{AMP}		5			μs

2.6.3 POR circuit characteristics

(TA = -40 to +85°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	V _{POR}	Power supply rise time	1.47	1.51	1.55	V
	V _{PDR}	Power supply fall time	1.46	1.50	1.54	V
Minimum pulse width ^{Note}	T _{PW}		300			μs

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



2.6.4 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interrupt Mode

(TA = -40 to +85°C, VPDR ≤ VDD ≤ 5.5 V, VSS = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection supply voltage	VLVD0	Power supply rise time	3.98	4.06	4.14	V
		Power supply fall time	3.90	3.98	4.06	V
	VLVD1	Power supply rise time	3.68	3.75	3.82	V
		Power supply fall time	3.60	3.67	3.74	V
	VLVD2	Power supply rise time	3.07	3.13	3.19	V
		Power supply fall time	3.00	3.06	3.12	V
	VLVD3	Power supply rise time	2.96	3.02	3.08	V
		Power supply fall time	2.90	2.96	3.02	V
	VLVD4	Power supply rise time	2.86	2.92	2.97	V
		Power supply fall time	2.80	2.86	2.91	V
	VLVD5	Power supply rise time	2.76	2.81	2.87	V
		Power supply fall time	2.70	2.75	2.81	V
	VLVD6	Power supply rise time	2.66	2.71	2.76	V
		Power supply fall time	2.60	2.65	2.70	V
	VLVD7	Power supply rise time	2.56	2.61	2.66	V
		Power supply fall time	2.50	2.55	2.60	V
	VLVD8	Power supply rise time	2.45	2.50	2.55	V
		Power supply fall time	2.40	2.45	2.50	V
	VLVD9	Power supply rise time	2.05	2.09	2.13	V
		Power supply fall time	2.00	2.04	2.08	V
VLVD10	Power supply rise time	1.94	1.98	2.02	V	
	Power supply fall time	1.90	1.94	1.98	V	
VLVD11	Power supply rise time	1.84	1.88	1.91	V	
	Power supply fall time	1.80	1.84	1.87	V	
Minimum pulse width	tLW		300			μs
Detection delay time					300	μs

LVD detection voltage of interrupt & reset mode**(TA = -40 to +85°C, VPDR ≤ VDD ≤ 5.5 V, VSS = 0 V)**

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit	
Interrupt and reset mode	VLVDB0	VPOC2, VPOC1, VPOC0 = 0, 0, 1, falling reset voltage	1.80	1.84	1.87	V	
	VLVDB1	LVIS1, LVIS0 = 1, 0	Rising reset release voltage	1.94	1.98	2.02	V
			Falling interrupt voltage	1.90	1.94	1.98	V
	VLVDB2	LVIS1, LVIS0 = 0, 1	Rising reset release voltage	2.05	2.09	2.13	V
			Falling interrupt voltage	2.00	2.04	2.08	V
	VLVDB3	LVIS1, LVIS0 = 0, 0	Rising reset release voltage	3.07	3.13	3.19	V
			Falling interrupt voltage	3.00	3.06	3.12	V
	VLVDC0	VPOC2, VPOC1, VPOC0 = 0, 1, 0, falling reset voltage	2.40	2.45	2.50	V	
	VLVDC1	LVIS1, LVIS0 = 1, 0	Rising reset release voltage	2.56	2.61	2.66	V
			Falling interrupt voltage	2.50	2.55	2.60	V
	VLVDC2	LVIS1, LVIS0 = 0, 1	Rising reset release voltage	2.66	2.71	2.76	V
			Falling interrupt voltage	2.60	2.65	2.70	V
	VLVDC3	LVIS1, LVIS0 = 0, 0	Rising reset release voltage	3.68	3.75	3.82	V
			Falling interrupt voltage	3.60	3.67	3.74	V
	VLVDD0	VPOC2, VPOC1, VPOC0 = 0, 1, 1, falling reset voltage	2.70	2.75	2.81	V	
	VLVDD1	LVIS1, LVIS0 = 1, 0	Rising reset release voltage	2.86	2.92	2.97	V
			Falling interrupt voltage	2.80	2.86	2.91	V
	VLVDD2	LVIS1, LVIS0 = 0, 1	Rising reset release voltage	2.96	3.02	3.08	V
			Falling interrupt voltage	2.90	2.96	3.02	V
	VLVDD3	LVIS1, LVIS0 = 0, 0	Rising reset release voltage	3.98	4.06	4.14	V
Falling interrupt voltage			3.90	3.98	4.06	V	

2.6.5 Power supply voltage rising slope characteristics**(TA = -40 to +85°C, VSS = 0 V)**

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				54	V/ms

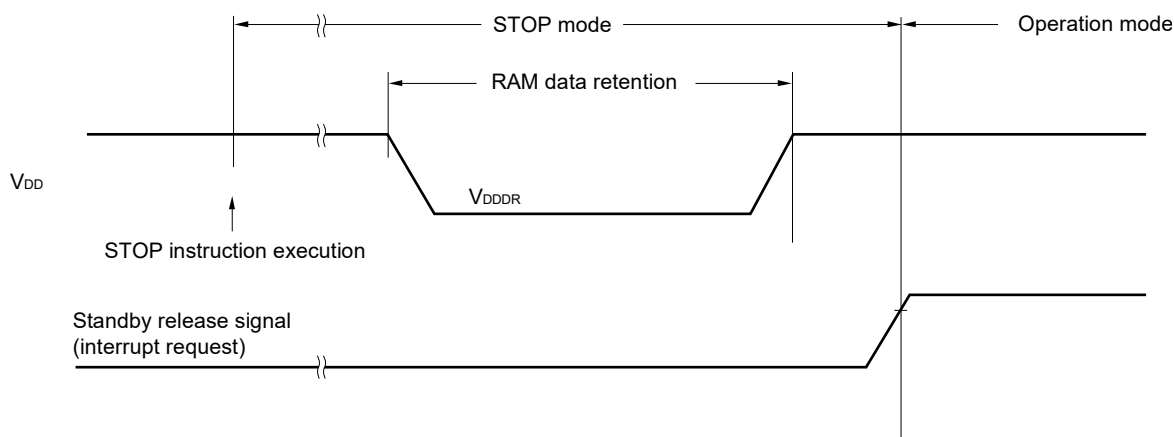
Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until VDD reaches the operating voltage range shown in 2.4 AC Characteristics.

2.7 RAM Data Retention Characteristics

(TA = -40 to +85°C, VSS = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.46 ^{Note}		5.5	V

Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.



2.8 Flash Memory Programming Characteristics

(TA = -40 to +85°C, 1.8 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
System clock frequency	fCLK		1		24	MHz
Code flash memory rewritable times <small>Notes 1, 2, 3</small>	C _{erwr}	Retained for 20 years TA = 85°C	1,000			Times
Data flash memory rewritable times <small>Notes 1, 2, 3</small>		Retained for 1 year TA = 25°C		1,000,000		
		Retained for 5 years TA = 85°C	100,000			
		Retained for 20 years TA = 85°C	10,000			

- Notes**
- 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.
 2. When using flash memory programmer and Renesas Electronics self programming library
 3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

2.9 Dedicated Flash Memory Programmer Communication (UART)

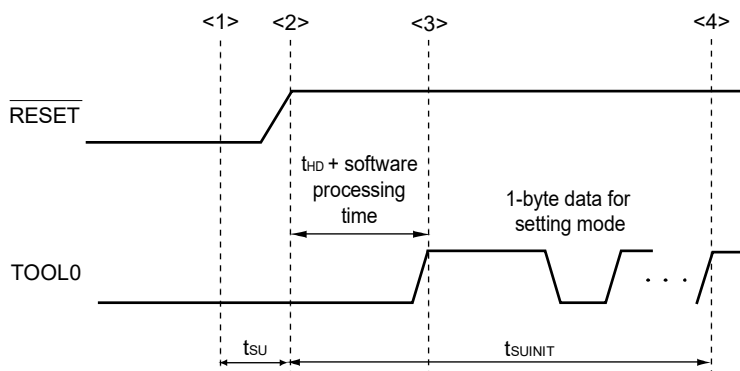
(TA = -40 to +85°C, 1.8 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

2.10 Timing of Entry to Flash Memory Programming Modes

(TA = -40 to +85°C, 1.8 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	t _{SUNIT}	POR and LVD reset are released before external reset release			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	t _{SU}	POR and LVD reset are released before external reset release	10			μs
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	t _{HD}	POR and LVD reset are released before external reset release	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset is released (POR and LVD reset must be released before the external reset is released.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark t_{SUNIT}: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.

t_{SU}: Time to release the external reset after the TOOL0 pin is set to the low level

t_{HD}: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)

3. ELECTRICAL SPECIFICATIONS (G: INDUSTRIAL APPLICATIONS $T_A = -40$ to $+105^\circ\text{C}$)

This chapter describes the following electrical specifications.

Target products G: Industrial applications $T_A = -40$ to $+105^\circ\text{C}$
R5F102xxGxx

- Cautions**
1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 2. The pins mounted depend on the product. Refer to 2.1 Port Functions to 2.2.1 Functions for each product in the RL78/G12 User's Manual.
 3. Please contact Renesas Electronics sales office for derating of operation under $T_A = +85^\circ\text{C}$ to $+105^\circ\text{C}$. Derating is the systematic reduction of load for the sake of improved reliability.

Remark When the RL78 microcontroller is used in the range of $T_A = -40$ to $+85^\circ\text{C}$, see **2. ELECTRICAL SPECIFICATIONS ($T_A = -40$ to $+85^\circ\text{C}$)**.

There are following differences between the products "G: Industrial applications ($T_A = -40$ to $+105^\circ\text{C}$)" and the products "A: Consumer applications, and D: Industrial applications".

Parameter	Application	
	A: Consumer applications, D: Industrial applications	G: Industrial applications
Operating ambient temperature	$T_A = -40$ to $+85^\circ\text{C}$	$T_A = -40$ to $+105^\circ\text{C}$
Operating mode Operating voltage range	HS (high-speed main) mode: $2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}@1\text{ MHz to }24\text{ MHz}$ $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}@1\text{ MHz to }16\text{ MHz}$ LS (low-speed main) mode: $1.8\text{ V} \leq V_{DD} \leq 5.5\text{ V}@1\text{ MHz to }8\text{ MHz}$	HS (high-speed main) mode only: $2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}@1\text{ MHz to }24\text{ MHz}$ $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}@1\text{ MHz to }16\text{ MHz}$
High-speed on-chip oscillator clock accuracy	R5F102 products, $1.8\text{ V} \leq V_{DD} \leq 5.5\text{ V}$: $\pm 1.0\% @ T_A = -20$ to $+85^\circ\text{C}$ $\pm 1.5\% @ T_A = -40$ to -20°C R5F103 products, $1.8\text{ V} \leq V_{DD} \leq 5.5\text{ V}$: $\pm 5.0\% @ T_A = -40$ to $+85^\circ\text{C}$	R5F102 products, $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$: $\pm 2.0\% @ T_A = +85$ to $+105^\circ\text{C}$ $\pm 1.0\% @ T_A = -20$ to $+85^\circ\text{C}$ $\pm 1.5\% @ T_A = -40$ to -20°C
Serial array unit	UART CSI: $f_{CLK}/2$ (supporting 12 Mbps), $f_{CLK}/4$ Simplified I ² C communication	UART CSI: $f_{CLK}/4$ Simplified I ² C communication
Voltage detector	Rise detection voltage: 1.88 V to 4.06 V (12 levels) Fall detection voltage: 1.84 V to 3.98 V (12 levels)	Rise detection voltage: 2.61 V to 4.06 V (8 levels) Fall detection voltage: 2.55 V to 3.98 V (8 levels)

Remark The electrical characteristics of the products G: Industrial applications ($T_A = -40$ to $+105^\circ\text{C}$) are different from those of the products "A: Consumer applications, and D: Industrial applications". For details, refer to **3.1** to **3.10**.

3.1 Absolute Maximum Ratings

Absolute Maximum Ratings (TA = 25°C)

Parameter	Symbols	Conditions		Ratings	Unit
Supply Voltage	V _{DD}			-0.5 to +6.5	V
REGC terminal input voltage ^{Note1}	V _{I_{REGC}}	REGC		-0.3 to +2.8 and -0.3 to V _{DD} + 0.3 ^{Note 2}	V
Input Voltage	V _{I1}	Other than P60, P61		-0.3 to V _{DD} + 0.3 ^{Note 3}	V
	V _{I2}	P60, P61 (N-ch open drain)		-0.3 to 6.5	V
Output Voltage	V _O			-0.3 to V _{DD} + 0.3 ^{Note 3}	V
Analog input voltage	V _{AI}	20-, 24-pin products: ANI0 to ANI3, ANI16 to ANI22 30-pin products: ANI0 to ANI3, ANI16 to ANI19		-0.3 to V _{DD} + 0.3 and -0.3 to AV _{REF} (+)+0.3 ^{Notes 3, 4}	V
Output current, high	I _{OH1}	Per pin	Other than P20 to P23	-40	mA
		Total of all pins	All the terminals other than P20 to P23	-170	mA
			20-, 24-pin products: P40 to P42 30-pin products: P00, P01, P40, P120	-70	mA
			20-, 24-pin products: P00 to P03 ^{Note 5} , P10 to P14 30-pin products: P10 to P17, P30, P31, P50, P51, P147	-100	mA
	I _{OH2}	Per pin	P20 to P23	-0.5	mA
		Total of all pins		-2	mA
Output current, low	I _{OL1}	Per pin	Other than P20 to P23	40	mA
		Total of all pins	All the terminals other than P20 to P23	170	mA
			20-, 24-pin products: P40 to P42 30-pin products: P00, P01, P40, P120	70	mA
			20-, 24-pin products: P00 to P03 ^{Note 5} , P10 to P14, P60, P61 30-pin products: P10 to P17, P30, P31, P50, P51, P60, P61, P147	100	mA
	I _{OL2}	Per pin	P20 to P23	1	mA
		Total of all pins		5	mA
Operating ambient temperature	T _A			-40 to +105	°C
Storage temperature	T _{stg}			-65 to +150	°C

Notes 1. 30-pin product only.

2. Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μF). This value determines the absolute maximum rating of the REGC pin. Do not use it with voltage applied.
3. Must be 6.5 V or lower.
4. Do not exceed AV_{REF}(+) + 0.3 V in case of A/D conversion target pin.
5. 24-pin products only.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

- Remarks** 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
2. AV_{REF}(+) : + side reference voltage of the A/D converter.
 3. V_{SS} : Reference voltage

3.2 Oscillator Characteristics

3.2.1 X1 oscillator characteristics

(TA = -40 to +105°C, 2.4 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (fx) ^{Note}	Ceramic resonator / crystal oscillator	2.7 V ≤ VDD ≤ 5.5 V	1.0		20.0	MHz
		2.4 V ≤ VDD < 2.7 V	1.0		8.0	

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator, refer to 5.4 System Clock Oscillator in the RL78/G12 User's Manual.

3.2.2 On-chip oscillator characteristics

(TA = -40 to +105°C, 2.4 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit	
High-speed on-chip oscillator clock frequency ^{Notes 1, 2}	f _H		1		24	MHz	
High-speed on-chip oscillator clock frequency accuracy		R5F102 products	TA = -20 to +85°C	-1.0		+1.0	%
			TA = -40 to -20°C	-1.5		+1.5	%
			TA = +85 to +105°C	-2.0		+2.0	%
Low-speed on-chip oscillator clock frequency	f _L			15		kHz	
Low-speed on-chip oscillator clock frequency accuracy			-15		+15	%	

Notes 1. High-speed on-chip oscillator frequency is selected by bits 0 to 3 of option byte (000C2H) and bits 0 to 2 of HOCODIV register.

2. This only indicates the oscillator characteristics. Refer to AC Characteristics for instruction execution time.

3.3 DC Characteristics

3.3.1 Pin characteristics

(TA = -40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

(1/4)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit		
Output current, high ^{Note 1}	I _{OH1}	20-, 24-pin products: Per pin for P00 to P03 ^{Note 4} , P10 to P14, P40 to P42 30-pin products: Per pin for P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147			-3.0 ^{Note 2}	mA		
		20-, 24-pin products: Total of P40 to P42 30-pin products: Total of P00, P01, P40, P120 (When duty ≤ 70% ^{Note 3})	4.0 V ≤ V _{DD} ≤ 5.5 V			-9.0	mA	
			2.7 V ≤ V _{DD} < 4.0 V			-6.0	mA	
			2.4 V ≤ V _{DD} < 2.7 V			-4.5	mA	
		20-, 24-pin products: Total of P00 to P03 ^{Note 4} , P10 to P14 30-pin products: Total of P10 to P17, P30, P31, P50, P51, P147 (When duty ≤ 70% ^{Note 3}) Total of all pins (When duty ≤ 70% ^{Note 3})	4.0 V ≤ V _{DD} ≤ 5.5 V			-27.0	mA	
			2.7 V ≤ V _{DD} < 4.0 V			-18.0	mA	
			2.4 V ≤ V _{DD} < 2.7 V			-10.0	mA	
						-36.0	mA	
		I _{OH2}	Per pin for P20 to P23				-0.1	mA
			Total of all pins				-0.4	mA

- Notes**
- value of current at which the device operation is guaranteed even if the current flows from the V_{DD} pin to an output pin.
 - However, do not exceed the total current value.
 - The output current value under conditions where the duty factor ≤ 70%.
If duty factor > 70%: The output current value can be calculated with the following expression (where n represents the duty factor as a percentage).
 - Total output current of pins = (I_{OH} × 0.7)/(n × 0.01)
<Example> Where n = 80% and I_{OH} = -10.0 mA
Total output current of pins = (-10.0 × 0.7)/(80 × 0.01) ≅ -8.7 mA
 However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.
 - 24-pin products only.

Caution P10 to P12 and P41 for 20-pin products, P01, P10 to P12, and P41 for 24-pin products, and P00, P10 to P15, P17, and P50 for 30-pin products do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(TA = -40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

(2/4)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Output current, low ^{Note 1}	I _{OL1}	20-, 24-pin products: Per pin for P00 to P03 ^{Note 4} , P10 to P14, P40 to P42 30-pin products: Per pin for P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147			8.5 ^{Note 2}	mA
		Per pin for P60, P61			15.0 ^{Note 2}	mA
	20-, 24-pin products: Total of P40 to P42 30-pin products: Total of P00, P01, P40, P120 (When duty ≤ 70% ^{Note 3})	4.0 V ≤ V _{DD} ≤ 5.5 V			25.5	mA
		2.7 V ≤ V _{DD} < 4.0 V			9.0	mA
		2.4 V ≤ V _{DD} < 2.7 V			1.8	mA
	20-, 24-pin products: Total of P00 to P03 ^{Note 4} , P10 to P14, P60, P61 30-pin products: Total of P10 to P17, P30, P31, P50, P51, P60, P61, P147 (When duty ≤ 70% ^{Note 3})	4.0 V ≤ V _{DD} ≤ 5.5 V			40.0	mA
		2.7 V ≤ V _{DD} < 4.0 V			27.0	mA
		2.4 V ≤ V _{DD} < 2.7 V			5.4	mA
	Total of all pins (When duty ≤ 70% ^{Note 3})				65.5	mA
	I _{OL2}	Per pin for P20 to P23				0.4
Total of all pins					1.6	mA

Notes 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the V_{SS} pin.

2. However, do not exceed the total current value.

3. The output current value under conditions where the duty factor ≤ 70%.

If duty factor > 70%: The output current value can be calculated with the following expression (where n represents the duty factor as a percentage).

• Total output current of pins = (I_{OL} × 0.7)/(n × 0.01)

<Example> Where n = 80% and I_{OL} = 10.0 mA

$$\text{Total output current of pins} = (10.0 \times 0.7)/(80 \times 0.01) \cong 8.7 \text{ mA}$$

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

4. 24-pin products only.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(TA = -40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

(3/4)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input voltage, high	V _{IH1}	Normal input buffer 20-, 24-pin products: P00 to P03 ^{Note 2} , P10 to P14, P40 to P42 30-pin products: P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147	0.8V _{DD}		V _{DD}	V
	V _{IH2}	TTL input buffer 20-, 24-pin products: P10, P11 30-pin products: P01, P10, P11, P13 to P17	4.0 V ≤ V _{DD} ≤ 5.5 V	2.2	V _{DD}	V
			3.3 V ≤ V _{DD} < 4.0 V	2.0	V _{DD}	V
			2.4 V ≤ V _{DD} < 3.3 V	1.5	V _{DD}	V
	V _{IH3}	Normal input buffer P20 to P23	0.7V _{DD}		V _{DD}	V
	V _{IH4}	P60, P61	0.7V _{DD}		6.0	V
V _{IH5}	P121, P122, P125 ^{Note 1} , P137, EXCLK, RESET	0.8V _{DD}		V _{DD}	V	
Input voltage, low	V _{IL1}	Normal input buffer 20-, 24-pin products: P00 to P03 ^{Note 2} , P10 to P14, P40 to P42 30-pin products: P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147	0		0.2V _{DD}	V
	V _{IL2}	TTL input buffer 20-, 24-pin products: P10, P11 30-pin products: P01, P10, P11, P13 to P17	4.0 V ≤ V _{DD} ≤ 5.5 V	0	0.8	V
			3.3 V ≤ V _{DD} < 4.0 V	0	0.5	V
			2.4 V ≤ V _{DD} < 3.3 V	0	0.32	V
	V _{IL3}	P20 to P23	0		0.3V _{DD}	V
	V _{IL4}	P60, P61	0		0.3V _{DD}	V
V _{IL5}	P121, P122, P125 ^{Note 1} , P137, EXCLK, RESET	0		0.2V _{DD}	V	
Output voltage, high	V _{OH1}	20-, 24-pin products: P00 to P03 ^{Note 2} , P10 to P14, P40 to P42 30-pin products: P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147	4.0 V ≤ V _{DD} ≤ 5.5 V, I _{OH1} = -3.0 mA	V _{DD} -0.7		V
			2.7 V ≤ V _{DD} ≤ 5.5 V, I _{OH1} = -2.0 mA	V _{DD} -0.6		V
			2.4 V ≤ V _{DD} ≤ 5.5 V, I _{OH1} = -1.5 mA	V _{DD} -0.5		V
	V _{OH2}	P20 to P23	I _{OH2} = -100 μA	V _{DD} -0.5		V

Notes 1. 20, 24-pin products only.

2. 24-pin products only.

Caution The maximum value of V_{IH} of pins P10 to P12 and P41 for 20-pin products, P01, P10 to P12, and P41 for 24-pin products, and P00, P10 to P15, P17, and P50 for 30-pin products is V_{DD} even in N-ch open-drain mode.

High level is not output in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(TA = -40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

(4/4)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, low	V _{OL1}	20-, 24-pin products: P00 to P03 ^{Note} , P10 to P14, P40 to P42	4.0 V ≤ V _{DD} ≤ 5.5 V, I _{OL1} = 8.5 mA			0.7	V
			2.7 V ≤ V _{DD} ≤ 5.5 V, I _{OL1} = 3.0 mA			0.6	V
		30-pin products: P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147	2.7 V ≤ V _{DD} ≤ 5.5 V, I _{OL1} = 1.5 mA			0.4	V
			2.4 V ≤ V _{DD} ≤ 5.5 V, I _{OL1} = 0.6 mA			0.4	V
	V _{OL2}	P20 to P23	I _{OL2} = 400 μA			0.4	V
	V _{OL3}	P60, P61	4.0 V ≤ V _{DD} ≤ 5.5 V, I _{OL1} = 15.0 mA			2.0	V
			4.0 V ≤ V _{DD} ≤ 5.5 V, I _{OL1} = 5.0 mA			0.4	V
			2.7 V ≤ V _{DD} ≤ 5.5 V, I _{OL1} = 3.0 mA			0.4	V
2.4 V ≤ V _{DD} ≤ 5.5 V, I _{OL1} = 2.0 mA					0.4	V	
Input leakage current, high	I _{LIH1}	Other than P121, P122	V _I = V _{DD}			1	μA
	I _{LIH2}	P121, P122 (X1, X2/EXCLK)	V _I = V _{DD}	Input port or external clock input		1	μA
				When resonator connected		10	μA
Input leakage current, low	I _{LIL1}	Other than P121, P122	V _I = V _{SS}			-1	μA
	I _{LIL2}	P121, P122 (X1, X2/EXCLK)	V _I = V _{SS}	Input port or external clock input		-1	μA
When resonator connected					-10	μA	
On-chip pull-up resistance	R _U	20-, 24-pin products: P00 to P03 ^{Note} , P10 to P14, P40 to P42, P125, RESET 30-pin products: P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147	V _I = V _{SS} , input port	10	20	100	kΩ

Note 24-pin products only.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

3.3.2 Supply current characteristics

(1) 20-, 24-pin products

(TA = -40 to +105°C, 2.4 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

(1/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit	
Supply current ^{Note 1}	IDD1	Operating mode	HS (High-speed main) mode ^{Note 4}	f _{IH} = 24 MHz ^{Note 3}	Basic operation	V _{DD} = 5.0 V		1.5		mA
						V _{DD} = 3.0 V		1.5		
				Normal operation	V _{DD} = 5.0 V		3.3	5.3	mA	
					V _{DD} = 3.0 V		3.3	5.3		
				f _{IH} = 16 MHz ^{Note 3}	V _{DD} = 5.0 V		2.5	3.9	mA	
					V _{DD} = 3.0 V		2.5	3.9		
		f _{MX} = 20 MHz ^{Note 2} , V _{DD} = 5.0 V	Square wave input		2.8	4.7	mA			
			Resonator connection		3.0	4.8				
		f _{MX} = 20 MHz ^{Note 2} , V _{DD} = 3.0 V	Square wave input		2.8	4.7	mA			
			Resonator connection		3.0	4.8				
		f _{MX} = 10 MHz ^{Note 2} , V _{DD} = 5.0 V	Square wave input		1.8	2.8	mA			
			Resonator connection		1.8	2.8				
f _{MX} = 10 MHz ^{Note 2} , V _{DD} = 3.0 V	Square wave input		1.8	2.8	mA					
	Resonator connection		1.8	2.8						

Notes 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

- 2. When high-speed on-chip oscillator clock is stopped.
- 3. When high-speed system clock is stopped
- 4. Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.

HS (High speed main) mode: V_{DD} = 2.7 V to 5.5 V @1 MHz to 24 MHz
 V_{DD} = 2.4 V to 5.5 V @1 MHz to 16 MHz

- Remarks 1.** f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- 2. f_{IH}: high-speed on-chip oscillator clock frequency
 - 3. Temperature condition of the TYP. value is TA = 25°C.

(1) 20-, 24-pin products

(TA = -40 to +105°C, 2.4 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

(2/2)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit		
Supply current ^{Note 1}	IDD2 ^{Note 2}	HALT mode	HS (High-speed main) mode ^{Note 6}	f _{IH} = 24 MHz ^{Note 4}	V _{DD} = 5.0 V		440	2230	μA
					V _{DD} = 3.0 V		440	2230	
				f _{IH} = 16 MHz ^{Note 4}	V _{DD} = 5.0 V		400	1650	μA
					V _{DD} = 3.0 V		400	1650	
				f _{MX} = 20 MHz ^{Note 3} , V _{DD} = 5.0 V	Square wave input		280	1900	μA
					Resonator connection		450	2000	
				f _{MX} = 20 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		280	1900	μA
					Resonator connection		450	2000	
				f _{MX} = 10 MHz ^{Note 3} , V _{DD} = 5.0 V	Square wave input		190	1010	μA
					Resonator connection		260	1090	
				f _{MX} = 10 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		190	1010	μA
					Resonator connection		260	1090	
IDD3 ^{Note 5}	STOP mode	T _A = -40°C			0.19	0.50	μA		
		T _A = +25°C			0.24	0.50			
		T _A = +50°C			0.32	0.80			
		T _A = +70°C			0.48	1.20			
		T _A = +85°C			0.74	2.20			
		T _A = +105°C			1.50	10.20			

- Notes**
- Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - During HALT instruction execution by flash memory.
 - When high-speed on-chip oscillator clock is stopped.
 - When high-speed system clock is stopped.
 - Not including the current flowing into the 12-bit interval timer and watchdog timer.
 - Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.

HS (High speed main) mode: V_{DD} = 2.7 V to 5.5 V @1 MHz to 24 MHz

V_{DD} = 2.4 V to 5.5 V @1 MHz to 16 MHz

- Remarks**
- f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - f_{IH}: high-speed on-chip oscillator clock frequency
 - Except temperature condition of the TYP. value is T_A = 25°C, other than STOP mode

(2) 30-pin products

(TA = -40 to +105°C, 2.4 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

(1/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit	
Supply current ^{Note 1}	IDD1	Operating mode	HS (High-speed main) mode ^{Note 4}	f _{HI} = 24 MHz ^{Note 3}	Basic operation	V _{DD} = 5.0 V		1.5		mA
						V _{DD} = 3.0 V		1.5		
					Normal operation	V _{DD} = 5.0 V		3.7	5.8	mA
						V _{DD} = 3.0 V		3.7	5.8	
					f _{HI} = 16 MHz ^{Note 3}	V _{DD} = 5.0 V		2.7	4.2	mA
						V _{DD} = 3.0 V		2.7	4.2	
				f _{MX} = 20 MHz ^{Note 2} , V _{DD} = 5.0 V	Square wave input		3.0	4.9	mA	
					Resonator connection		3.2	5.0		
				f _{MX} = 20 MHz ^{Note 2} , V _{DD} = 3.0 V	Square wave input		3.0	4.9	mA	
					Resonator connection		3.2	5.0		
				f _{MX} = 10 MHz ^{Note 2} , V _{DD} = 5.0 V	Square wave input		1.9	2.9	mA	
					Resonator connection		1.9	2.9		
f _{MX} = 10 MHz ^{Note 2} , V _{DD} = 3.0 V	Square wave input		1.9	2.9	mA					
	Resonator connection		1.9	2.9						

- Notes**
- Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - When high-speed on-chip oscillator clock is stopped.
 - When high-speed system clock is stopped
 - Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.
 HS (High speed main) mode: V_{DD} = 2.7 V to 5.5 V @1 MHz to 24 MHz
 V_{DD} = 2.4 V to 5.5 V @1 MHz to 16 MHz

- Remarks**
- f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - f_{HI}: high-speed on-chip oscillator clock frequency
 - Temperature condition of the TYP. value is TA = 25°C.

(2) 30-pin products

(TA = -40 to +105°C, 2.4 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

(2/2)

Parameter	Symbol	Conditions			MIN.	TYP.	MAX.	Unit	
Supply current Note 1	IDD2 Note 2	HALT mode	HS (High-speed main) mode Note 6	f _{IH} = 24 MHz Note 4	V _{DD} = 5.0 V		440	2300	μA
					V _{DD} = 3.0 V		440	2300	
				f _{IH} = 16 MHz Note 4	V _{DD} = 5.0 V		400	1700	μA
					V _{DD} = 3.0 V		400	1700	
				f _{MX} = 20 MHz Note 3, V _{DD} = 5.0 V	Square wave input		280	1900	μA
					Resonator connection		450	2000	
				f _{MX} = 20 MHz Note 3, V _{DD} = 3.0 V	Square wave input		280	1900	μA
					Resonator connection		450	2000	
				f _{MX} = 10 MHz Note 3, V _{DD} = 5.0 V	Square wave input		190	1020	μA
					Resonator connection		260	1100	
				f _{MX} = 10 MHz Note 3, V _{DD} = 3.0 V	Square wave input		190	1020	μA
					Resonator connection		260	1100	
IDD3 Note 5	STOP mode	T _A = -40°C				0.18	0.50	μA	
		T _A = +25°C				0.23	0.50		
		T _A = +50°C				0.30	1.10		
		T _A = +70°C				0.46	1.90		
		T _A = +85°C				0.75	3.30		
		T _A = +105°C				2.94	15.30		

- Notes**
- Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - During HALT instruction execution by flash memory.
 - When high-speed on-chip oscillator clock is stopped.
 - When high-speed system clock is stopped.
 - Not including the current flowing into the 12-bit interval timer and watchdog timer.
 - Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.

HS (High speed main) mode: V_{DD} = 2.7 V to 5.5 V @1 MHz to 24 MHz

V_{DD} = 2.4 V to 5.5 V @1 MHz to 16 MHz

- Remarks**
- f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - f_{IH}: high-speed on-chip oscillator clock frequency
 - Except STOP mode, temperature condition of the TYP. value is T_A = 25°C.

(3) Peripheral functions (Common to all products)**(TA = -40 to +105°C, 2.4 V ≤ VDD ≤ 5.5 V, VSS = 0 V)**

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Low-speed onchip oscillator operating current	IFIL ^{Note 1}				0.20		μA
12-bit interval timer operating current	ITMKA ^{Notes 1, 2, 3}				0.02		μA
Watchdog timer operating current	IWDT ^{Notes 1, 2, 4}	f _{IL} = 15 kHz			0.22		μA
A/D converter operating current	IADC ^{Notes 1, 5}	When conversion at maximum speed	Normal mode, AV _{REFP} = V _{DD} = 5.0 V		1.30	1.70	mA
			Low voltage mode, AV _{REFP} = V _{DD} = 3.0 V		0.50	0.70	mA
A/D converter reference voltage operating current	IADREF ^{Note 1}				75.0		μA
Temperature sensor operating current	ITMPS ^{Note 1}				75.0		μA
LVD operating current	ILVD ^{Notes 1, 6}				0.08		μA
Self-programming operating current	IFSP ^{Notes 1, 8}				2.00	12.20	mA
BGO operating current	IBGO ^{Notes 1, 7}				2.00	12.20	mA
SNOOZE operating current	ISNOZ ^{Note 1}	ADC operation	The mode is performed ^{Note 9}		0.50	1.10	mA
			The A/D conversion operations are performed, Low voltage mode, AV _{REFP} = V _{DD} = 3.0 V		1.20	2.04	mA
		CSI/UART operation		0.70	1.54	mA	

Notes 1. Current flowing to the V_{DD}.

2. When high speed on-chip oscillator and high-speed system clock are stopped.

3. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator). The current value of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3}, and I_{FIL} and I_{TMKA} when the 12-bit interval timer operates.4. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The current value of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{WDT} when the watchdog timer operates.5. Current flowing only to the A/D converter. The current value of the RL78 microcontrollers is the sum of I_{DD1} or I_{DD2} and I_{ADC} when the A/D converter operates in an operation mode or the HALT mode.6. Current flowing only to the LVD circuit. The current value of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{LVD} when the LVD circuit operates.

7. Current flowing only during data flash rewrite.

8. Current flowing only during self programming.

9. For shift time to the SNOOZE mode, see **17.3.3 SNOOZE mode** in the RL78/G12 User's Manual.**Remarks** 1. f_{IL}: Low-speed on-chip oscillator clock frequency2. Temperature condition of the TYP. value is T_A = 25°C

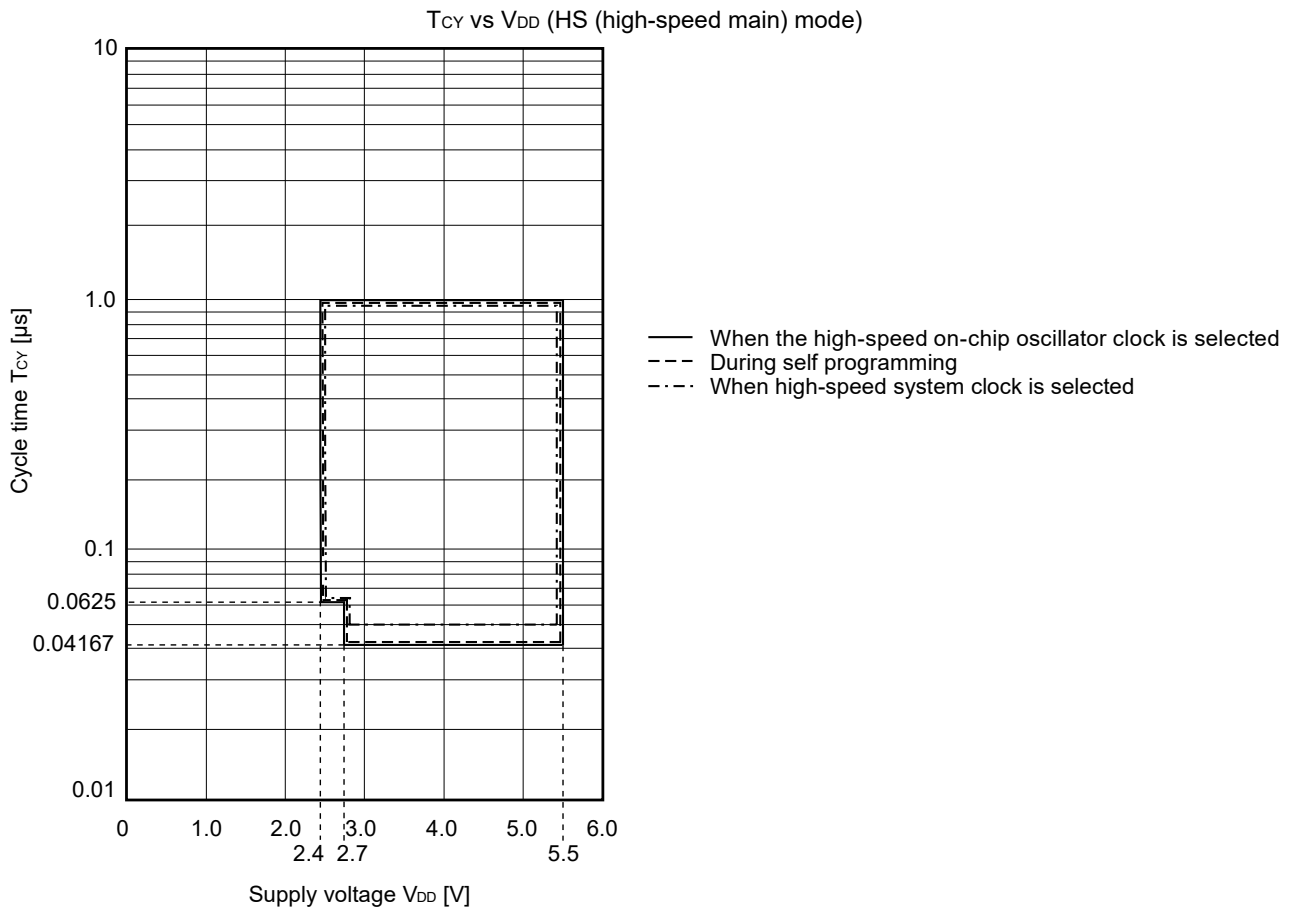
3.4 AC Characteristics

(TA = -40 to +105°C, 2.4 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

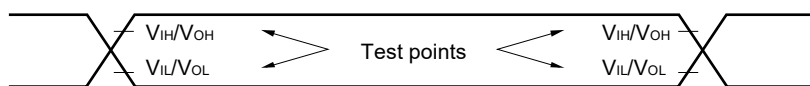
Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	TCY	Main system clock (fMAIN) operation	HS (High-speed main) mode	2.7 V ≤ VDD ≤ 5.5 V	0.04167	1	μs
				2.4 V ≤ VDD < 2.7 V	0.0625	1	μs
		During self programming	HS (High-speed main) mode	2.7 V ≤ VDD ≤ 5.5 V	0.04167	1	μs
				2.4 V ≤ VDD < 2.7 V	0.0625	1	μs
External main system clock frequency	fEX	2.7 V ≤ VDD ≤ 5.5 V		1.0		20.0	MHz
		2.4 V ≤ VDD < 2.7 V		1.0		16.0	MHz
External main system clock input high-level width, low-level width	tEXH, tEXL	2.7 V ≤ VDD ≤ 5.5 V		24			ns
		2.4 V ≤ VDD < 2.7 V		30			ns
TI00 to TI07 input high-level width, low-level width	tTIH, tTIL			1/fMCK + 10			ns
TO00 to TO07 output frequency	fTO	4.0 V ≤ VDD ≤ 5.5 V				12	MHz
		2.7 V ≤ VDD < 4.0 V				8	MHz
		2.4 V ≤ VDD < 2.7 V				4	MHz
PCLBUZ0, or PCLBUZ1 output frequency	fPCL	4.0 V ≤ VDD ≤ 5.5 V				16	MHz
		2.7 V ≤ VDD < 4.0 V				8	MHz
		2.4 V ≤ VDD < 2.7 V				4	MHz
INTP0 to INTP5 input high-level width, low-level width	tINTH, tINTL			1			μs
KR0 to KR9 input available width	tKR			250			ns
RESET low-level width	tRSL			10			μs

Remark fMCK: Timer array unit operation clock frequency
 (Operation clock to be set by the timer clock select register 0 (TPS0) and the CKS0n bit of timer mode register 0n (TMR0n). n: Channel number (n = 0 to 7))

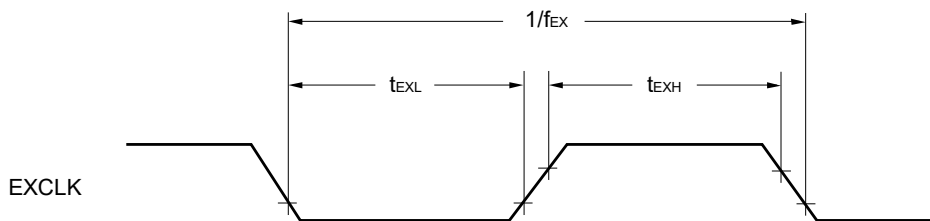
Minimum Instruction Execution Time during Main System Clock Operation



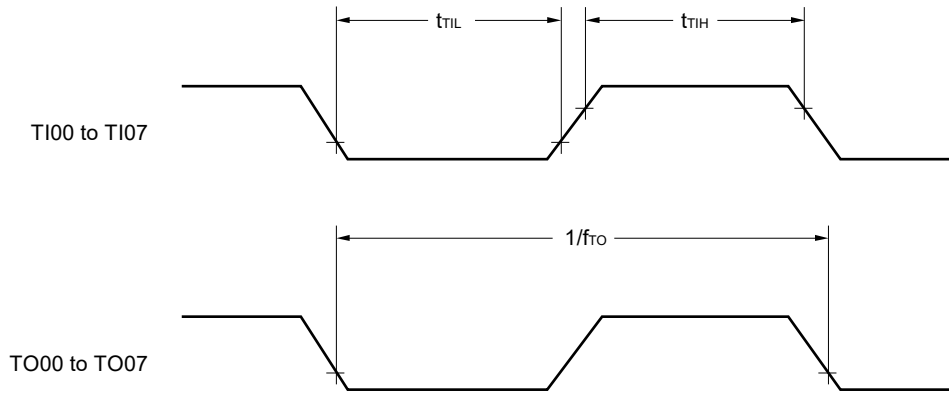
AC Timing Test Point



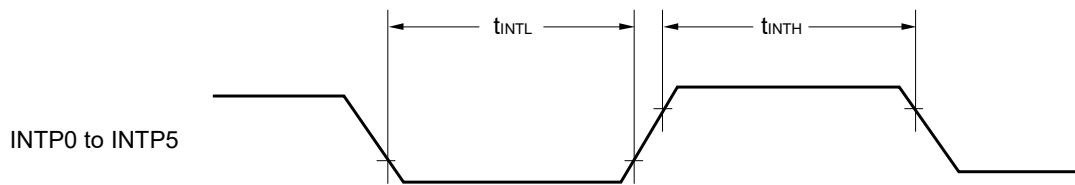
External Main System Clock Timing



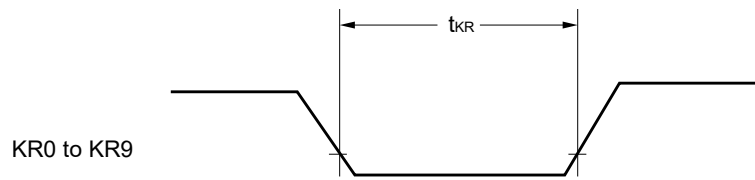
TI/TO Timing



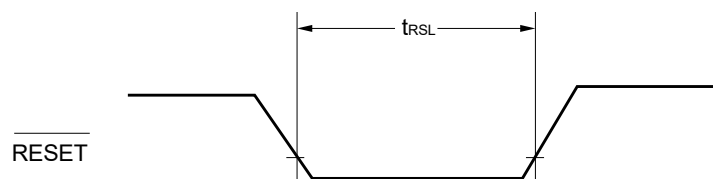
Interrupt Request Input Timing



Key Interrupt Input Timing

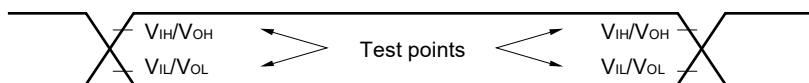


RESET Input Timing



3.5 Peripheral Functions Characteristics

AC Timing Test Point



3.5.1 Serial array unit

(1) During communication at same potential (UART mode)

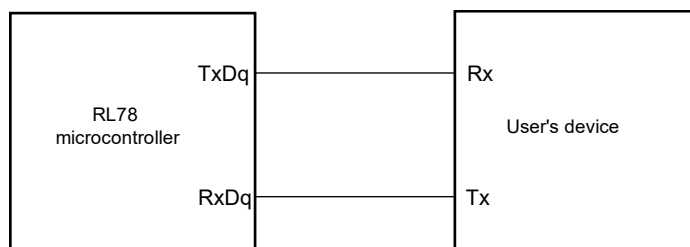
(TA = -40 to +105°C, 2.4 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
Transfer rate				fMCK/12	bps
Note 1		Theoretical value of the maximum transfer rate fCLK = fMCK ^{Note 2}		2.0	Mbps

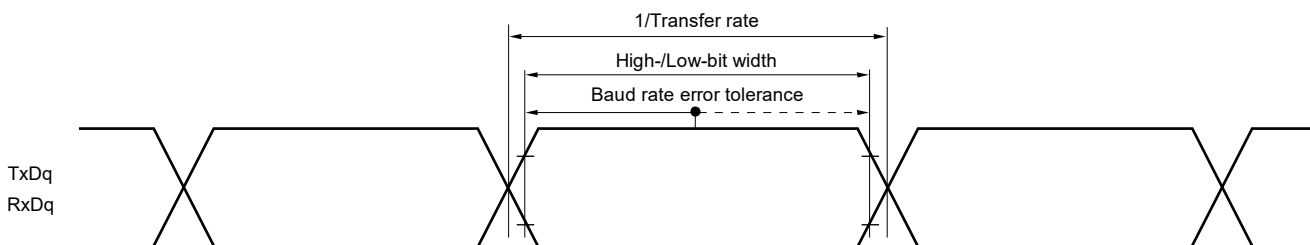
- Notes**
1. Transfer rate in the SNOOZE mode is 4800 bps only.
 2. The maximum operating frequencies of the CPU/peripheral hardware clock (fCLK) are:
 HS (high-speed main) mode: 24 MHz (2.7 V ≤ VDD ≤ 5.5 V)
 16 MHz (2.4 V ≤ VDD ≤ 5.5 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



- Remarks**
1. q: UART number (q = 0 to 2), g: PIM, POM number (g = 0, 1)
 2. fMCK: Serial array unit operation clock frequency
 (Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn).
 m: Unit number, n: Channel number (mn = 00 to 03, 10, 11))

(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output)
(TA = -40 to +105°C, 2.4 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit	
			MIN.	MAX.		
SCKp cycle time	t _{KCY1}	t _{KCY1} ≥ 4/f _{CLK}	2.7 V ≤ V _{DD} ≤ 5.5 V	334		ns
			2.4 V ≤ V _{DD} ≤ 5.5 V	500		ns
SCKp high-/low-level width	t _{KH1} , t _{KL1}	4.0 V ≤ V _{DD} ≤ 5.5 V	t _{KCY1} /2-24		ns	
		2.7 V ≤ V _{DD} ≤ 5.5 V	t _{KCY1} /2-36		ns	
		2.4 V ≤ V _{DD} ≤ 5.5 V	t _{KCY1} /2-76		ns	
Slp setup time (to SCKp↑) ^{Note 1}	t _{SIK1}	4.0 V ≤ V _{DD} ≤ 5.5 V	66		ns	
		2.7 V ≤ V _{DD} ≤ 5.5 V	66		ns	
		2.4 V ≤ V _{DD} ≤ 5.5 V	113		ns	
Slp hold time (from SCKp↑) ^{Note 2}	t _{KSI1}		38		ns	
Delay time from SCKp↓ to SOp output ^{Note 3}	t _{KSO1}	C = 30 pF ^{Note 4}		50	ns	

- Notes**
1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the Slp pin and the normal output mode for the SOp and SCKp pins by using port input mode register 1 (PIM1) and port output mode registers 0, 1, 4 (POM0, POM1, POM4).

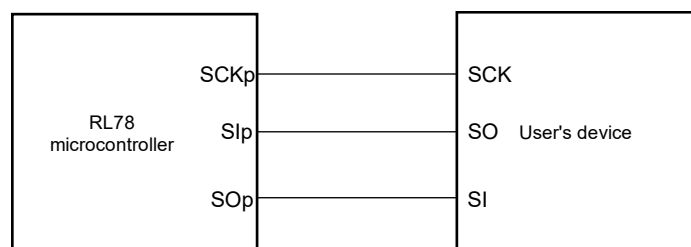
- Remarks**
1. p: CSI number (p = 00, 01, 11, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0, 1, 3)
 2. f_{MCK}: Serial array unit operation clock frequency
 (Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0, 1, 3))

(3) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input)**(TA = -40 to +105°C, 2.4 V ≤ VDD ≤ 5.5 V, VSS = 0 V)**

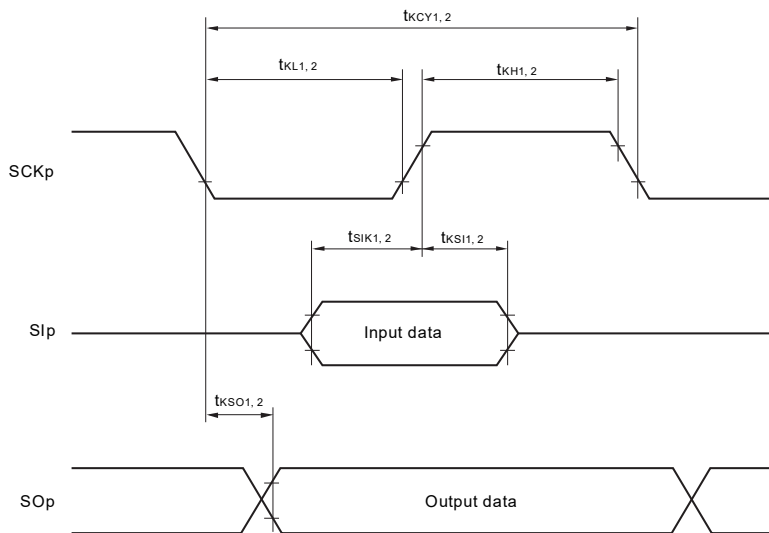
Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time ^{Note 5}	t _{KCY2}	4.0 V ≤ V _{DD} ≤ 5.5 V	20 MHz < f _{MCK}	16/f _{MCK}		ns
			f _{MCK} ≤ 20 MHz	12/f _{MCK}		ns
		2.7 V ≤ V _{DD} ≤ 5.5 V	16 MHz < f _{MCK}	16/f _{MCK}		ns
			f _{MCK} ≤ 16 MHz	12/f _{MCK}		ns
2.4 V ≤ V _{DD} ≤ 5.5 V		12/f _{MCK} and 1000		ns		
SCKp high-/low-level width	t _{KH2} ,	4.0 V ≤ V _{DD} ≤ 5.5 V		t _{KCY2} /2-14		ns
	t _{KL2}	2.7 V ≤ V _{DD} ≤ 5.5 V		t _{KCY2} /2-16		ns
		2.4 V ≤ V _{DD} ≤ 5.5 V		t _{KCY2} /2-36		ns
Slp setup time (to SCKp↑) ^{Note 1}	t _{SIK2}	2.7 V ≤ V _{DD} ≤ 5.5 V		1/f _{MCK} + 40		ns
		2.4 V ≤ V _{DD} ≤ 5.5 V		1/f _{MCK} + 60		ns
Slp hold time (from SCKp↑) ^{Note 2}	t _{KSI2}			1/f _{MCK} + 62		ns
Delay time from SCKp↓ to SOp output ^{Note 3}	t _{KSO2}	C = 30 pF ^{Note 4}	2.7 V ≤ V _{DD} ≤ 5.5 V		2/f _{MCK} + 66	ns
			2.4 V ≤ V _{DD} ≤ 5.5 V		2/f _{MCK} + 113	ns

- Notes**
1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 4. C is the load capacitance of the SOp output lines.
 5. Transfer rate in the SNOOZE mode: MAX. 1 Mbps.

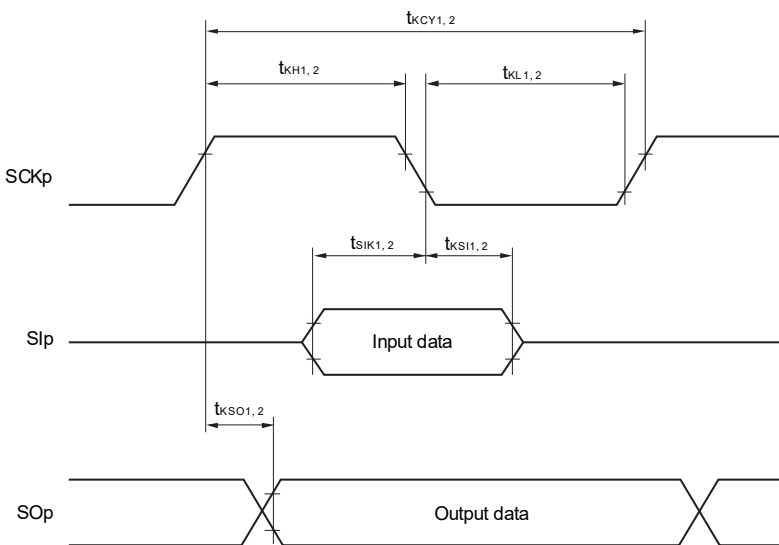
Caution Select the normal input buffer for the Slp and SCKp pins and the normal output mode for the SOp pin by using port input mode register 1 (PIM1) and port output mode registers 0, 1, 4 (POM0, POM1, POM4).

CSI mode connection diagram (during communication at same potential)

**CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)**



**CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)**



- Remarks 1.** p: CSI number (p = 00, 01, 11, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0, 1, 3)
- 2.** f_{MCK} : Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0,1), n: Channel number (n = 0, 1, 3))

(4) During communication at same potential (simplified I²C mode)

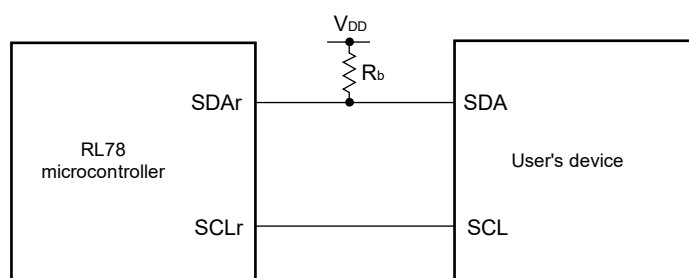
(TA = -40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCLr clock frequency	f _{SCL}	C _b = 100 pF, R _b = 3 kΩ		100 ^{Note 1}	kHz
Hold time when SCLr = "L"	t _{LOW}	C _b = 100 pF, R _b = 3 kΩ	4600		ns
Hold time when SCLr = "H"	t _{HIGH}	C _b = 100 pF, R _b = 3 kΩ	4600		ns
Data setup time (reception)	t _{SU:DAT}	C _b = 100 pF, R _b = 3 kΩ	1/f _{MCK} + 580 ^{Note 2}		ns
Data hold time (transmission)	t _{HD:DAT}	C _b = 100 pF, R _b = 3 kΩ	0	1420	ns

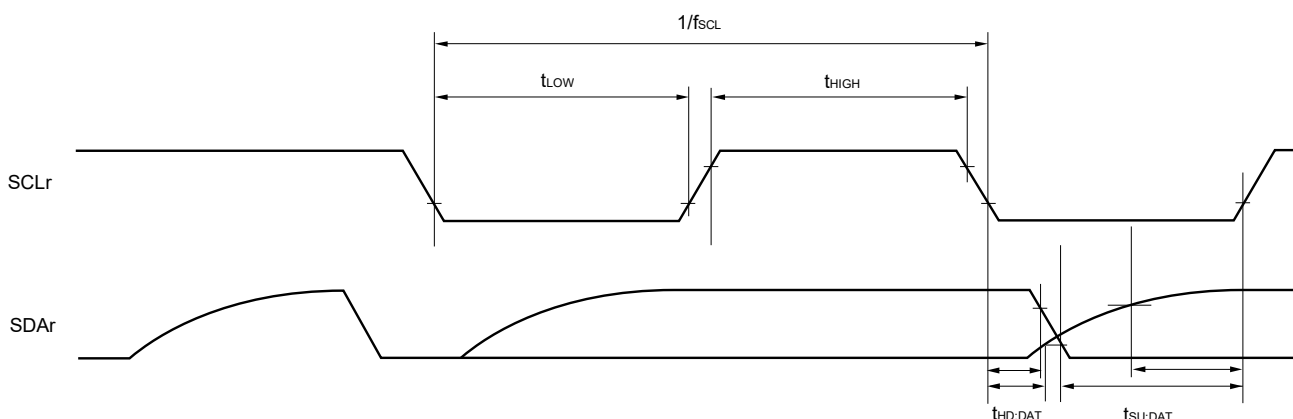
- Notes**
- The value must be equal to or less than f_{MCK}/4.
 - Set t_{SU:DAT} so that it will not exceed the hold time when SCLr = "L" or SCLr = "H".

Caution Select the N-ch open drain output (V_{DD} tolerance) mode for SDAr by using port output mode register h (POMh).

Simplified I²C mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



- Remarks**
- R_b [Ω]: Communication line (SDAr) pull-up resistance

C_b [F]: Communication line (SCLr, SDAr) load capacitance
 - r: IIC number (r = 00, 01, 11, 20), h: = POM number (h = 0, 1, 4, 5)
 - f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn).
m: Unit number (m = 0, 1), n: Channel number (0, 1, 3))

(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)

(TA = -40 to +105°C, 2.4 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
Transfer rate ^{Note4}		Reception	4.0 V ≤ VDD ≤ 5.5 V, 2.7 V ≤ Vb ≤ 4.0 V		fMCK/12 Note 1	bps
				Theoretical value of the maximum transfer rate fMCK = fCLK ^{Note 2}	2.0	Mbps
			2.7 V ≤ VDD < 4.0 V, 2.3 V ≤ Vb ≤ 2.7 V		fMCK/12 Note 1	bps
				Theoretical value of the maximum transfer rate fMCK = fCLK ^{Note 2}	2.0	Mbps
			2.4 V ≤ VDD < 3.3 V, 1.6 V ≤ Vb ≤ 2.0 V		fMCK/12 Note 1	bps
				Theoretical value of the maximum transfer rate fMCK = fCLK ^{Note 2}	2.0	Mbps
		Transmission	4.0 V ≤ VDD ≤ 5.5 V, 2.7 V ≤ Vb ≤ 4.0 V		Note 3	bps
				Theoretical value of the maximum transfer rate Cb = 50 pF, Rb = 1.4 kΩ, Vb = 2.7 V	2.0 Note 4	Mbps
			2.7 V ≤ VDD < 4.0 V, 2.3 V ≤ Vb ≤ 2.7 V,		Note 5	bps
				Theoretical value of the maximum transfer rate Cb = 50 pF, Rb = 2.7 kΩ, Vb = 2.3 V	1.2 Note 6	Mbps
			2.4 V ≤ VDD < 3.3 V, 1.6 V ≤ Vb ≤ 2.0 V		Notes 2, 7	bps
				Theoretical value of the maximum transfer rate Cb = 50 pF, Rb = 5.5 kΩ, Vb = 1.6 V	0.43 Note 8	Mbps

- Notes**
- Transfer rate in the SNOOZE mode is 4800 bps only.
 - The maximum operating frequencies of the CPU/peripheral hardware clock (fCLK) are:
HS (high-speed main) mode: 24 MHz (2.7 V ≤ VDD ≤ 5.5 V)
16 MHz (2.4 V ≤ VDD ≤ 5.5 V)
 - The smaller maximum transfer rate derived by using fMCK/12 or the following expression is the valid maximum transfer rate.
Expression for calculating the transfer rate when 4.0 V ≤ VDD ≤ 5.5 V and 2.7 V ≤ Vb ≤ 4.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

4. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to **Note 3** above to calculate the maximum transfer rate under conditions of the customer.
5. The smaller maximum transfer rate derived by using $f_{MCK}/12$ or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when $2.7 \text{ V} \leq V_{DD} < 4.0 \text{ V}$ and $2.3 \text{ V} \leq V_b \leq 2.7 \text{ V}$

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\} \times 3} \quad [\text{bps}]$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

6. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to **Note 5** above to calculate the maximum transfer rate under conditions of the customer.
7. The smaller maximum transfer rate derived by using $f_{MCK}/12$ or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when $2.4 \text{ V} \leq V_{DD} < 3.3 \text{ V}$, $1.6 \text{ V} \leq V_b \leq 2.0 \text{ V}$

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\} \times 3} \quad [\text{bps}]$$

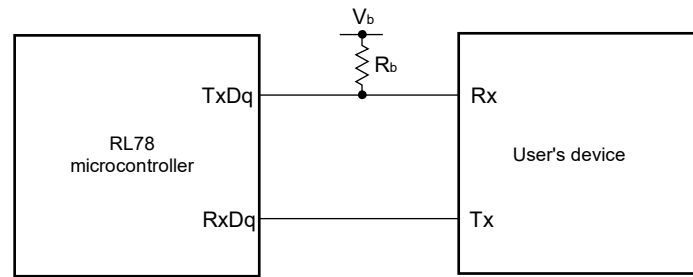
$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

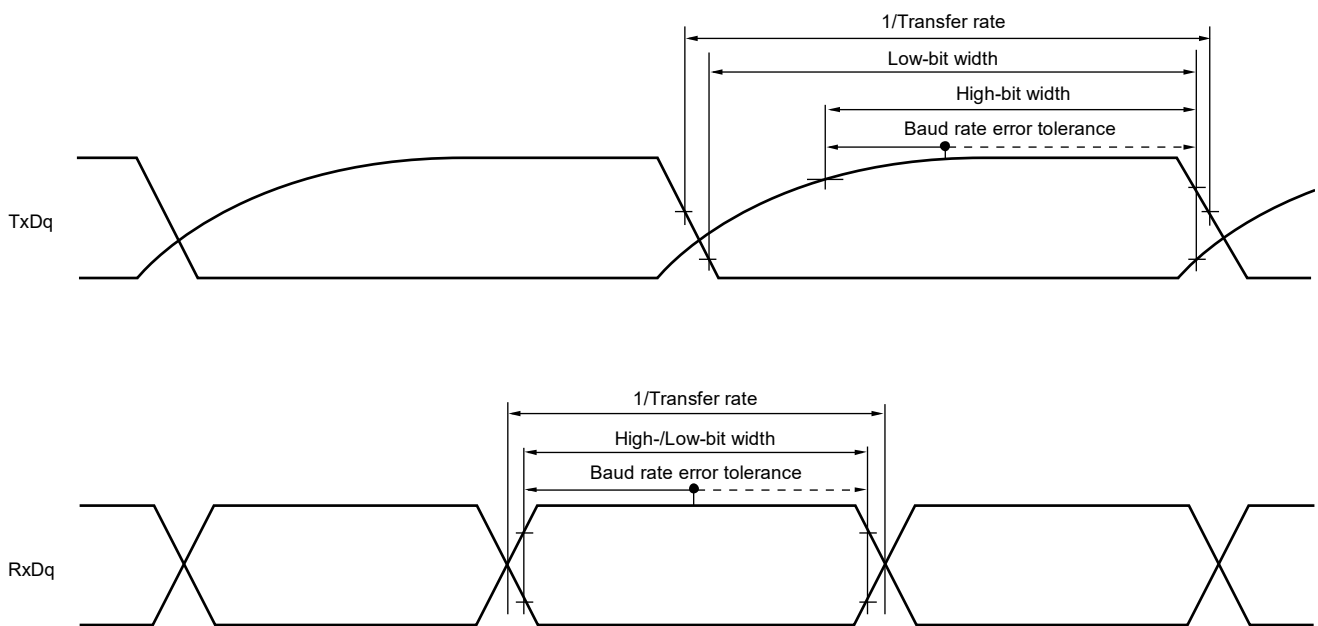
8. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to **Note 7** above to calculate the maximum transfer rate under conditions of the customer.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.

UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)



- Remarks**
1. $R_b[\Omega]$: Communication line (TxDq) pull-up resistance, $C_b[F]$: Communication line (TxDq) load capacitance, $V_b[V]$: Communication line voltage
 2. q: UART number (q = 0 to 2), g: PIM and POM number (g = 0, 1)
 3. f_{MCK} : Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPS_m) and the CKS_{mn} bit of serial mode register mn (SMR_{mn}).
m: Unit number, n: Channel number (mn = 00 to 03, 10, 11))
 4. UART0 of the 20- and 24-pin products supports communication at different potential only when the peripheral I/O redirection function is not used.

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (1/3)**(TA = -40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)**

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCKp cycle time	t _{KCY1}	t _{KCY1} ≥ 4/f _{CLK} 4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ	600		ns
		2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ	1000		ns
		2.4 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V, C _b = 30 pF, R _b = 5.5 kΩ	2300		ns
SCKp high-level width	t _{KH1}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ	t _{KCY1} /2 - 150		ns
		2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ	t _{KCY1} /2 - 340		ns
		2.4 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V, C _b = 30 pF, R _b = 5.5 kΩ	t _{KCY1} /2 - 916		ns
SCKp low-level width	t _{KL1}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ	t _{KCY1} /2 - 24		ns
		2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ	t _{KCY1} /2 - 36		ns
		2.4 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V, C _b = 30 pF, R _b = 5.5 kΩ	t _{KCY1} /2 - 100		ns

Cautions 1. Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

2. CSI01 and CSI11 cannot communicate at different potential.

Remarks 1. R_b [Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b [F]: Communication line (SCKp, SOp) load capacitance, V_b [V]: Communication line voltage

2. p: CSI number (p = 00, 20)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (2/3)**(TA = -40 to +105°C, 2.4 V ≤ VDD ≤ 5.5 V, VSS = 0 V)**

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
Slp setup time (to SCKp↑) <small>Note</small>	t _{SIK1}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ	162		ns
		2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ	354		ns
		2.4 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V, C _b = 30 pF, R _b = 5.5 kΩ	958		ns
Slp hold time (from SCKp↑) <small>Note</small>	t _{KSI1}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ	38		ns
		2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ	38		ns
		2.4 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V, C _b = 30 pF, R _b = 5.5 kΩ	38		ns
Delay time from SCKp↓ to SO _p output <small>Note</small>	t _{KSO1}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ		200	ns
		2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ		390	ns
		2.4 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V, C _b = 30 pF, R _b = 5.5 kΩ		966	ns

Note When DAP_mn = 0 and CKP_mn = 0, or DAP_mn = 1 and CKP_mn = 1.

(Cautions and Remarks are listed on the next page.)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (3/3)

(TA = -40 to +105°C, 2.4 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

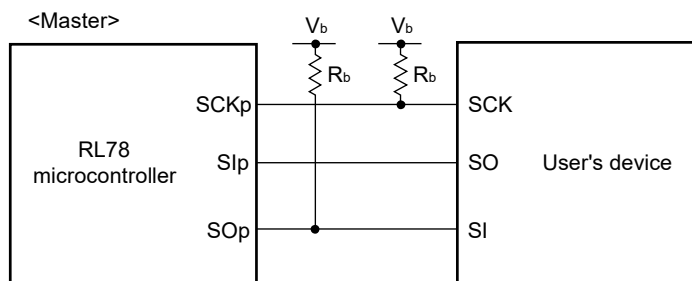
Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
Slp setup time (to SCKp↓) <small>Note</small>	t _{SIK1}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ	88		ns
		2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ	88		ns
		2.4 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V, C _b = 30 pF, R _b = 5.5 kΩ	220		ns
Slp hold time (from SCKp↓) <small>Note</small>	t _{KSI1}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ	38		ns
		2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ	38		ns
		2.4 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V, C _b = 30 pF, R _b = 5.5 kΩ	38		ns
Delay time from SCKp↑ to SO _p output <small>Note</small>	t _{KSO1}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 30 pF, R _b = 1.4 kΩ		50	ns
		2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ		50	ns
		2.4 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V, C _b = 30 pF, R _b = 5.5 kΩ		50	ns

Note When DAP_mn = 0 and CKP_mn = 1, or DAP_mn = 1 and CKP_mn = 0.

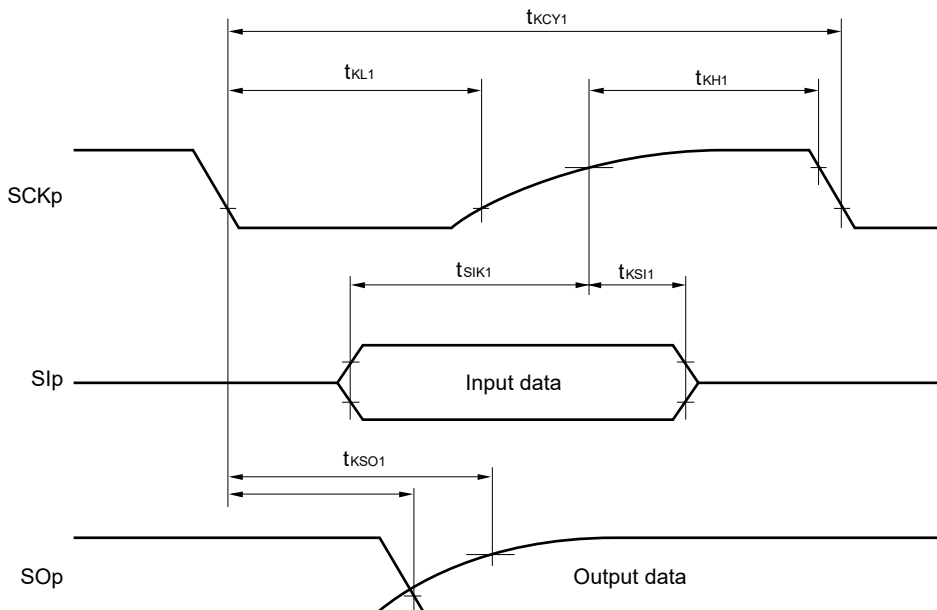
- Cautions 1.** Select the TTL input buffer for the Slp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SO_p pin and SCKp pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.
- 2.** CSI01 and CSI11 cannot communicate at different potential.

- Remarks 1.** R_b [Ω]: Communication line (SCKp, SO_p) pull-up resistance, C_b [F]: Communication line (SCKp, SO_p) load capacitance, V_b [V]: Communication line voltage
- 2.** p: CSI number (p = 00, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0)

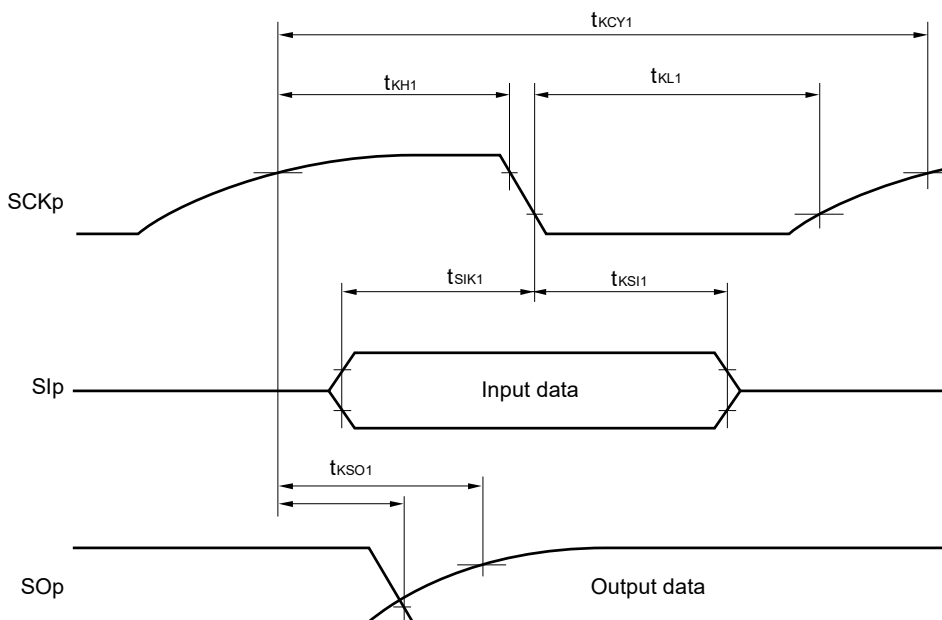
CSI mode connection diagram (during communication at different potential)



CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1)



CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark p: CSI number (p = 00, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0)

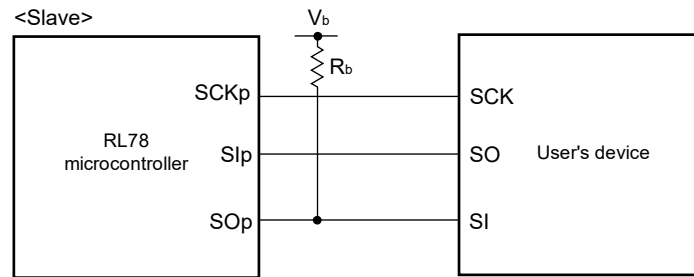
(7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)
(TA = -40 to +105°C, 2.4 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time ^{Note 1}	tkCY2	4.0 V ≤ VDD ≤ 5.5 V, 2.7 V ≤ Vb ≤ 4.0 V	20 MHz < fMCK ≤ 24 MHz	24/fMCK		ns
			8 MHz < fMCK ≤ 20 MHz	20/fMCK		ns
			4 MHz < fMCK ≤ 8 MHz	16/fMCK		ns
			fMCK ≤ 4 MHz	12/fMCK		ns
		2.7 V ≤ VDD < 4.0 V, 2.3 V ≤ Vb ≤ 2.7 V	20 MHz < fMCK ≤ 24 MHz	32/fMCK		ns
			16 MHz < fMCK ≤ 20 MHz	28/fMCK		ns
			8 MHz < fMCK ≤ 16 MHz	24/fMCK		ns
			4 MHz < fMCK ≤ 8 MHz	16/fMCK		ns
		2.4 V ≤ VDD < 3.3 V, 1.6 V ≤ Vb ≤ 2.0 V	fMCK ≤ 4 MHz	12/fMCK		ns
			20 MHz < fMCK ≤ 24 MHz	72/fMCK		ns
			16 MHz < fMCK ≤ 20 MHz	64/fMCK		ns
			8 MHz < fMCK ≤ 16 MHz	52/fMCK		ns
	4 MHz < fMCK ≤ 8 MHz	32/fMCK		ns		
	fMCK ≤ 4 MHz	20/fMCK		ns		
	SCKp high-/low-level width	tkH2, tkL2	4.0 V ≤ VDD ≤ 5.5 V, 2.7 V ≤ Vb ≤ 4.0 V	tkCY2/2 - 24		ns
			2.7 V ≤ VDD < 4.0 V, 2.3 V ≤ Vb ≤ 2.7 V	tkCY2/2 - 36		ns
2.4 V ≤ VDD < 3.3 V, 1.6 V ≤ Vb ≤ 2.0 V			tkCY2/2 - 100		ns	
Slp setup time (to SCKp↑) ^{Note 2}	tsIK2	4.0 V ≤ VDD ≤ 5.5 V, 2.7 V ≤ VDD ≤ 4.0 V	1/fMCK + 40		ns	
		2.7 V ≤ VDD < 4.0 V, 2.3 V ≤ Vb ≤ 2.7 V	1/fMCK + 40		ns	
		2.4 V ≤ VDD < 3.3 V, 1.6 V ≤ VDD ≤ 2.0 V	1/fMCK + 60		ns	
Slp hold time (from SCKp↑) ^{Note 3}	tkSI2		1/fMCK + 62		ns	
Delay time from SCKp↓ to SOP output ^{Note 4}	tkSO2	4.0 V ≤ VDD ≤ 5.5 V, 2.7 V ≤ Vb ≤ 4.0 V, Cb = 30 pF, Rb = 1.4 kΩ		2/fMCK + 240	ns	
		2.7 V ≤ VDD < 4.0 V, 2.3 V ≤ Vb ≤ 2.7 V, Cb = 30 pF, Rb = 2.7 kΩ		2/fMCK + 428	ns	
		2.4 V ≤ VDD < 3.3 V, 1.6 V ≤ Vb ≤ 2.0 V, Cb = 30 pF, Rb = 5.5 kΩ		2/fMCK + 1146	ns	

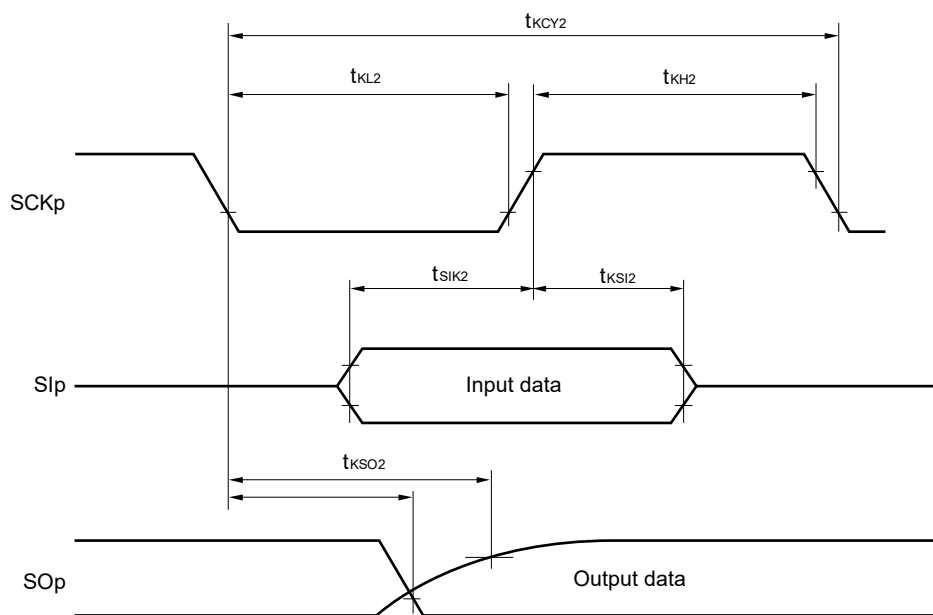
- Notes**
1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps
 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOP output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

- Cautions**
1. Select the TTL input buffer for the Slp and SCKp pins and the N-ch open drain output (VDD tolerance) mode for the SOP pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). For VIH and VIL, see the DC characteristics with TTL input buffer selected.
 2. CSI01 and CSI11 cannot communicate at different potential.

CSI mode connection diagram (during communication at different potential)

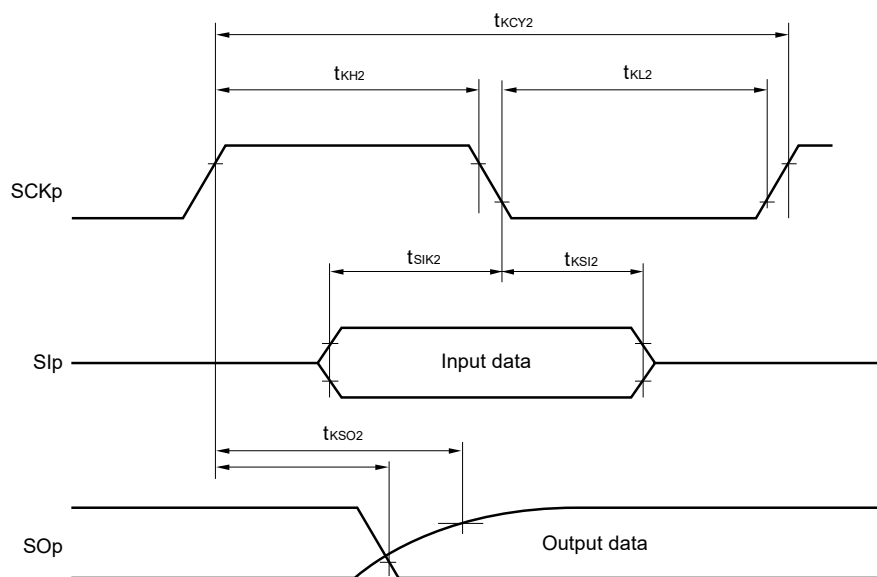


**CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)**



- Remarks**
1. R_b [Ω]: Communication line (SO_p) pull-up resistance, C_b [F]: Communication line (SO_p) load capacitance, V_b [V]: Communication line voltage
 2. p: CSI number (p = 00, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0)
 3. f_{MCK} : Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPS_m) and the CKS_{mn} bit of serial mode register mn (SMR_{mn}))

CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark p: CSI number (p = 00, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0)

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode)**(T_A = -40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)**

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCLr clock frequency	f _{SCL}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 100 pF, R _b = 2.8 kΩ		100 ^{Note1}	kHz
		2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 100 pF, R _b = 2.7 kΩ		100 ^{Note1}	kHz
		2.4 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V, C _b = 100 pF, R _b = 5.5 kΩ		100 ^{Note1}	kHz
Hold time when SCLr = "L"	t _{LOW}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 100 pF, R _b = 2.8 kΩ	4600		ns
		2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 100 pF, R _b = 2.7 kΩ	4600		ns
		2.4 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V, C _b = 100 pF, R _b = 5.5 kΩ	4650		ns
Hold time when SCLr = "H"	t _{HIGH}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 100 pF, R _b = 2.8 kΩ	2700		ns
		2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 100 pF, R _b = 2.7 kΩ	2400		ns
		2.4 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V, C _b = 100 pF, R _b = 5.5 kΩ	1830		ns
Data setup time (reception)	t _{SU:DAT}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 100 pF, R _b = 2.8 kΩ	1/f _{MCK} + 760 ^{Note2}		ns
		2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 100 pF, R _b = 2.7 kΩ	1/f _{MCK} + 760 ^{Note2}		ns
		2.4 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V, C _b = 100 pF, R _b = 5.5 kΩ	1/f _{MCK} + 570 ^{Note2}		ns
Data hold time (transmission)	t _{HD:DAT}	4.0 V ≤ V _{DD} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V, C _b = 100 pF, R _b = 2.8 kΩ	0	1420	ns
		2.7 V ≤ V _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 100 pF, R _b = 2.7 kΩ	0	1420	ns
		2.4 V ≤ V _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V, C _b = 100 pF, R _b = 5.5 kΩ	0	1215	ns

Notes 1. The value must be equal to or less than f_{MCK}/4.

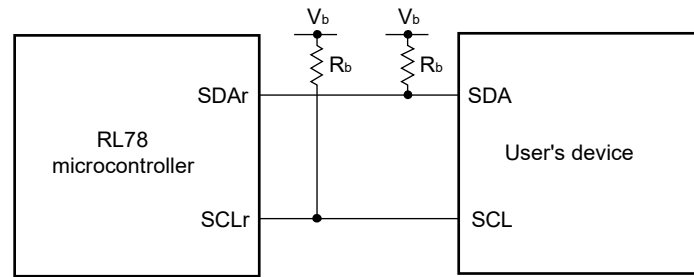
2. Set t_{SU:DAT} so that it will not exceed the hold time when SCLr = "L" or SCLr = "H".

Cautions 1. Select the TTL input buffer and the N-ch open drain output (V_{DD} tolerance) mode for the SDAr pin and the N-ch open drain output (V_{DD} tolerance) mode for the SCLr pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

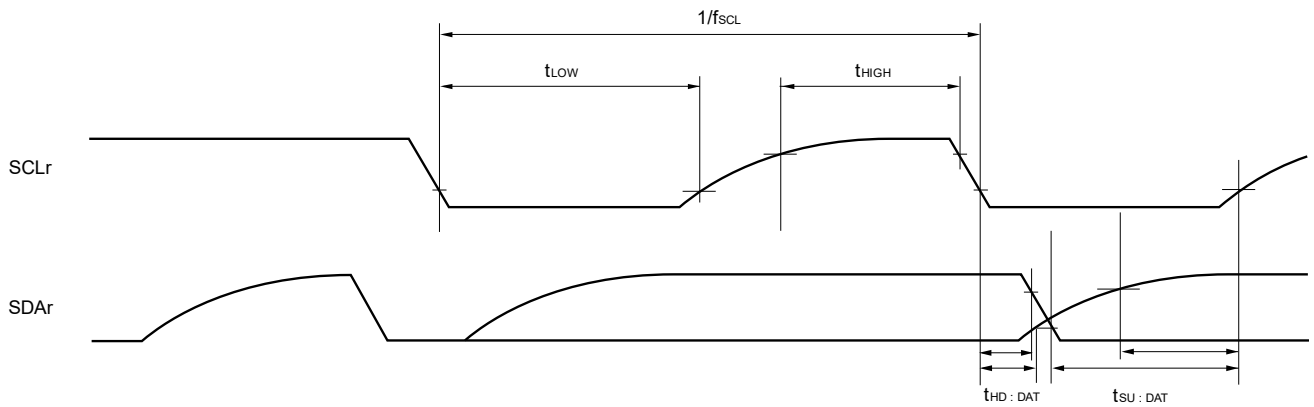
2. IIC01 and IIC11 cannot communicate at different potential.

(Remarks are listed on the next page.)

Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



- Remarks**
1. R_b [Ω]: Communication line (SDAr, SCLr) pull-up resistance, C_b [F]: Communication line (SDAr, SCLr) load capacitance, V_b [V]: Communication line voltage
 2. r: IIC Number (r = 00, 20)
 3. f_{MCK} : Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn).
m: Unit number (m = 0,1), n: Channel number (n = 0))

3.5.2 Serial interface IICA

(TA = -40 to +105°C, 2.4 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) mode				Unit
			Standard Mode		Fast Mode		
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	f _{SCL}	Fast mode: f _{CLK} ≥ 3.5 MHz			0	400	kHz
		Normal mode: f _{CLK} ≥ 1 MHz	0	100			
Setup time of restart condition	t _{SU:STA}		4.7		0.6		μs
Hold time ^{Note 1}	t _{HD:STA}		4.0		0.6		μs
Hold time when SCLA0 = "L"	t _{LOW}		4.7		1.3		μs
Hold time when SCLA0 = "H"	t _{HIGH}		4.0		0.6		μs
Data setup time (reception)	t _{SU:DAT}		250		100		ns
Data hold time (transmission) ^{Note 2}	t _{HD:DAT}		0	3.45	0	0.9	μs
Setup time of stop condition	t _{SU:STO}		4.0		0.6		μs
Bus-free time	t _{BUF}		4.7		1.3		μs

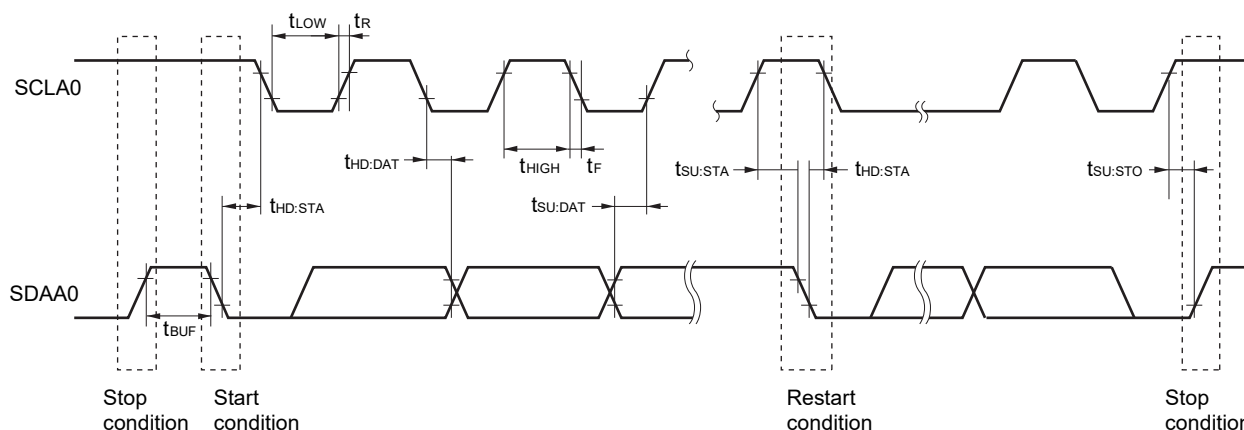
- Notes**
- The first clock pulse is generated after this period when the start/restart condition is detected.
 - The maximum value (MAX.) of t_{HD:DAT} is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution Only in the 30-pin products, the values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (I_{OH1}, I_{OL1}, V_{OH1}, V_{OL1}) must satisfy the values in the redirect destination.

Remark The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.

Normal mode: C_b = 400 pF, R_b = 2.7 kΩ
 Fast mode: C_b = 320 pF, R_b = 1.1 kΩ

IICA serial transfer timing



3.6 Analog Characteristics

3.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Input channel	Reference Voltage		
	Reference voltage (+) = AV _{REFP} Reference voltage (-) = AV _{REFM}	Reference voltage (+) = V _{DD} Reference voltage (-) = V _{SS}	Reference voltage (+) = V _{BGR} Reference voltage (-) = AV _{REFM}
ANI0 to ANI3	Refer to 3.6.1 (1).	Refer to 3.6.1 (3).	Refer to 3.6.1 (4).
ANI16 to ANI22	Refer to 3.6.1 (2).		
Internal reference voltage Temperature sensor output voltage	Refer to 3.6.1 (1).		-

(1) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), target pin: ANI2, ANI3, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +105°C, 2.4 V ≤ AV_{REFP} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, Reference voltage (+) = AV_{REFP}, Reference voltage (-) = AV_{REFM} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES		8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}		1.2	±3.5	LSB
Conversion time	t _{CONV}	10-bit resolution Target pin: ANI2, ANI3	3.6 V ≤ V _{DD} ≤ 5.5 V	2.125	39	μs
			2.7 V ≤ V _{DD} ≤ 5.5 V	3.1875	39	μs
			2.4 V ≤ V _{DD} ≤ 5.5 V	17	39	μs
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V ≤ V _{DD} ≤ 5.5 V	2.375	39	μs
			2.7 V ≤ V _{DD} ≤ 5.5 V	3.5625	39	μs
			2.4 V ≤ V _{DD} ≤ 5.5 V	17	39	μs
Zero-scale error ^{Notes 1, 2}	EZS	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}			±0.25	%FSR
Full-scale error ^{Notes 1, 2}	EFS	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}			±0.25	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}			±2.5	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}			±1.5	LSB
Analog input voltage	V _{AIN}	ANI2, ANI3	0		AV _{REFP}	V
		Internal reference voltage (HS (high-speed main) mode)		V _{BGR} ^{Note 4}		V
		Temperature sensor output voltage (HS (high-speed main) mode)		V _{TMPS25} ^{Note 4}		V

(Notes are listed on the next page.)

- Notes**
1. Excludes quantization error ($\pm 1/2$ LSB).
 2. This value is indicated as a ratio (%FSR) to the full-scale value.
 3. When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.
 Overall error: Add ± 1.0 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.
 Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when $AV_{REFP} = V_{DD}$.
 Integral linearity error/ Differential linearity error: Add ± 0.5 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.
 4. Refer to **3.6.2 Temperature sensor/internal reference voltage characteristics**.

(2) When reference voltage (+) = $AV_{REFP}/ANI0$ (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = $AV_{REFM}/ANI1$ (ADREFM = 1), target pin: ANI16 to ANI22

(TA = -40 to +105°C, 2.4 V \leq $AV_{REFP} \leq$ $V_{DD} \leq$ 5.5 V, $V_{SS} = 0$ V, Reference voltage (+) = AV_{REFP} , Reference voltage (-) = $AV_{REFM} = 0$ V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES		8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}		1.2	± 5.0	LSB
Conversion time	t _{CONV}	10-bit resolution Target ANI pin: ANI16 to ANI22	$3.6 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$	2.125	39	μs
			$2.7 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$	3.1875	39	μs
			$2.4 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$	17	39	μs
Zero-scale error ^{Notes 1, 2}	EZS	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}			± 0.35	%FSR
Full-scale error ^{Notes 1, 2}	EFS	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}			± 0.35	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}			± 3.5	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution $AV_{REFP} = V_{DD}$ ^{Note 3}			± 2.0	LSB
Analog input voltage	V _{AIN}	ANI16 to ANI22	0		AV_{REFP} and V_{DD}	V

- Notes**
1. Excludes quantization error ($\pm 1/2$ LSB).
 2. This value is indicated as a ratio (%FSR) to the full-scale value.
 3. When $AV_{REFP} \leq V_{DD}$, the MAX. values are as follows.
 Overall error: Add ± 4.0 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.
 Zero-scale error/Full-scale error: Add $\pm 0.20\%$ FSR to the MAX. value when $AV_{REFP} = V_{DD}$.
 Integral linearity error/ Differential linearity error: Add ± 2.0 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

(3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = V_{SS} (ADREFM = 0), target pin: ANI0 to ANI3, ANI16 to ANI22, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, Reference voltage (+) = V_{DD} , Reference voltage (-) = V_{SS})

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit	
Resolution	RES		8		10	bit	
Overall error ^{Note 1}	AINL	10-bit resolution		1.2	±7.0	LSB	
Conversion time	t _{CONV}	10-bit resolution Target pin: ANI0 to ANI3, ANI16 to ANI22	3.6 V ≤ V_{DD} ≤ 5.5 V	2.125		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.1875		39	μs
			2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
Conversion time	t _{CONV}	10-bit resolution Target pin: internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V ≤ V_{DD} ≤ 5.5 V	2.375		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.5625		39	μs
			2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
Zero-scale error ^{Notes 1, 2}	EZS	10-bit resolution			±0.60	%FSR	
Full-scale error ^{Notes 1, 2}	EFS	10-bit resolution			±0.60	%FSR	
Integral linearity error ^{Note 1}	ILE	10-bit resolution			±4.0	LSB	
Differential linearity error ^{Note 1}	DLE	10-bit resolution			±2.0	LSB	
Analog input voltage	V _{AIN}	ANI0 to ANI3, ANI16 to ANI22	0		V_{DD}	V	
		Internal reference voltage (HS (high-speed main) mode)	V_{BGR} ^{Note 3}			V	
		Temperature sensor output voltage (HS (high-speed main) mode)	V_{TMPS25} ^{Note 3}			V	

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. Refer to **3.6.2 Temperature sensor/internal reference voltage characteristics**.

(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM (ADREFM = 1), target pin: ANI0, ANI2, ANI3, and ANI16 to ANI22

(TA = -40 to +105°C, 2.4 V ≤ VDD ≤ 5.5 V, VSS = 0 V, Reference voltage (+) = VBGR^{Note 3}, Reference voltage (-) = AVREFM^{Note 4} = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES		8			bit
Conversion time	tCONV	8-bit resolution	17		39	μs
Zero-scale error ^{Notes 1, 2}	EZS	8-bit resolution			±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	8-bit resolution			±2.0	LSB
Differential linearity error ^{Note 1}	DLE	8-bit resolution			±1.0	LSB
Analog input voltage	VAIN		0		VBGR ^{Note 3}	V

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. Refer to **3.6.2 Temperature sensor/internal reference voltage characteristics**.

4. When reference voltage (-) = VSS, the MAX. values are as follows.

Zero-scale error: Add ±0.35%FSR to the MAX. value when reference voltage (-) = AVREFM.

Integral linearity error: Add ±0.5 LSB to the MAX. value when reference voltage (-) = AVREFM.

Differential linearity error: Add ±0.2 LSB to the MAX. value when reference voltage (-) = AVREFM.

3.6.2 Temperature sensor/internal reference voltage characteristics

(TA = -40 to +105°C, 2.4 V ≤ VDD ≤ 5.5 V, VSS = 0 V, HS (high-speed main) mode

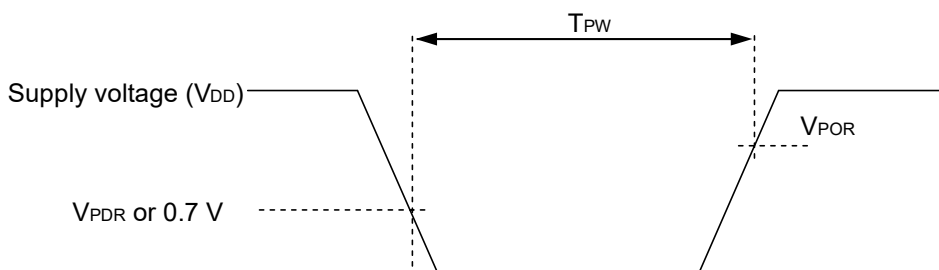
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V _{TMP25}	Setting ADS register = 80H, TA = +25°C		1.05		V
Internal reference voltage	V _{BGR}	Setting ADS register = 81H	1.38	1.45	1.50	V
Temperature coefficient	F _{VTMP5}	Temperature sensor output voltage that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	t _{AMP}		5			μs

3.6.3 POR circuit characteristics

(TA = -40 to +105°C, VSS = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	V _{POR}	Power supply rise time	1.45	1.51	1.57	V
	V _{PDR}	Power supply fall time	1.44	1.50	1.56	V
Minimum pulse width ^{Note}	T _{PW}		300			μs

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



3.6.4 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interrupt Mode

(TA = -40 to +105°C, VPDR ≤ VDD ≤ 5.5 V, VSS = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection supply voltage	VLVD0	Power supply rise time	3.90	4.06	4.22	V
		Power supply fall time	3.83	3.98	4.13	V
	VLVD1	Power supply rise time	3.60	3.75	3.90	V
		Power supply fall time	3.53	3.67	3.81	V
	VLVD2	Power supply rise time	3.01	3.13	3.25	V
		Power supply fall time	2.94	3.06	3.18	V
	VLVD3	Power supply rise time	2.90	3.02	3.14	V
		Power supply fall time	2.85	2.96	3.07	V
	VLVD4	Power supply rise time	2.81	2.92	3.03	V
		Power supply fall time	2.75	2.86	2.97	V
	VLVD5	Power supply rise time	2.70	2.81	2.92	V
		Power supply fall time	2.64	2.75	2.86	V
	VLVD6	Power supply rise time	2.61	2.71	2.81	V
		Power supply fall time	2.55	2.65	2.75	V
	VLVD7	Power supply rise time	2.51	2.61	2.71	V
		Power supply fall time	2.45	2.55	2.65	V
Minimum pulse width	tLW		300			μs
Detection delay time					300	μs

LVD detection voltage of interrupt & reset mode**(TA = -40 to +105°C, V_{PDR} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)**

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit	
Interrupt and reset mode	V _{LVDD0}	V _{POC2} , V _{POC1} , V _{POC1} = 0, 1, 1, falling reset voltage	2.64	2.75	2.86	V	
	V _{LVDD1}	LVIS1, LVIS0 = 1, 0	Rising reset release voltage	2.81	2.92	3.03	V
			Falling interrupt voltage	2.75	2.86	2.97	V
	V _{LVDD2}	LVIS1, LVIS0 = 0, 1	Rising reset release voltage	2.90	3.02	3.14	V
			Falling interrupt voltage	2.85	2.96	3.07	V
	V _{LVDD3}	LVIS1, LVIS0 = 0, 0	Rising reset release voltage	3.90	4.06	4.22	V
Falling interrupt voltage			3.83	3.98	4.13	V	

3.6.5 Power supply voltage rising slope characteristics**(TA = -40 to +105°C, V_{SS} = 0 V)**

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	S _{VDD}				54	V/ms

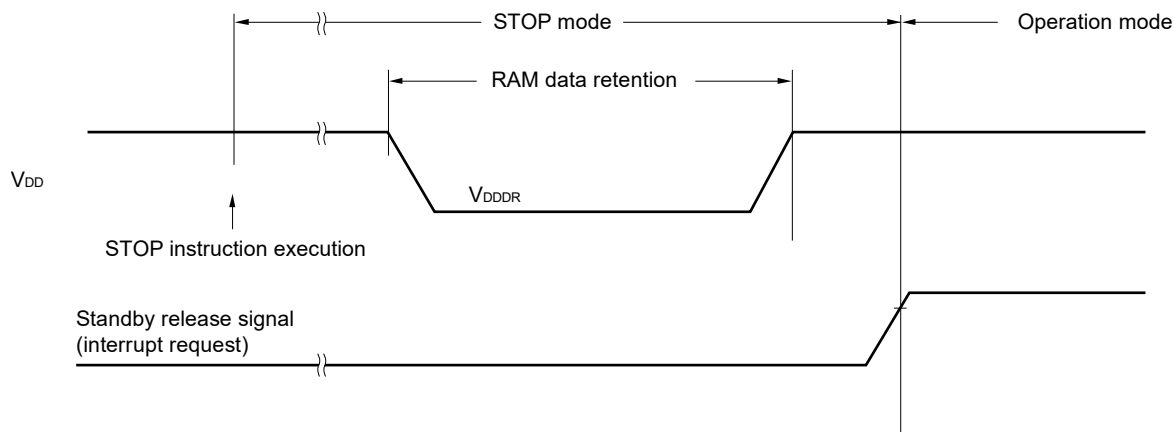
Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 3.4 AC Characteristics.

3.7 RAM Data Retention Characteristics

(TA = -40 to +105°C, VSS = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.44 <small>Note</small>		5.5	V

Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.



3.8 Flash Memory Programming Characteristics

(TA = -40 to +105°C, 2.4 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
System clock frequency	fCLK		1		24	MHz
Code flash memory rewritable times <small>Notes 1, 2, 3</small>	C _{erwr}	Retained for 20 years TA = 85°C <small>Note 4</small>	1,000			Times
Data flash memory rewritable times <small>Notes 1, 2, 3</small>		Retained for 1 year TA = 25°C		1,000,000		
		Retained for 5 years TA = 85°C <small>Note 4</small>	100,000			
		Retained for 20 years TA = 85°C <small>Note 4</small>	10,000			

- Notes**
- 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.
 2. When using flash memory programmer and Renesas Electronics self programming library
 3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.
 4. This temperature is the average value at which data are retained.

3.9 Dedicated Flash Memory Programmer Communication (UART)

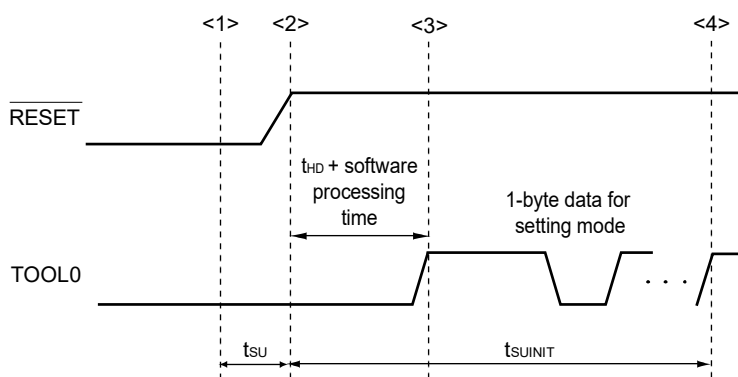
(TA = -40 to +105°C, 2.4 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

3.10 Timing of Entry to Flash Memory Programming Modes

(TA = -40 to +105°C, 2.4 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	t _{SUINIT}	POR and LVD reset are released before external release			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	t _{SU}	POR and LVD reset are released before external release	10			μs
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	t _{HD}	POR and LVD reset are released before external release	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset is released (POR and LVD reset must be released before the external reset is released.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark t_{SUINIT}: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.

t_{SU}: Time to release the external reset after the TOOL0 pin is set to the low level

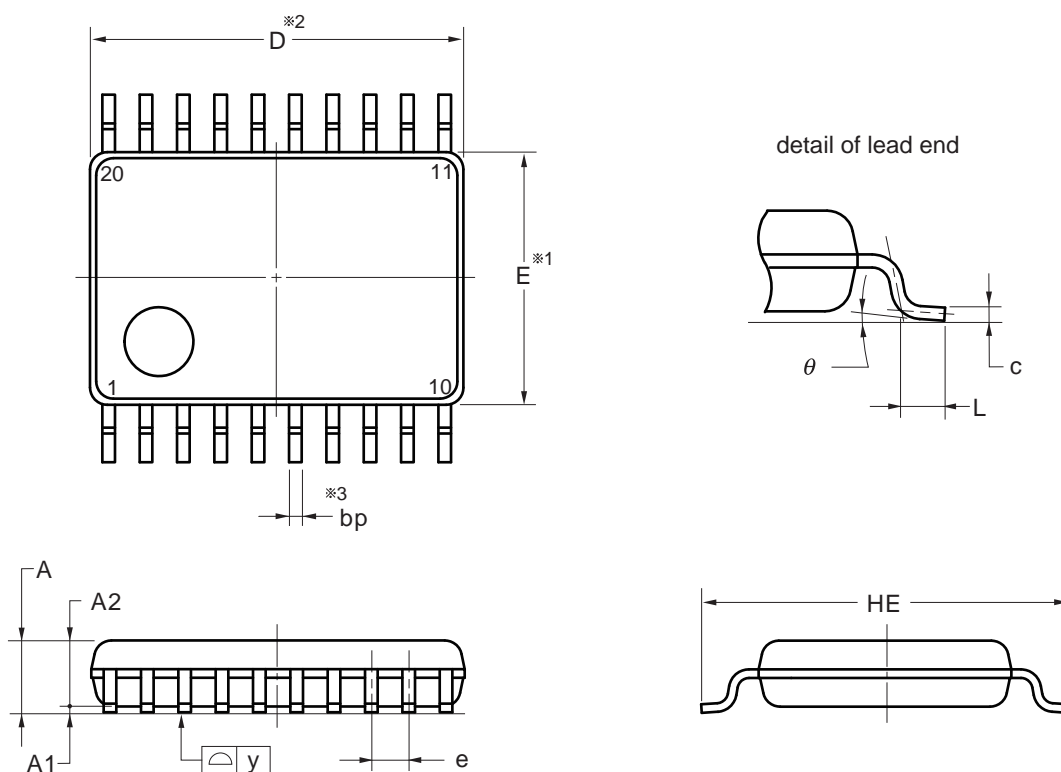
t_{HD}: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)

4. PACKAGE DRAWINGS

4.1 20-pin products

R5F1026AASP, R5F10269ASP, R5F10268ASP, R5F10267ASP, R5F10266ASP
 R5F1036AASP, R5F10369ASP, R5F10368ASP, R5F10367ASP, R5F10366ASP
 R5F1026ADSP, R5F10269DSP, R5F10268DSP, R5F10267DSP, R5F10266DSP
 R5F1036ADSP, R5F10369DSP, R5F10368DSP, R5F10367DSP, R5F10366DSP
 R5F1026AGSP, R5F10269GSP, R5F10268GSP, R5F10267GSP, R5F10266GSP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP20-4.4x6.5-0.65	PLSP0020JB-A	P20MA-65-NAA-1	0.1



NOTE

- 1. Dimensions "※1" and "※2" do not include mold flash.
- 2. Dimension "※3" does not include trim offset.

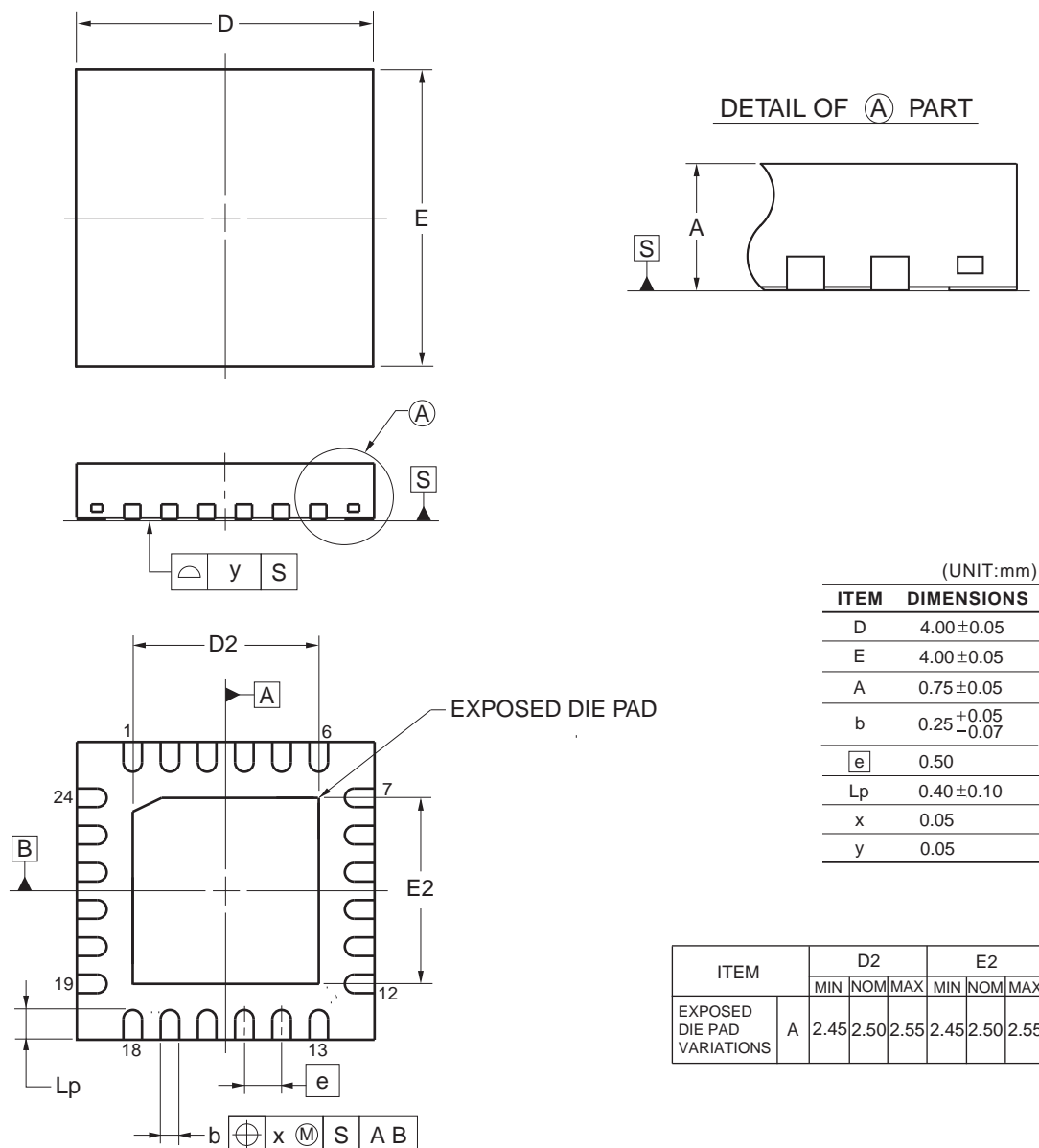
(UNIT:mm)

ITEM	DIMENSIONS
D	6.50±0.10
E	4.40±0.10
HE	6.40±0.20
A	1.45 MAX.
A1	0.10±0.10
A2	1.15
e	0.65±0.12
bp	0.22 ^{+0.10} _{-0.05}
c	0.15 ^{+0.05} _{-0.02}
L	0.50±0.20
y	0.10
θ	0° to 10°

4.2 24-pin products

R5F1027AANA, R5F10279ANA, R5F10278ANA, R5F10277ANA
 R5F1037AANA, R5F10379ANA, R5F10378ANA, R5F10377ANA
 R5F1027ADNA, R5F10279DNA, R5F10278DNA, R5F10277DNA
 R5F1037ADNA, R5F10379DNA, R5F10378DNA, R5F10377DNA
 R5F1027AGNA, R5F10279GNA, R5F10278GNA, R5F10277GNA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-HWQFN24-4x4-0.50	PWQN0024KE-A	P24K8-50-CAB-1	0.04

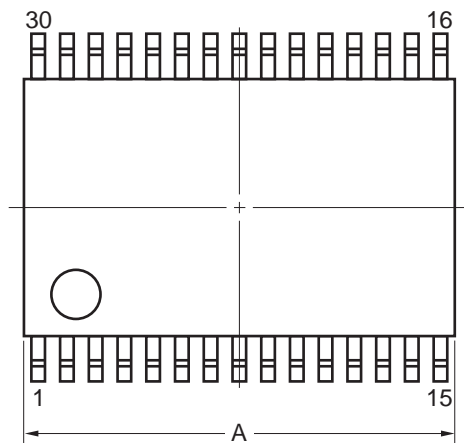


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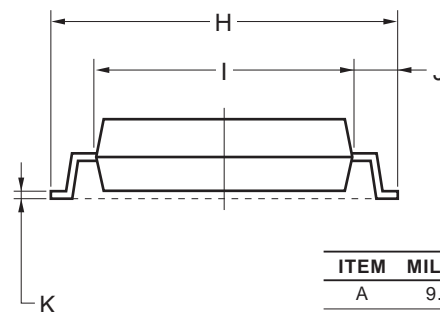
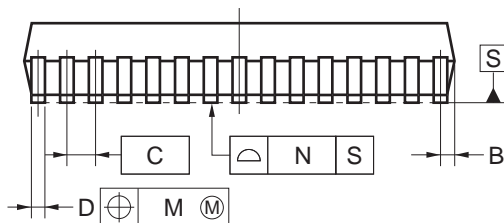
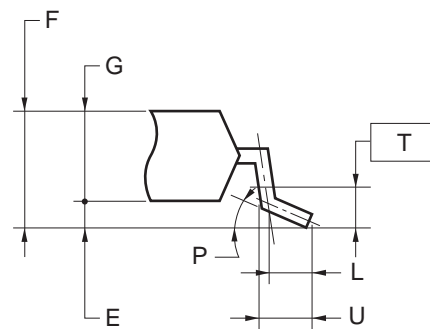
4.3 30-pin products

R5F102AAASP, R5F102A9ASP, R5F102A8ASP, R5F102A7ASP
 R5F103AAASP, R5F103A9ASP, R5F103A8ASP, R5F103A7ASP
 R5F102AADSP, R5F102A9DSP, R5F102A8DSP, R5F102A7DSP
 R5F103AADSP, R5F103A9DSP, R5F103A8DSP, R5F103A7DSP
 R5F102AAGSP, R5F102A9GSP, R5F102A8GSP, R5F102A7GSP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP30-0300-0.65	PLSP0030JB-B	S30MC-65-5A4-3	0.18



detail of lead end



NOTE

Each lead centerline is located within 0.13 mm of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS
A	9.85±0.15
B	0.45 MAX.
C	0.65 (T.P.)
D	0.24 ^{+0.08} _{-0.07}
E	0.1±0.05
F	1.3±0.1
G	1.2
H	8.1±0.2
I	6.1±0.2
J	1.0±0.2
K	0.17±0.03
L	0.5
M	0.13
N	0.10
P	3° ^{+5°} _{-3°}
T	0.25
U	0.6±0.15

Revision History	RL78/G12 Datasheet
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Rev.	Date	Description	
		Page	Summary
1.00	Dec 10, 2012	-	First Edition issued
2.00	Sep 06, 2013	1	Modification of 1.1 Features
		3	Modification of 1.2 List of Part Numbers
		4	Modification of Table 1-1. List of Ordering Part Numbers, Note, and Caution
		7 to 9	Modification of package name in 1.4.1 to 1.4.3
		14	Modification of tables in 1.7 Outline of Functions
		17	Modification of description of table in 2.1 Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$)
		18	Modification of table, Note, and Caution in 2.2.1 X1 oscillator characteristics
		18	Modification of table in 2.2.2 On-chip oscillator characteristics
		19	Modification of Note 3 in 2.3.1 Pin characteristics (1/4)
		20	Modification of Note 3 in 2.3.1 Pin characteristics (2/4)
		23	Modification of Notes 1 and 2 in (1) 20-, 24-pin products (1/2)
		24	Modification of Notes 1 and 3 in (1) 20-, 24-pin products (2/2)
		25	Modification of Notes 1 and 2 in (2) 30-pin products (1/2)
		26	Modification of Notes 1 and 3 in (2) 30-pin products (2/2)
		27	Modification of (3) Peripheral functions (Common to all products)
		28	Modification of table in 2.4 AC Characteristics
		29	Addition of Minimum Instruction Execution Time during Main System Clock Operation
		30	Modification of figures of AC Timing Test Point and External Main System Clock Timing
		31	Modification of figure of AC Timing Test Point
		31	Modification of description and Note 2 in (1) During communication at same potential (UART mode)
		32	Modification of description in (2) During communication at same potential (CSI mode)
		33	Modification of description in (3) During communication at same potential (CSI mode)
		34	Modification of description in (4) During communication at same potential (CSI mode)
		36	Modification of table and Note 2 in (5) During communication at same potential (simplified I ² C mode)
		38, 39	Modification of table and Notes 1 to 9 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)
		40	Modification of Remarks 1 to 3 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)
		41	Modification of table in (7) Communication at different potential (2.5 V, 3 V) (CSI mode)
		42	Modification of Caution in (7) Communication at different potential (2.5 V, 3 V) (CSI mode)
43	Modification of table in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (1/3)		
44	Modification of table and Notes 1 and 2 in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (2/3)		
45	Modification of table, Note 1, and Caution 1 in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (3/3)		
47	Modification of table in (9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode)		
50	Modification of table, Note 1, and Caution 1 in (10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I ² C mode)		

Rev.	Date	Description	
		Page	Summary
2.00	Sep 06, 2013	52	Modification of Remark in 2.5.2 Serial interface IICA
		53	Addition of table to 2.6.1 A/D converter characteristics
		53	Modification of description in 2.6.1 (1)
		54	Modification of Notes 3 to 5 in 2.6.1 (1)
		54	Modification of description and Notes 2 to 4 in 2.6.1 (2)
2.00	Sep 06, 2013	55	Modification of description and Notes 3 and 4 in 2.6.1 (3)
		56	Modification of description and Notes 3 and 4 in 2.6.1 (4)
		57	Modification of table in 2.6.2 Temperature sensor/internal reference voltage characteristics
		57	Modification of table and Note in 2.6.3 POR circuit characteristics
		58	Modification of table in 2.6.4 LVD circuit characteristics
		59	Modification of table of LVD detection voltage of interrupt & reset mode
		59	Modification of number and title to 2.6.5 Power supply voltage rising slope characteristics
		61	Modification of table, figure, and Remark in 2.10 Timing of Entry to Flash Memory Programming Modes
		62 to 103	Addition of products of industrial applications (G: T _A = -40 to +105°C)
		104 to 106	Addition of products of industrial applications (G: T _A = -40 to +105°C)
2.10	Mar 25, 2016	6	Modification of Figure 1-1 Part Number, Memory Size, and Package of RL78/G12
		7	Modification of Table 1-1 List of Ordering Part Numbers
		8	Addition of product name (RL78/G12) and description (Top View) in 1.4.1 20-pin products
		9	Addition of product name (RL78/G12) and description (Top View) in 1.4.2 24-pin products
		10	Addition of product name (RL78/G12) and description (Top View) in 1.4.3 30-pin products
		15	Modification of description in 1.7 Outline of Functions
		16	Modification of description, and addition of target products
		52	Modification of note 2 in 2.5.2 Serial interface IICA
		60	Modification of title and note, and addition of caution in 2.7 RAM Data Retention Characteristics
		60	Modification of conditions in 2.8 Flash Memory Programming Characteristics
		62	Modification of description, and addition of target products and remark
		94	Modification of note 2 in 3.5.2 Serial interface IICA
		102	Modification of title and note in 3.7 RAM Data Retention Characteristics
		102	Modification of conditions in 3.8 Flash Memory Programming Characteristics
		104 to 106	Addition of package name
2.20	Oct 31, 2018	4	Modification of Table 1-1 List of Ordering Part Numbers
		7	Modification of pin configuration diagram in 1.4.1 20-pin products

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NOTES FOR CMOS DEVICES

- (1) **VOLTAGE APPLICATION WAVEFORM AT INPUT PIN:** Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between VIL (MAX) and VIH (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between VIL (MAX) and VIH (MIN).
- (2) **HANDLING OF UNUSED INPUT PINS:** Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.
- (3) **PRECAUTION AGAINST ESD:** A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.
- (4) **STATUS BEFORE INITIALIZATION:** Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.
- (5) **POWER ON/OFF SEQUENCE:** In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current. The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.
- (6) **INPUT OF SIGNAL DURING POWER OFF STATE :** Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.

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(Rev.4.0-1 November 2017)



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